

RL78/G12

RENESAS MCU

True Low Power Platform (as low as 63 µA/MHz), 1.8V to 5.5V operation, 2 to 16 Kbyte Flash, 31 DMIPS at 24MHz, for General Purpose Applications

1. OUTLINE

1.1 Features

Ultra-low power consumption technology

- V_{DD} = single power supply voltage of 1.8 to 5.5 V which can operate at a low voltage
- HALT mode
- STOP mode
- SNOOZE mode

RL78 CPU core

- CISC architecture with 3-stage pipeline
- Minimum instruction execution time: Can be changed from high speed (0.04167 μs: @ 24 MHz operation with high-speed on-chip oscillator) to ultra-low speed (1 μs: @ 1 MHz operation)
- Address space: 1 MB
- General-purpose registers: (8-bit register x 8) x 4 banks
- On-chip RAM: 256 B to 2 KB
- Code flash memory
- Code flash memory: 2 to 16 KB
- Block size: 1 KB
- Prohibition of block erase and rewriting (security function)
- On-chip debug function
- Self-programming (with flash shield window function)

Data flash memory Note

- Data flash memory: 2 KB
- Back ground operation (BGO): Instructions are executed from the program memory while rewriting the data flash memory.
- Number of rewrites: 1,000,000 times (TYP.)
- Voltage of rewrites: VDD = 1.8 to 5.5 V

High-speed on-chip oscillator

- Select from 24 MHz, 16 MHz, 12 MHz, 8 MHz, 6 MHz, 4 MHz, 3 MHz, 2 MHz, and 1 MHz
- High accuracy: +/- 1.0 % (V_{DD} = 1.8 to 5.5 V, T_A = -20 to +85 °C)

Operating ambient temperature

- T_A = -40 to +85 °C (A: Consumer applications, D: Industrial applications)
- T_A = -40 to +105 °C (G: Industrial applications) ^{Note}

Power management and reset function

- On-chip power-on-reset (POR) circuit
- On-chip voltage detector (LVD) (Select interrupt and reset from 12 levels)

DMA (Direct Memory Access) controller Note

- 2 channels
- Number of clocks during transfer between 8/16-bit SFR and internal RAM: 2 clocks

Multiplier and divider/multiply-accumulator

- 16 bits x 16 bits = 32 bits (Unsigned or signed)
- 32 bits x 32 bits = 32 bits (Unsigned)
- 16 bits x 16 bits + 32 bits = 32 bits (Unsigned or signed)

Serial interface

- CSI
- UART
 Simplified I²C communication

.

: 1 to 3 channels : 1 to 3 channels

: 1 channel

- : 0 to 3 channels
- I²C communication

Timer

- 16-bit timer : 4 to 8 channels
 - 12-bit interval timer : 1 channel
 - Watchdog timer
 - : 1 channel (operable with the dedicated low-speed on-chip

oscillator)

A/D converter

- 8/10-bit resolution A/D converter (VDD = 1.8 to 5.5 V)
- 8 to 11 channels, internal reference voltage (1.45 V), and temperature sensor ^{Note}

I/O port

- I/O port: 18 to 26
- (N-ch open drain I/O [withstand voltage of 6 V]: 2, N-ch open drain I/O [V_DD withstand voltage]: 4 to 9)
- Can be set to N-ch open drain, TTL input buffer, and on-chip pull-up resistor
- Different potential interface: Can connect to a 1.8/2.5/3 V device
- On-chip key interrupt function
- On-chip clock output/buzzer output controller

Others

- On-chip BCD (binary-coded decimal) correction circuit
- Note Can be selected only in HS (high-speed main) mode.
- RemarkThe functions mounted depend on the product.See 1.7Outline of Functions.

Datasheet

R01DS0193EJ0220 Rev.2.20 Oct 31, 2018

Code flash	Data flash	RAM	20 pins	24 pins	30 pins
16 KB	2 KB	2 KB	_	_	R5F102AA
	_		_	_	R5F103AA
	2 KB	1.5 KB	R5F1026A Note 1	R5F1027A Note 1	-
	-		R5F1036A Note 1	R5F1037A Note 1	_
12 KB	2KB	1 KB	R5F10269 Note 1	R5F10279 Note 1	R5F102A9
	-		R5F10369 Note 1	R5F10379 Note 1	R5F103A9
8 KB	2 KB	768 B	R5F10268 Note 1	R5F10278 Note 1	R5F102A8
	-		R5F10368 Note 1	R5F10378 Note 1	R5F103A8
4 KB	2KB	512 B	R5F10267	R5F10277	R5F102A7
	-		R5F10367	R5F10377	R5F103A7
2 KB	2 KB	256 B	R5F10266 Note 2	_	_
	-		R5F10366 Note 2	_	_

O ROM, RAM capacities

Notes 1. This is 640 bytes when the self-programming function or data flash function is used. (For details, see CHAPTER 3 CPU ARCHITECTURE in the RL78/G12 User's Manual.)

2. The self-programming function cannot be used for R5F10266 and R5F10366.



Caution When the flash memory is rewritten via a user program, the code flash area and RAM area are used because each library is used. When using the library, refer to RL78 Family Flash Self Programming Library Type01 User's Manual and RL78 Family Data Flash Library Type04 User's Manual.

1.2 List of Part Numbers

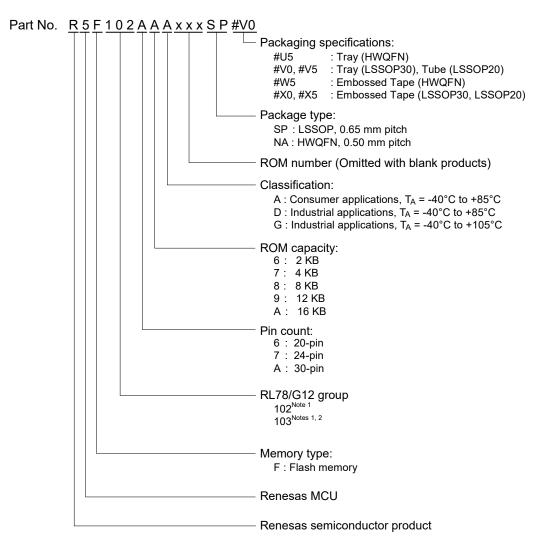


Figure 1-1. Part Number, Memory Size, and Package of RL78/G12

- Notes 1. For details about the differences between the R5F102 products and the R5F103 products of RL78/G12, see 1.1 Differences between the R5F102 Products and the R5F103 Products.
 - Products only for "A: Consumer applications (T_A = -40 to +85°C)" and "D: Industrial applications (T_A = -40 to +85°C)"



Table 1-1.	List of Ordering Part Numbers
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Pin count	Package	Data flash	Fields of Application	Part Number
20 pins	20-pin plastic LSSOP (4.4 × 6.5 mm, 0.65 mm pitch)	Mounted	A	R5F1026AASP#V5, R5F10269ASP#V5, R5F10268ASP#V5, R5F10267ASP#V5, R5F10266ASP#V5 R5F1026AASP#X5, R5F10269ASP#X5, R5F10268ASP#X5, R5F10267ASP#X5, R5F10266ASP#X5
			D	R5F1026ADSP#V5, R5F10269DSP#V5, R5F10268DSP#V5, R5F10267DSP#V5, R5F10266DSP#V5 R5F1026ADSP#X5, R5F10269DSP#X5, R5F10268DSP#X5, R5F10267DSP#X5, R5F10266DSP#X5
			G	R5F1026AGSP#V5, R5F10269GSP#V5, R5F10268GSP#V5, R5F10267GSP#V5, R5F10266GSP#V5 R5F1026AGSP#X5, R5F10269GSP#X5, R5F10268GSP#X5, R5F10267GSP#X5, R5F10266GSP#X5
		Not mounted	A	R5F1036AASP#V5, R5F10369ASP#V5, R5F10368ASP#V5, R5F10367ASP#V5, R5F10366ASP#V5 R5F1036AASP#X5, R5F10369ASP#X5, R5F10368ASP#X5, R5F10367ASP#X5, R5F10366ASP#X5
			D	R5F1036ADSP#V5, R5F10369DSP#V5, R5F10368DSP#V5, R5F10367DSP#V5, R5F10366DSP#V5 R5F1036ADSP#X5, R5F10369DSP#X5, R5F10368DSP#X5, R5F10367DSP#X5, R5F10366DSP#X5
24 pins			A	R5F1027AANA#U5, R5F10279ANA#U5, R5F10278ANA#U5, R5F10277ANA#U5 R5F1027AANA#W5, R5F10279ANA#W5, R5F10278ANA#W5, R5F10277ANA#W5
		mm pitch)		D
			G	R5F1027AGNA#U5, R5F10279GNA#U5, R5F10278GNA#U5, R5F10277GNA#U5 R5F1027AGNA#W5, R5F10279GNA#W5, R5F10278GNA#W5, R5F10277GNA#W5
		Not mounted	A	R5F1037AANA#U5, R5F10379ANA#U5, R5F10378ANA#U5, R5F10377ANA#U5, R5F1037AANA#W5, R5F10379ANA#W5, R5F10378ANA#W5, R5F10377ANA#W5
			D	R5F1037ADNA#U5, R5F10379DNA#U5, R5F10378DNA#U5, R5F10377DNA#U5, R5F1037ADNA#W5, R5F10379DNA#W5, R5F10378DNA#W5, R5F10377DNA#W5
30 pins	30-pin plastic LSSOP	Mounted	A	R5F102AAASP#V0, R5F102A9ASP#V0, R5F102A8ASP#V0, R5F102A7ASP#V0 R5F102AAASP#X0, R5F102A9ASP#X0, R5F102A8ASP#X0, R5F102A7ASP#X0
	(7.62 mm (300), 0.65 mm		D	R5F102AADSP#V0, R5F102A9DSP#V0, R5F102A8DSP#V0, R5F102A7DSP#V0 R5F102AADSP#X0, R5F102A9DSP#X0, R5F102A8DSP#X0, R5F102A7DSP#X0
	pitch))	G	R5F102AAGSP#V0, R5F102A9GSP#V0, R5F102A8GSP#V0, R5F102AAGSP#V0 R5F102AAGSP#X0, R5F102A9GSP#X0, R5F102A8GSP#X0, R5F102AAGSP#X0
		Not mounted	A	R5F103AAASP#V0, R5F103A9ASP#V0, R5F103A8ASP#V0, R5F103A7ASP#V0 R5F103AAASP#X0, R5F103A9ASP#X0, R5F103A8ASP#X0, R5F103A7ASP#X0
			D	R5F103AADSP#V0, R5F103A9DSP#V0, R5F103A8DSP#V0, R5F103A7DSP#V0 R5F103AADSP#X0, R5F103A9DSP#X0, R5F103A8DSP#X0, R5F103A7DSP#X0

Note For fields of application, see Figure 1-1 Part Number, Memory Size, and Package of RL78/G12.

Caution The ordering part numbers represent the numbers at the time of publication. For the latest ordering part numbers, refer to the target product page of the Renesas Electronics website.



1.3 Differences between the R5F102 Products and the R5F103 Products

The following are differences between the R5F102 products and the R5F103 products.

- O Whether the data flash memory is mounted or not
- O High-speed on-chip oscillator oscillation frequency accuracy
- O Number of channels in serial interface
- O Whether the DMA function is mounted or not
- O Whether a part of the safety functions are mounted or not

1.3.1 Data Flash

The data flash memory of 2 KB is mounted on the R5F102 products, but not on the R5F103 products.

Product	Data Flash
R5F102 products	2 KB
R5F1026A, R5F1027A, R5F102AA,	
R5F10269, R5F10279, R5F102A9,	
R5F10268, R5F10278, R5F102A8,	
R5F10267, R5F10277, R5F102A7,	
R5F10266 Note	
R5F103 products	Not mounted
R5F1036A, R5F1037A, R5F103AA,	
R5F10369, R5F10379, R5F103A9,	
R5F10368, R5F10378 R5F103A8,	
R5F10367, R5F10377, R5F103A7,	
R5F10366	

- **Note** The RAM in the R5F10266 has capacity as small as 256 bytes. Depending on the customer's program specification, the stack area to execute the data flash library may not be kept and data may not be written to or erased from the data flash memory.
- Caution When the flash memory is rewritten via a user program, the code flash area and RAM area are used because each library is used. When using the library, refer to RL78 Family Flash Self Programming Library Type01 User's Manual and RL78 Family Data Flash Library Type04 User's Manual.



1.3.2 On-chip oscillator characteristics

(1) High-speed on-chip oscillator oscillation frequency of the R5F102 products

Oscillator	Oscillator Condition		MAX	Unit
High-speed on-chip	T _A = -20 to +85°C	-1.0	+1.0	%
oscillator oscillation	T _A = -40 to -20°C	-1.5	+1.5	
frequency accuracy	T _A = +85 to +105°C	-2.0	+2.0	

(2) High-speed on-chip oscillator oscillation frequency of the R5F103 products

Oscillator	Condition	MIN	MAX	Unit
High-speed on-chip	T _A = -40 to + 85°C	-5.0	+5.0	%
oscillator oscillation				
frequency accuracy				

1.3.3 Peripheral Functions

The following are differences in peripheral functions between the R5F102 products and the R5F103 products.

	R5F102	product	R5F103 product			
RL78/G12		20, 24 pin product	30 pin product	20, 24 pin product	30 pin product	
Serial interface	UART	1 channel	3 channels	1 channel	product	
	CSI	2 channels	3 channels	1 channel		
	Simplified I ² C	2 channels	3 channels	None		
DMA function		2 channels		None		
Safety function	CRC operation	Yes		None		
	RAM guard	Yes		None		
	SFR guard	Yes		None		

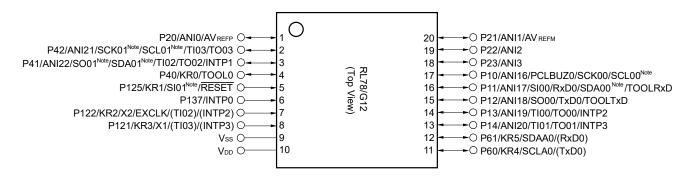


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1.4 Pin Configuration (Top View)

1.4.1 20-pin products

• 20-pin plastic LSSOP (4.4 × 6.5 mm, 0.65 mm pitch)



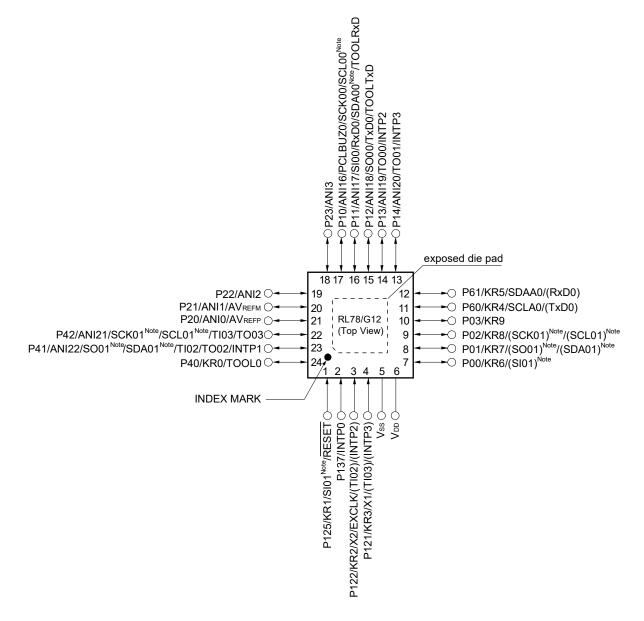
Note Provided only in the R5F102 products.

- Remarks 1. For pin identification, see 1.5 Pin Identification.
 - Functions in parentheses in the above figure can be assigned via settings in the peripheral I/O redirection register (PIOR). See Figure 4-8 Format of Peripheral I/O Redirection Register (PIOR) in the RL78/G12 User's Manual.



1.4.2 24-pin products

• 24-pin plastic HWQFN (4 × 4 mm, 0.5 mm pitch)



Note Provided only in the R5F102 products.

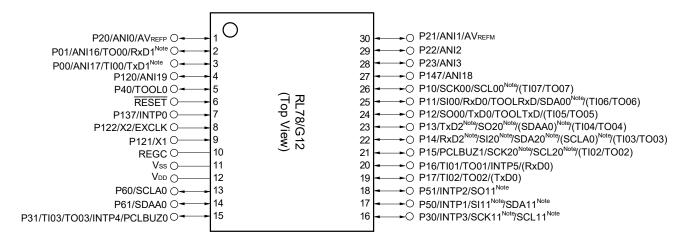
Remarks 1. For pin identification, see 1.5 Pin Identification.

- Functions in parentheses in the above figure can be assigned via settings in the peripheral I/O redirection register (PIOR). See Figure 4-8 Format of Peripheral I/O Redirection Register (PIOR) in the RL78/G12 User's Manual.
- 3. It is recommended to connect an exposed die pad to Vss.



1.4.3 30-pin products

• 30-pin plastic LSSOP (7.62 mm (300), 0.65 mm pitch)



Note Provided only in the R5F102 products.

Caution Connect the REGC pin to Vss via capacitor (0.47 to 1 μ F).

Remarks 1. For pin identification, see 1.5 Pin Identification.

 Functions in parentheses in the above figure can be assigned via settings in the peripheral I/O redirection register (PIOR). See Figure 4-8 Format of Peripheral I/O Redirection Register (PIOR) in the RL78/G12 User's Manual.



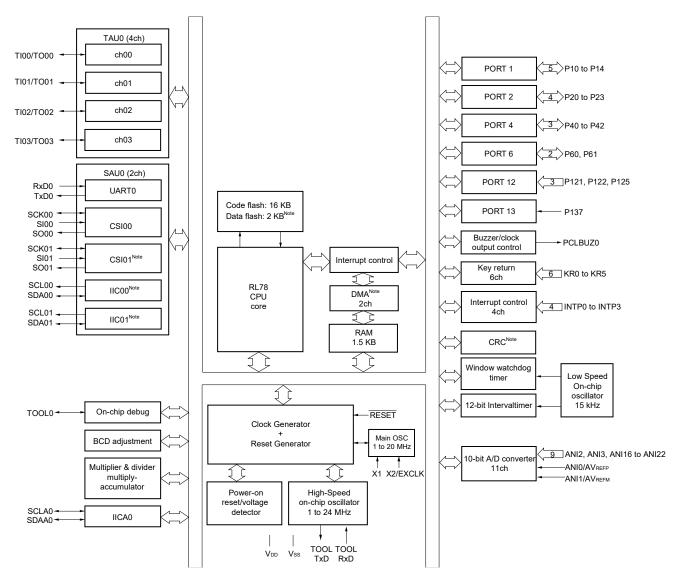
1.5 Pin Identification

ANI0 to ANI3,		REGC:	Regulator Capacitance
ANI16 to ANI22:	Analog input	RESET:	Reset
AVREFM:	Analog Reference Voltage Minus	RxD0 to RxD2:	Receive Data
AVREFP:	Analog reference voltage plus	SCK00, SCK01, SCK11,	
EXCLK:	External Clock Input	SCK20:	Serial Clock Input/Output
	(Main System Clock)	SCL00, SCL01,	
INTP0 to INTP5	Interrupt Request From Peripheral	SCL11, SCL20, SCLA0:	Serial Clock Input/Output
KR0 to KR9:	Key Return	SDA00, SDA01, SDA11,	
P00 to P03:	Port 0	SDA20, SDAA0:	Serial Data Input/Output
P10 to P17:	Port 1	SI00, SI01, SI11, SI20:	Serial Data Input
P20 to P23:	Port 2	SO00, SO01, SO11,	
P30 to P31:	Port 3	SO20:	Serial Data Output
P40 to P42:	Port 4	TI00 to TI07:	Timer Input
P50, P51:	Port 5	TO00 to TO07:	Timer Output
P60, P61:	Port 6	TOOL0:	Data Input/Output for Tool
P120 to P122, P125:	Port 12	TOOLRxD, TOOLTxD:	Data Input/Output for External
P137:	Port 13		Device
P147:	Port 14	TxD0 to TxD2:	Transmit Data
PCLBUZ0, PCLBUZ1:	Programmable Clock Output/	Vdd:	Power supply
	Buzzer Output	Vss:	Ground
		X1, X2:	Crystal Oscillator (Main System Clock)



1.6 Block Diagram

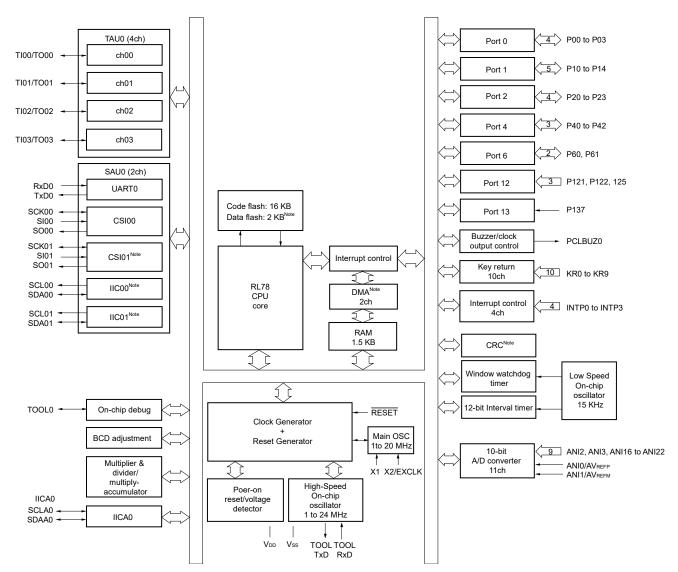
1.6.1 20-pin products



Note Provided only in the R5F102 products.



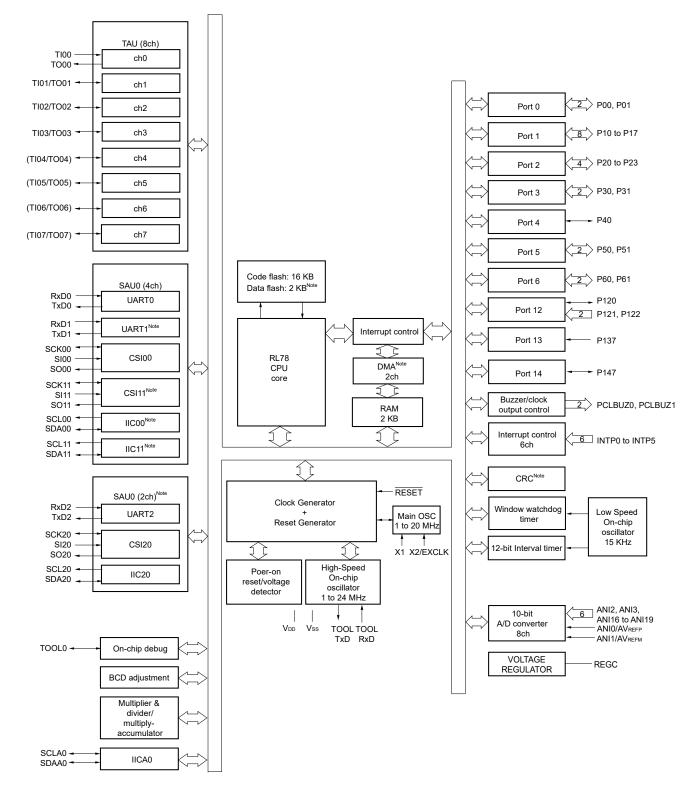
1.6.2 24-pin products



Note Provided only in the R5F102 products.



1.6.3 30-pin products



Note Provided only in the R5F102 products.

Remark Functions in parentheses in the above figure can be assigned via settings in the peripheral I/O redirection register (PIOR). See Figure 4-8 Format of Peripheral I/O Redirection Register (PIOR) in the RL78/G12 User's Manual.

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1.7 Outline of Functions

This outline describes the function at the time when Peripheral I/O redirection register (PIOR) is set to 00H.

	Item	20-	-pin	24-pin		30-pin		
		R5F1026x	R5F1036x	R5F1027x	R5F1037x	R5F102Ax	R5F103Ax	
Code flas	h memory	2 to 16	KB Note 1		4 to 2	16 KB		
Data flash memory		2 KB	_	2 KB	_	2 KB	_	
RAM		256 B to	o 1.5 KB	512 B to	o 1.5 KB	512 B	to 2KB	
Address space				11	ИB			
Main system clock	High-speed system clock	HS (High-spee HS (High-spee	ed main) mode : ed main) mode :	n, external main s 1 to 20 MHz (Vɒ 1 to 16 MHz (Vɒ 1 to 8 MHz (Vɒ⊳ =	D = 2.7 to 5.5 V) D = 2.4 to 5.5 V)	,		
	High-speed on-chip oscillator clock	HS (High-speed	IS (High-speed main) mode : 1 to 24 MHz (V_{DD} = 2.7 to 5.5 V), IS (High-speed main) mode : 1 to 16 MHz (V_{DD} = 2.4 to 5.5 V), .S (Low-speed main) mode : 1 to 8 MHz (V_{DD} = 1.8 to 5.5 V)					
Low-spee	ed on-chip oscillator clock	15 kHz (TYP)						
General-purpose register		(8-bit register × 8) × 4 banks						
Minimum	instruction execution time	0.04167 μ s (High-speed on-chip oscillator clock: fi $_{H}$ = 24 MHz operation)						
		0.05 μs (High-speed system clock: f _{MX} = 20 MHz operation)						
Instructio	n set	Data transfer (8/16 bits)						
		Adder and subtractor/logical operation (8/16 bits)						
		Multiplication (8 bits × 8 bits)						
	T	• Rotate, barrel shift, and bit manipulation (set, reset, test, and Boolean operation), etc.						
I/O port	Total	1	8	2	2	2	26	
	CMOS I/O	(N-ch C	2 D.D. I/O id voltage]: 4)	(N-ch C	6).D. I/O d voltage]: 5)	(N-ch (:1 D.D. I/O id voltage]: 9)	
	CMOS input	4	4		1	;	3	
	N-ch open-drain I/O (6 V tolerance)			2	2			
Timer	16-bit timer		4 channels			8 cha	nnels	
	Watchdog timer	1 channel						
	12-bit Interval timer	1 channel						
Timer output		4 channels (PWM outputs: 3 ^{Note 3})			8 channels (PWM outputs: 7 ^{Notes 2, 3})			

Notes 1. The self-programming function cannot be used in the R5F10266 and R5F10366.

2. The maximum number of channels when PIOR0 is set to 1.

3. The number of PWM outputs varies depending on the setting of channels in use (the number of masters and slaves). (See **6.9.3 Operation as multiple PWM output function** in the RL78/G12 User's Manual.)

Caution When the flash memory is rewritten via a user program, the code flash area and RAM area are used because each library is used. When using the library, refer to RL78 Family Flash Self Programming Library Type01 User's Manual and RL78 Family Data Flash Library Type04 User's Manual.

Item		20	nin	24-	nin	30-p	(2 vin		
item		20- R5F1026x	R5F1036x	R5F1027x	R5F1037x	R5F102Ax	R5F103Ax		
Clock output/buzzer ou	itout	1101 1020		1		2			
	nput	2 44 kHz to 10		al hardware cloc	k: fman - 20 MH				
9/10 hit recolution A/D	convertor	2.44 KHZ to TO		annels	K. IMAIN - 20 IVII I.	8 chan	nolo		
8/10-bit resolution A/D converter		IDEE402014 (20				o char	ineis		
Serial interface			-pin), R5F1027						
			•	C: 2 channels/U	ART: 1 channel				
		[R5F102Ax (30							
				C: 1 channel/UAF					
				C: 1 channel/UAF					
				C: 1 channel/UAF	KI: 1 channel				
		-	-pin), R5F1037						
			• CSI: 1 channel/Simplified I ² C: 0 channel/UART: 1 channel						
		[R5F103Ax (30-pin)]							
	-0.5.1	CSI: 1 channel/Simplified I ² C: 0 channel/UART: 1 channel							
	I ² C bus	1 channel							
Multiplier and divider/m accumulator	ultiply-	• 16 bits × 16 bits = 32 bits (unsigned or signed)							
accumulator		• 32 bits × 32 bits = 32 bits (unsigned)							
		• 16 bits × 16 bits + 32 bits = 32 bits (unsigned or signed)							
DMA controller	1	2 channels	-	2 channels	_	2 channels	-		
Vectored interrupt	Internal	18	16	18	16	26	19		
sources	External			5		6			
Key interrupt		6		1	0	_			
Reset		Reset by RE							
			t by watchdog ti						
			 Internal reset by power-on-reset Internal reset by voltage detector 						
		Internal reset by voltage detector Internal reset by illegal instruction execution ^{Note}							
		Internal reset by RAM parity error							
		Internal reset by illegal-memory access							
Power-on-reset circuit		Power-on-reset: 1.51 V (TYP)							
		Power-down-reset: 1.50 V (TYP)							
Voltage detector		• Rising edge : 1.88 to 4.06 V (12 stages)							
		• Falling edge : 1.84 to 3.98 V (12 stages)							
On-chip debug functior	ı	Provided	Provided						
Power supply voltage		V _{DD} = 1.8 to 5.5	5 V						
Operating ambient tem	perature	$T_A = -40$ to +85	5°C (A: Consum	er applications,	D: Industrial app	olications), T _A = -4	0 to +105°C		
		(G: Industrial a	nnlications)						

Note The illegal instruction is generated when instruction code FFH is executed.

Reset by the illegal instruction execution not issued by emulation with the in-circuit emulator or on-chip debug emulator.

2. ELECTRICAL SPECIFICATIONS ($T_A = -40$ to +85°C)

This chapter describes the following electrical specifications.

- Target products A: Consumer applications T_A = -40 to +85°C
 - R5F102xxAxx, R5F103xxAxx
 - D: Industrial applications T_A = -40 to +85°C R5F102xxDxx, R5F103xxDxx
 - G: Industrial applications when $T_A = -40$ to $+105^{\circ}$ C products is used in the range of $T_A = -40$ to $+85^{\circ}$ C R5F102xxGxx
- Cautions 1. The RL78 microcontrollers have an on-chip debug function, which is provided for development and evaluation. Do not use the on-chip debug function in products designated for mass production, because the guaranteed number of rewritable times of the flash memory may be exceeded when this function is used, and product reliability therefore cannot be guaranteed. Renesas Electronics is not liable for problems occurring when the on-chip debug function is used.
 - 2. The pins mounted depend on the product. Refer to 2.1 Port Functions to 2.2.1 Functions for each product in the RL78/G12 User's Manual.



2.1 Absolute Maximum Ratings

Absolute Maximum Ratings (T_A = 25°C)

Parameter	Symbols	Conditions		Ratings	Unit
Supply Voltage	VDD			-0.5 to + 6.5	V
REGC terminal input voltage ^{Note1}	V _{IREGC} REGC			-0.3 to +2 and -0.3 to V _{DD} + 0.3	V
0				Note 2	
Input Voltage	VI1	Other than P60, F	Other than P60, P61		V
	VI2	P60, P61 (N-ch o	pen drain)	–0.3 to 6.5	V
Output Voltage	Vo			-0.3 to V _{DD} + $0.3^{Note 3}$	V
Analog input voltage	Vai	20-, 24-pin produ	cts: ANI0 to ANI3, ANI16 to ANI22	-0.3 to V _{DD} + 0.3	V
		30-pin products: A	ANI0 to ANI3, ANI16 to ANI19	and –0.3 to $AV_{REF}(+)+0.3^{Notes 3, 4}$	
Output current, high	Іон1	Per pin	Other than P20 to P23	-40	mA
		Total of all pins	All the terminals other than P20 to P23	-170	mA
			20-, 24-pin products: P40 to P42	-70	mA
			30-pin products: P00, P01, P40, P120		
			20-, 24-pin products: P00 to P03 ^{Note 5} , P10 to P14	-100	mA
			30-pin products: P10 to P17, P30, P31, P50, P51, P147		
	Іона Ре	Per pin	P20 to P23	-0.5	mA
		Total of all pins		-2	mA
Output current, low	IOL1	Per pin	Other than P20 to P23	40	mA
		Total of all pins	All the terminals other than P20 to P23	170	mA
			20-, 24-pin products: P40 to P42 30-pin products: P00, P01, P40, P120	70	mA
			20-, 24-pin products: P00 to P03 ^{Note 5} , P10 to P14, P60, P61 30-pin products: P10 to P17, P30, P31, P50, P51, P60, P61, P147	100	mA
	IOL2 Per pin		P20 to P23	1	mA
		Total of all pins]	5	mA
Operating ambient temperature	TA			-40 to +85	°C
Storage temperature	Tstg			-65 to +150	°C

Notes 1. 30-pin product only.

- 2. Connect the REGC pin to Vss via a capacitor (0.47 to 1 μ F). This value determines the absolute maximum rating of the REGC pin. Do not use it with voltage applied.
- 3. Must be 6.5 V or lower.
- 4. Do not exceed AVREF(+) + 0.3 V in case of A/D conversion target pin.
- **5.** 24-pin products only.
- Caution Product quality may suffer if the absolute maximum rating is exceeded even momentarily for any parameter. That is, the absolute maximum ratings are rated values at which the product is on the verge of suffering physical damage, and therefore the product must be used under conditions that ensure that the absolute maximum ratings are not exceeded.
- **Remarks 1.** Unless specified otherwise, the characteristics of alternate-function pins are the same as those of the port pins.
 - **2.** AVREF(+) : + side reference voltage of the A/D converter.
 - 3. Vss : Reference voltage

2.2 Oscillator Characteristics

2.2.1 X1 oscillator characteristics

$(T_A = -40 \text{ to } +85^{\circ}\text{C}, 1.8 \text{ V} \le \text{V}_{DD} \le \text{V}_{DD} \le 5.5 \text{ V}, \text{V}_{SS} = 0 \text{ V})$

Parameter	Resonator	Conditions	MIN.	TYP.	MAX.	Unit
X1 clock oscillation	Ceramic resonator /	$2.7 \text{ V} \leq \text{V}_{\text{DD}} \leq 5.5 \text{ V}$	1.0		20.0	MHz
frequency (fx) ^{Note}	x) ^{Note} crystal oscillator	$1.8 \text{ V} \le \text{V}_{\text{DD}} \le 2.7 \text{ V}$	1.0		8.0	

Note Indicates only permissible oscillator frequency ranges. Refer to AC Characteristics for instruction execution time. Request evaluation by the manufacturer of the oscillator circuit mounted on a board to check the oscillator characteristics.

- Caution Since the CPU is started by the high-speed on-chip oscillator clock after a reset release, check the X1 clock oscillation stabilization time using the oscillation stabilization time counter status register (OSTC) by the user. Determine the oscillation stabilization time of the OSTC register and the oscillation stabilization time select register (OSTS) after sufficiently evaluating the oscillation stabilization time with the resonator to be used.
- Remark When using the X1 oscillator, refer to 5.4 System Clock Oscillator in the RL78/G12 User's Manual.

2.2.2 On-chip oscillator characteristics

$(T_A = -40 \text{ to } +85^{\circ}\text{C}, 1.8 \text{ V} \le \text{V}_{DD} \le 5.5 \text{ V}, \text{ V}_{SS} = 0 \text{ V})$

Oscillators	Parameters	Conditions		MIN.	TYP.	MAX.	Unit
High-speed on-chip oscillator clock frequency ^{Notes 1, 2}	fін			1		24	MHz
High-speed on-chip oscillator		R5F102 products	T _A = -20 to +85°C	-1.0		+1.0	%
clock frequency accuracy			$T_A = -40 \text{ to } -20^{\circ}\text{C}$	-1.5		+1.5	%
		R5F103 products		-5.0		+5.0	%
Low-speed on-chip oscillator clock frequency	fı∟				15		kHz
Low-speed on-chip oscillator clock frequency accuracy				-15		+15	%

Notes 1. High-speed on-chip oscillator frequency is selected by bits 0 to 3 of option byte (000C2H) and bits 0 to 2 of HOCODIV register.

2. This only indicates the oscillator characteristics. Refer to AC Characteristics for instruction execution time.



2.3 DC Characteristics

2.3.1 Pin characteristics

TA = <mark>-40 to +85°C</mark> , 1	I.8 V ≤ V	$f_{DD} \le 5.5 \text{ V}, \text{ Vss} = 0 \text{ V}$	-			(1/4)	
Parameter	Symbol	Conditions			TYP.	MAX.	Unit
Output current, high ^{Note 1}	Іон1	20-, 24-pin products: Per pin for P00 to P03 ^{Note 4} , P10 to P14, P40 to P42 30-pin products: Per pin for P00, P01, P10 to P17, P30, P31, P40, P50, P51, P120, P147				-10.0 Note 2	mA
		20-, 24-pin products:	$4.0 \text{ V} \leq \text{V}_{\text{DD}} \leq 5.5 \text{ V}$			-30.0	mA
		Total of P40 to P42	$2.7 \text{ V} \leq \text{V}_{\text{DD}} < 4.0 \text{ V}$			-6.0	mA
		30-pin products: Total of P00, P01, P40, P120 (When duty ≤ 70% ^{Note 3})	$1.8 \text{ V} \le \text{V}_{\text{DD}} \le 2.7 \text{ V}$			-4.5	mA
		20-, 24-pin products:	$4.0 \text{ V} \leq \text{V}_{\text{DD}} \leq 5.5 \text{ V}$			-80.0	mA
		Total of P00 to P03 ^{Note 4} , P10 to P14	$2.7 \text{ V} \leq \text{V}_{\text{DD}} < 4.0 \text{ V}$			-18.0	mA
		30-pin products: Total of P10 to P17, P30, P31, P50, P51, P147 (When duty ≤ 70% ^{Note 3})	$1.8 \text{ V} \le \text{V}_{\text{DD}} \le 2.7 \text{ V}$			-10.0	mA
		Total of all pins (When duty $\leq 70\%^{\text{Note 3}}$)				-100	mA
	Іон2	Per pin for P20 to P23				-0.1	mA
		Total of all pins				-0.4	mA

Notes 1. value of current at which the device operation is guaranteed even if the current flows from the VDD pin to an output pin.

2. However, do not exceed the total current value.

3. The output current value under conditions where the duty factor $\leq 70\%$. If duty factor > 70%: The output current value can be calculated with the following expression (where n

represents the duty factor as a percentage).

• Total output current of pins = $(I_{OH} \times 0.7)/(n \times 0.01)$

<Example> Where n = 80% and IoH = -10.0 mA

Total output current of pins = $(-10.0 \times 0.7)/(80 \times 0.01) \approx -8.7$ mA

However, the current that is allowed to flow into one pin does not vary depending on the duty factor. A current higher than the absolute maximum rating must not flow into one pin.

4. 24-pin products only.

Caution P10 to P12 and P41 for 20-pin products, P01, P10 to P12, and P41 for 24-pin products, and P00, P10 to P15, P17, and P50 for 30-pin products do not output high level in N-ch open-drain mode.

Remark Unless specified otherwise, the characteristics of alternate-function pins are the same as those of the port pins.

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$T_A = -40 \text{ to } +85^{\circ}\text{C}, 1.8 \text{ V}$		VDD ≤ 5.5 V, Vss = 0 V)						
Parameter	Symbol	Conditions			TYP.	MAX.	Unit	
Output current, low ^{Note 1}		20-, 24-pin products: Per pin for P00 to P03 ^{Note 4} , P10 to P14, P40 to P42				20.0 Note 2	mA	
		30-pin products: Per pin for P00, P01, P10 to P17, P30, P31, P40, P50, P51, P120, P147						
		Per pin for P60, P61				15.0 Note 2	mA	
		20-, 24-pin products:	$4.0 \text{ V} \leq \text{V}_{\text{DD}} \leq 5.5 \text{ V}$			60.0	mA	
		Total of P40 to P42	$2.7 \text{ V} \leq \text{V}_{\text{DD}} < 4.0 \text{ V}$			9.0	mA	
		30-pin products: Total of P00, P01, P40, P120 (When duty ≤ 70% ^{Note 3})	$1.8 \text{ V} \le \text{V}_{\text{DD}} < 2.7 \text{ V}$			1.8	mA	
		20-, 24-pin products:	$4.0 \text{ V} \leq \text{V}_{\text{DD}} \leq 5.5 \text{ V}$			80.0	mA	
		Total of P00 to P03 ^{Note 4} ,	$2.7 \text{ V} \leq \text{V}_{\text{DD}} < 4.0 \text{ V}$			27.0	mA	
		P10 to P14, P60, P61 30-pin products: Total of P10 to P17, P30, P31, P50, P51, P60, P61, P147 (When duty ≤ 70% ^{Note 3})	1.8 V ≤ V _{DD} < 2.7 V			5.4	mA	
		Total of all pins (When duty $\leq 70\%^{\text{Note 3}}$)				140	mA	
	Iol2	Per pin for P20 to P23				0.4	mA	
		Total of all pins				1.6	mA	

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Notes 1. Value of current at which the device operation is guaranteed even if the current flows from an output pin to the Vss pin.

- 2. However, do not exceed the total current value.
- **3.** The output current value under conditions where the duty factor \leq 70%.

If duty factor > 70%: The output current value can be calculated with the following expression (where n represents the duty factor as a percentage).

- Total output current of pins = $(I_{OL} \times 0.7)/(n \times 0.01)$
- <Example> Where n = 80% and IoL = 10.0 mA

Total output current of pins = $(10.0 \times 0.7)/(80 \times 0.01) \approx 8.7$ mA

However, the current that is allowed to flow into one pin does not vary depending on the duty factor. A current higher than the absolute maximum rating must not flow into one pin.

- 4. 24-pin products only.
- Remark Unless specified otherwise, the characteristics of alternate-function pins are the same as those of the port pins.



Parameter	Symbol	Condition	s	MIN.	TYP.	MAX.	Unit
Input voltage, high	VIH1	Normal input buffer	0.8Vdd		Vdd	V	
		20-, 24-pin products: P00 to P0 P40 to P42					
		30-pin products: P00, P01, P1 P40, P50, P51, P120, P147	0 to P17, P30, P31,				
	VIH2	TTL input buffer	$4.0 \text{ V} \leq \text{V}_{\text{DD}} \leq 5.5 \text{ V}$	2.2		Vdd	V
		20-, 24-pin products: P10, P11	$3.3 \text{ V} \leq \text{V}_{\text{DD}} < 4.0 \text{ V}$	2.0		Vdd	V
		30-pin products: P01, P10, P11, P13 to P17	$1.8 \text{ V} \le \text{V}_{\text{DD}} < 3.3 \text{ V}$	1.5		Vdd	V
	VIH3	P20 to P23		0.7Vdd		Vdd	V
	VIH4	P60, P61	0.7Vdd		6.0	V	
	VIH5	P121, P122, P125 ^{Note 1} , P137,	0.8Vdd		Vdd	V	
Input voltage, low	VIL1	Normal input buffer	0		0.2VDD	V	
		20-, 24-pin products: P00 to P0 P40 to P42)3 ^{Note 2} , P10 to P14,				
		30-pin products: P00, P01, P10 P40, P50, P51, P120, P147					
	VIL2	TTL input buffer	$4.0 \text{ V} \leq \text{V}_{\text{DD}} \leq 5.5 \text{ V}$	0		0.8	V
		20-, 24-pin products: P10, P11	$3.3 \text{ V} \leq \text{V}_{\text{DD}} < 4.0 \text{ V}$	0		0.5	V
		30-pin products: P01, P10, P11, P13 to P17	$1.8 \text{ V} \le \text{V}_{\text{DD}} < 3.3 \text{ V}$	0		0.32	V
	VIL3	P20 to P23		0		0.3Vdd	V
	VIL4	P60, P61		0		0.3Vdd	V
	VIL5	P121, P122, P125 ^{Note 1} , P137, EXCLK, RESET		0		0.2VDD	V
Output voltage, high	Vон1	20-, 24-pin products: P00 to P03 ^{Note 2} , P10 to P14,	4.0 V ≤ V _{DD} ≤ 5.5 V, Іон1 = −10.0 mA	VDD-1.5			V
	30-pin products: P00, P01, P10 to P17, P30, P31, P40, P50, P51, P120, P147	-	4.0 V ≤ V _{DD} ≤ 5.5 V, Іон1 = –3.0 mA	Vdd-0.7			V
		2.7 V ≤ V _{DD} ≤ 5.5 V, Іон1 = −2.0 mA	Vdd-0.6			V	
		1.8 V ≤ V _{DD} ≤ 5.5 V, Іон1 = −1.5 mA	Vdd-0.5			V	
	V _{OH2}	P20 to P23	Іон2 = –100 µA	Vdd-0.5			V

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Notes 1. 20, 24-pin products only. 2. 24-pin products only.

Caution The maximum value of V_I of pins P10 to P12 and P41 for 20-pin products, P01, P10 to P12, and P41 for 24-pin products, and P00, P10 to P15, P17, and P50 for 30-pin products is VDD even in N-ch opendrain mode.

High level is not output in the N-ch open-drain mode.

Remark Unless specified otherwise, the characteristics of alternate-function pins are the same as those of the port pins.



Parameter	Symbol		Conditions			TYP.	MAX.	Unit
Output voltage, low	Vol1		20-, 24-pin products: P00 to P03 ^{Note} , P10 to P14,				1.3	V
		P40 to P42 30-pin products: P00, P01,		$4.0 \text{ V} \le \text{V}_{\text{DD}} \le 5.5 \text{ V},$ $I_{\text{OL1}} = 8.5 \text{ mA}$			0.7	V
		P10 to P17, P30, F P50, P51, P120, P		$2.7 \text{ V} \le \text{V}_{\text{DD}} \le 5.5 \text{ V},$ Iol1 = 3.0 mA			0.6	V
				$2.7 \text{ V} \le \text{V}_{\text{DD}} \le 5.5 \text{ V},$ Iol1 = 1.5 mA			0.4	V
				$1.8 V \le V_{DD} \le 5.5 V$, $I_{OL1} = 0.6 \text{ mA}$			0.4	V
	Vol2	P20 to P23		I _{OL2} = 400 μA			0.4	V
	Vol3	P60, P61 4. loi 4. loi 2. loi 1.		$4.0 \text{ V} \le \text{V}_{\text{DD}} \le 5.5 \text{ V},$ $I_{\text{OL1}} = 15.0 \text{ mA}$			2.0	V
				$4.0 \text{ V} \le \text{V}_{\text{DD}} \le 5.5 \text{ V},$ $I_{\text{OL1}} = 5.0 \text{ mA}$			0.4	V
				$2.7 \text{ V} \le \text{V}_{\text{DD}} \le 5.5 \text{ V},$ $I_{\text{OL1}} = 3.0 \text{ mA}$			0.4	V
				$1.8 \text{ V} \le \text{V}_{\text{DD}} \le 5.5 \text{ V},$ $I_{\text{OL1}} = 2.0 \text{ mA}$			0.4	V
nput leakage current, high	Ішні	$\begin{array}{ll} \text{Other than P121,} & V_{I} = V_{DD} \\ \text{P122} \end{array}$					1	μA
	Ішн2	P121, P122 (X1, X2/EXCLK)	VI = VDD	Input port or external clock input			1	μA
				When resonator connected			10	μA
nput leakage current, ow	ILIL1	Other than P121, P122	VI = Vss				-1	μA
	ILIL2	P121, P122 (X1, X2/EXCLK)	VI = Vss	Input port or external clock input			-1	μA
				When resonator connected			-10	μA
Dn-chip pull-up esistance	Ru	20-, 24-pin product P00 to P03 ^{Note} , P10 P40 to P42, P125,	0 to P14,	Vı = Vss, input port	10	20	100	kΩ
		30-pin products: P00, P01, P10 to P17, P30, P31, P40, P50, P51, P120, P147						

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Note 24-pin products only.

Remark Unless specified otherwise, the characteristics of alternate-function pins are the same as those of the port pins.

2.3.2 Supply current characteristics

(1) 20-, 24-pin products

 $(T_A = -40 \text{ to } +85^{\circ}\text{C}, 1.8 \text{ V} \le \text{V}_{DD} \le 5.5 \text{ V}, \text{V}_{SS} = 0 \text{ V})$

$T_{\rm A} = -40$ to		1.8 V ≤ Vo	o ≤ 5.5 V, Vss :	= 0 V)				r	r	(1/2)		
Parameter	Symbol			Conditions			MIN.	TYP.	MAX.	Unit		
Supply IDD1	Operating	HS(High-speed	$f_{H} = 24 \text{ MHz}^{Note 3}$	Basic	V _{DD} = 5.0 V		1.5		mA			
current ^{Note 1}		mode	main) mode ^{Note 4}		operation	V _{DD} = 3.0 V		1.5				
					Normal	V _{DD} = 5.0 V		3.3	5.0	mA		
					operation	V _{DD} = 3.0 V		3.3	5.0			
			f⊩ = 16 MHz ^{Note 3}		V _{DD} = 5.0 V		2.5	3.7	mA			
				V _{DD} = 3.0 V		2.5	3.7					
				LS(Low-speed	f⊮ = 8 MHz ^{Note 3}		V _{DD} = 3.0 V		1.2	1.8	mA	
	HS(Hig	main) mode ^{Note 4}			V _{DD} = 2.0 V		1.2	1.8				
			$f_{MX} = 20 \text{ MHz}^{\text{Note 2}},$		Square wave input		2.8	4.4	mA			
			main) mode ^{Note4}	V _{DD} = 5.0 V		Resonator connection		3.0	4.6			
					$f_{MX} = 20 \text{ MHz}^{\text{Note 2}},$ $V_{\text{DD}} = 3.0 \text{ V}$,	· · · · · · · · · · · · · · · · · · ·		Square wave input		2.8	4.4
				V _{DD} = 3.0 V				V _{DD} = 3.0 V		Resonator connection		3.0
				f _{MX} = 10 MHz ^{Note 2} ,	^{ote 2} , Squar	Square wave input		1.8	2.6	mA		
				$V_{DD} = 5.0 \text{ V}$ $f_{MX} = 10 \text{ MHz}^{\text{Note 2}},$		V _{DD} = 5.0 V		Resonator connection		1.8	2.6	
							Square wave input		1.8	2.6	mA	
	LS(Low-speed main) mode ^{Note 4}	V _{DD} = 3.0 V	R R	Resonator connection		1.8	2.6					
		$f_{MX} = 8 \text{ MHz}^{\text{Note 2}},$ $V_{DD} = 3.0 \text{ V}$		Square wave input		1.1	1.7	mA				
				Resonator connection		1.1	1.7					
				f _{MX} = 8 MHz ^{Note 2} ,		Square wave input		1.1	1.7	mA		
			V _{DD} = 2.0 V		Resonator connection		1.1	1.7				

Notes 1. Total current flowing into VDD, including the input leakage current flowing when the level of the input pin is fixed to VDD or Vss. The values below the MAX. column include the peripheral operation current. However, not including the current flowing into the A/D converter, LVD circuit, I/O port, and on-chip pull-up/pull-down resistors and the current flowing during data flash rewrite.

- 2. When high-speed on-chip oscillator clock is stopped.
- 3. When high-speed system clock is stopped
- 4. Relationship between operation voltage width, operation frequency of CPU and operation mode is as follows.

HS (High speed main) mode: VDD = 2.7 V to 5.5 V @1 MHz to 24 MHz

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VDD = 2.4 V to 5.5 V @1 MHz to 16 MHz
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- LS (Low speed main) mode: VDD = 1.8 V to 5.5 V @1 MHz to 8 MHz
- Remarks 1. fmx: High-speed system clock frequency (X1 clock oscillation frequency or external main system clock frequency)
 - 2. fin: high-speed on-chip oscillator clock frequency
 - **3.** Temperature condition of the TYP. value is $T_A = 25^{\circ}C$.



(2/2)

(1) 20-, 24-pin products

Parameter	Symbol			Conditions		MIN.	TYP.	MAX.	Unit
Supply	DD2Note 2	HALT	HS (High-speed	f⊪ = 24 MHz ^{Note 4}	V _{DD} = 5.0 V		440	1210	μA
current ^{Note 1}		mode	main) mode ^{Note 6}		V _{DD} = 3.0 V		440	1210	
				f⊮ = 16 MHz ^{Note 4}	V _{DD} = 5.0 V		400	950	μA
					V _{DD} = 3.0 V		400	950	
			LS (Low-speed	f⊪ = 8 MHz ^{Note 4}	V _{DD} = 3.0 V		270	542	μA
		main) mode ^{Note 6}	mode ^{Note 6}	V _{DD} = 2.0 V		270	542		
		main) mode ^{Note 6}	f _{MX} = 20 MHz ^{Note 3} ,	Square wave input		280	1000	μA	
			V _{DD} = 5.0 V	Resonator connection		450	1170		
				Square wave input		280	1000	μA	
				Resonator connection		450	1170		
				Square wave input		190	590	μA	
				Resonator connection		260	660		
				$f_{MX} = 10 \text{ MHz}^{\text{Note 3}},$	Square wave input		190	590	μA
				$V_{DD} = 3.0 V$ f _{MX} = 8 MHz ^{Note 3} ,	Resonator connection		260	660	
			LS (Low-speed		Square wave input		110	360	μA
			main) mode ^{Note 6}	V _{DD} = 3.0 V	Resonator connection		150	416	
				f _{MX} = 8 MHz ^{Note 3} ,	Square wave input		110	360	μA
			V _{DD} = 2.0 V	Resonator connection		150	416		
IDD3 ^{Note 5}	DD3 ^{Note 5}	DD3 ^{Note 5} STOP	T _A = -40°C	$T_A = -40^{\circ}C$			0.19	0.50	μA
	mode	mode $T_A = +25^{\circ}C$				0.24	0.50		
			T _A = +50°C	50°C			0.32	0.80	
			T _A = +70°C				0.48	1.20	
			T _A = +85°C				0.74	2.20	1

Notes 1. Total current flowing into V_{DD}, including the input leakage current flowing when the level of the input pin is fixed to V_{DD} or V_{SS}. The values below the MAX. column include the peripheral operation current. However, not including the current flowing into the A/D converter, LVD circuit, I/O port, and on-chip pull-up/pull-down resistors and the current flowing during data flash rewrite.

- 2. During HALT instruction execution by flash memory.
- 3. When high-speed on-chip oscillator clock is stopped.
- 4. When high-speed system clock is stopped.
- 5. Not including the current flowing into the 12-bit interval timer and watchdog timer.
- **6.** Relationship between operation voltage width, operation frequency of CPU and operation mode is as follows.

HS (High speed main) mode: V_{DD} = 2.7 V to 5.5 V @1 MHz to 24 MHz V_{DD} = 2.4 V to 5.5 V @1 MHz to 16 MHz

- LS (Low speed main) mode: VDD = 1.8 V to 5.5 V @1 MHz to 8 MHz
- **Remarks 1.** f_{MX}: High-speed system clock frequency (X1 clock oscillation frequency or external main system clock frequency)
 - 2. fil: high-speed on-chip oscillator clock frequency
 - 3. Except temperature condition of the TYP. value is $T_A = 25^{\circ}C$, other than STOP mode

(1/2)

(2) 30-pin products

Parameter	Symbol			Conditions			MIN.	TYP.	MAX.	Unit		
Supply		Operating	(U I	f⊪ = 24 MHz ^{Note 3}	Basic	V _{DD} = 5.0 V		1.5		mA		
current ^{Note 1}		mode	main) mode ^{Note 4}		operation	V _{DD} = 3.0 V		1.5				
					Normal	V _{DD} = 5.0 V		3.7	5.5	mA		
					operation	V _{DD} = 3.0 V		3.7	5.5			
			f⊮ = 16 MHz ^{Note 3}		V _{DD} = 5.0 V		2.7	4.0	mA			
				V _{DD} = 3.0 V		2.7	4.0					
	main) mode™ HS (High-spe		f⊩ = 8 MHz ^{Note 3}		V _{DD} = 3.0 V		1.2	1.8	mA			
		main) mode ^{Note 4}			V _{DD} = 2.0 V		1.2	1.8				
		HS (High-speed	$f_{MX} = 20 \text{ MHz}^{Note 2},$		Square wave input		3.0	4.6	mA			
ma	main) mode $^{Note 4}$ V _{DD} = 5.0 V	V _{DD} = 5.0 V		Resonator connection		3.2	4.8					
		$f_{MX} = 20 \text{ MHz}^{\text{Note 2}},$	Note 2	Square wave input		3.0	4.6	mA				
				$V_{DD} = 3.0 V$ f _{MX} = 10 MHz ^{Note 2} ,		Resonator connection		3.2	4.8			
					$f_{MX} = 10 \text{ MHz}^{\text{Note 2}},$,	,		Square wave input		1.9
				V _{DD} = 5.0 V		Resonator connection		1.9	2.7			
				$f_{MX} = 10 \text{ MHz}^{\text{Note 2}},$	f _{MX} = 10 MHz ^{Note 2} , Squa	Square wave input		1.9	2.7	mA		
				V _{DD} = 3.0 V		Resonator connection		1.9	2.7			
	LS (Low-speed main) mode ^{Note 4}	$f_{MX} = 8 \text{ MHz}^{\text{Note 2}},$ $V_{DD} = 3.0 \text{ V}$		Square wave input		1.1	1.7	mA				
				Resonator connection		1.1	1.7					
				$f_{MX} = 8 \text{ MHz}^{\text{Note 2}},$		Square wave input		1.1	1.7	mA		
		V _{DD} = 2.0 V				Resonator connection		1.1	1.7			

Notes 1. Total current flowing into V_{DD}, including the input leakage current flowing when the level of the input pin is fixed to V_{DD} or V_{SS}. The values below the MAX. column include the peripheral operation current. However, not including the current flowing into the A/D converter, LVD circuit, I/O port, and on-chip pull-up/pull-down resistors and the current flowing during data flash rewrite.

- 2. When high-speed on-chip oscillator clock is stopped.
- 3. When high-speed system clock is stopped
- 4. Relationship between operation voltage width, operation frequency of CPU and operation mode is as follows.

HS (High speed main) mode: V_DD = 2.7 V to 5.5 V @1 MHz to 24 MHz

- V_{DD} = 2.4 V to 5.5 V @1 MHz to 16 MHz
- LS (Low speed main) mode: V_{DD} = 1.8 V to 5.5 V @1 MHz to 8 MHz
- Remarks 1. fmx: High-speed system clock frequency (X1 clock oscillation frequency or external main system clock frequency)
 - 2. fin: high-speed on-chip oscillator clock frequency
 - **3.** Temperature condition of the TYP. value is $T_A = 25^{\circ}C$.



(2/2)

(2) 30-pin products

$(T_A = -40 \text{ to } +85^\circ \text{C},$	$1.8 V \leq V_{DD} \leq 5.5$	V, Vss = 0 V)
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Parameter	Symbol			Conditions		MIN.	TYP.	MAX.	Unit
Supply	IDD2 ^{Note 2}	HALT	HS (High-speed	f _{IH} = 24 MHz ^{Note 4}	V _{DD} = 5.0 V		440	1280	μA
current ^{Note 1}		mode	main) mode ^{Note 6}		V _{DD} = 3.0 V		440	1280	
				f⊪ = 16 MHz ^{Note 4}	V _{DD} = 5.0 V		400	1000	μA
					V _{DD} = 3.0 V		400	1000	
			LS (Low-speed	f _{IH} = 8 MHz ^{Note 4}	V _{DD} = 3.0 V		260	530	μA
			main) mode ^{Note 6}	V _{DD} = 2.0 V		260	530		
			HS (High-speed main) mode ^{Note 6}	f _{MX} = 20 MHz ^{Note 3} ,	Square wave input		280	1000	μA
main) mode ^{Note 6}				V _{DD} = 5.0 V	Resonator connection		450	1170	
				f _{MX} = 20 MHz ^{Note 3} ,	Square wave input		280	1000	μA
				V _{DD} = 3.0 V	Resonator connection		450	1170	
		Square wave input		190	600	μA			
				V _{DD} = 5.0 V	Resonator connection		260	670	
				$f_{MX} = 10 \text{ MHz}^{\text{Note 3}},$	Square wave input		190	600	μA
			LS (Low-speed	V _{DD} = 3.0 V	Resonator connection		260	670	
				f _{MX} = 8 MHz ^{Note 3} ,	Square wave input		95	330	μA
			main) mode ^{Note 6}	V _{DD} = 3.0 V	Resonator connection		145	380	
				f _{MX} = 8 MHz ^{Note 3} ,	Square wave input		95	330	μA
				V _{DD} = 2.0 V	Resonator connection		145	380	
	DD3 ^{Note 5}	STOP	T _A = -40°C				0.18	0.50	μA
		mode	T _A = +25°C	T _A = +25°C			0.23	0.50	
			T _A = +50°C	T _A = +50°C			0.30	1.10	
			T _A = +70°C				0.46	1.90	
			T _A = +85°C				0.75	3.30	

Notes 1. Total current flowing into V_{DD}, including the input leakage current flowing when the level of the input pin is fixed to V_{DD} or V_{SS}. The values below the MAX. column include the peripheral operation current. However, not including the current flowing into the A/D converter, LVD circuit, I/O port, and on-chip pull-up/pull-down resistors and the current flowing during data flash rewrite.

- 2. During HALT instruction execution by flash memory.
- 3. When high-speed on-chip oscillator clock is stopped.
- 4. When high-speed system clock is stopped.
- 5. Not including the current flowing into the 12-bit interval timer and watchdog timer.
- **6.** Relationship between operation voltage width, operation frequency of CPU and operation mode is as follows.

HS (High speed main) mode: V_DD = 2.7 V to 5.5 V @1 MHz to 24 MHz V_DD = 2.4 V to 5.5 V @1 MHz to 16 MHz

LS (Low speed main) mode: V_{DD} = 1.8 V to 5.5 V @1 MHz to 8 MHz

- **Remarks 1.** f_{MX}: High-speed system clock frequency (X1 clock oscillation frequency or external main system clock frequency)
 - 2. fin: high-speed on-chip oscillator clock frequency
 - 3. Except STOP mode, temperature condition of the TYP. value is $T_A = 25^{\circ}C$.

(3) Peripheral functions (Common to all products)

$(T_A = -40 \text{ to } +85^{\circ}\text{C}, 1.8 \text{ V} \le \text{V}_{DD} \le 5.5 \text{ V}, \text{V}_{SS} = 0 \text{ V})$

Parameter	Symbol		Conditions	MIN.	TYP.	MAX.	Unit
Low-speed onchip oscillator operating current	FiL Note 1				0.20		μA
12-bit interval timer operating current	ITMKA Notes 1, 2, 3				0.02		μA
Watchdog timer operating current	WDT Notes 1, 2, 4	fı∟ = 15 kHz			0.22		μA
A/D converter	ADC ^{Notes 1, 5}	When conversion at	Normal mode, AV _{REFP} = V _{DD} = 5.0 V		1.30	1.70	mA
operating current		maximum speed	Low voltage mode, $AV_{REFP} = V_{DD} = 3.0 V$		0.50	0.70	mA
A/D converter reference voltage operating current	ADREF Note 1				75.0		μA
Temperature sensor operating current	TMPS Note 1				75.0		μA
LVD operating current	ILVD Notes 1, 6				0.08		μA
Self- programming operating current	FSP Notes 1, 8				2.00	12.20	mA
BGO operating current	BGO Notes 1, 7				2.00	12.20	mA
SNOOZE	ISNOZ Note 1	ADC operation	The mode is performed Note 9		0.50	0.60	mA
operating current			The A/D conversion operations are performed, Low voltage mode, $AV_{REFP} = V_{DD} = 3.0 V$		1.20	1.44	mA
		CSI/UART operation			0.70	0.84	mA

Notes 1. Current flowing to the VDD.

- 2. When high speed on-chip oscillator and high-speed system clock are stopped.
- 3. Current flowing only to the 12-bit interval timer (excluding the operating current of the low-speed on-chip oscillator). The current value of the RL78 microcontrollers is the sum of IDD1, IDD2 or IDD3, and IFIL and ITMKA when the 12-bit interval timer operates.
- 4. Current flowing only to the watchdog timer (including the operating current of the low-speed on-chip oscillator). The current value of the RL78 microcontrollers is the sum of IDD1, IDD2 or IDD3 and IWDT when the watchdog timer operates.
- **5.** Current flowing only to the A/D converter. The current value of the RL78 microcontrollers is the sum of IDD1 or IDD2 and IADC when the A/D converter operates in an operation mode or the HALT mode.
- **6.** Current flowing only to the LVD circuit. The current value of the RL78 microcontrollers is the sum of IDD1, IDD2 or IDD3 and ILVD when the LVD circuit operates.
- 7. Current flowing only during data flash rewrite.
- 8. Current flowing only during self programming.
- 9. For shift time to the SNOOZE mode, see 17.3.3 SNOOZE mode in the RL78/G12 User's Manual.

Remarks 1. fil: Low-speed on-chip oscillator clock frequency

2. Temperature condition of the TYP. value is $T_A = 25^{\circ}C$



2.4 AC Characteristics

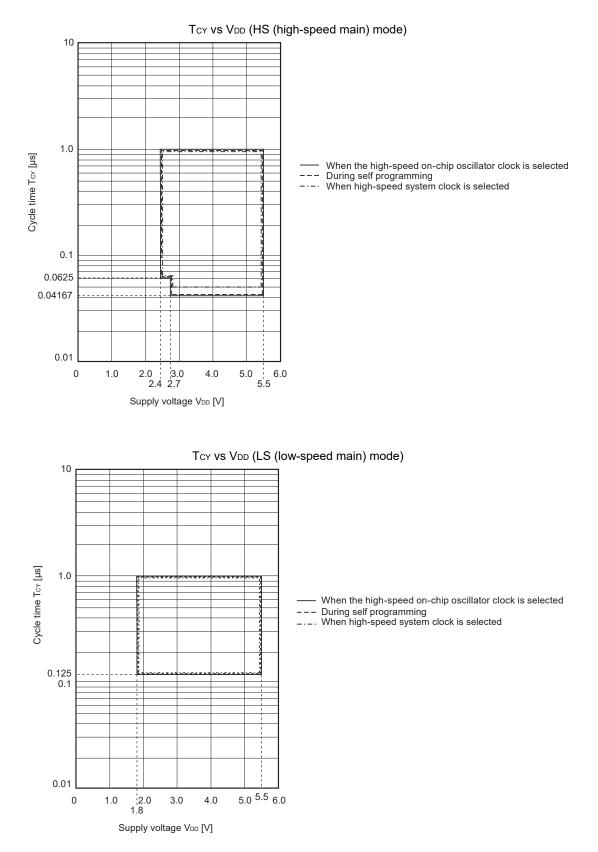
$T_A = -40$ to +85°C, 1.8 V \leq VDD \leq 5.5 V,	, Vss = 0 V)
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Items	Symbol		Condition	s	MIN.	TYP.	MAX.	Unit
Instruction cycle (minimum	Тсү	Main system	HS (High-	$2.7 \text{ V} \leq \text{V}_{\text{DD}} \leq 5.5 \text{ V}$	0.04167		1	μs
instruction execution time)		clock (fMAIN) operation	speed main) mode	$2.4 \text{ V} \leq \text{V}_{\text{DD}} < 2.7 \text{ V}$	0.0625		1	μs
			LS (Low- speed main) mode	$1.8 \text{ V} \leq \text{V}_{\text{DD}} \leq 5.5 \text{ V}$	0.125		1	μs
		During self programming	HS (High- speed main) mode	$2.7 \text{ V} \leq \text{V}_{\text{DD}} \leq 5.5 \text{ V}$	0.04167		1	μs
				$2.4 \text{ V} \leq \text{V}_{\text{DD}} < 2.7 \text{ V}$	0.0625		1	μs
			LS (Low- speed main) mode	$1.8 \text{ V} \le \text{V}_{\text{DD}} \le 5.5 \text{ V}$	0.125		1	μs
External main system clock	fex	$f_{EX} = \frac{2.7 \text{ V} \le \text{V}_{\text{DD}} \le 5.5 \text{ V}}{2.4 \text{ V} \le \text{V}_{\text{DD}} \le 2.7 \text{ V}}$			1.0		20.0	MHz
frequency					1.0		16.0	MHz
		1.8 V ≤ V _{DD} < 2	.4 V		1.0		8.0	MHz
External main system clock	texh, texl	$2.7 \text{ V} \leq \text{V}_{\text{DD}} \leq 5.5 \text{ V}$			24			ns
input high-level width, low-		$2.4 \text{ V} \le \text{V}_{\text{DD}} \le 2.7 \text{ V}$			30			ns
level width		$1.8 \text{ V} \le \text{V}_{\text{DD}} < 2.4 \text{ V}$			60			ns
TI00 to TI07 input high-level width, low-level width	t⊤⊮, t⊤∟				1/fмск + 10			ns
TO00 to TO07 output	fто	$4.0 V \leq V_{DD} \leq 5$.5 V				12	MHz
frequency		$2.7 \text{ V} \leq \text{V}_{\text{DD}} < 4$.0 V				8	MHz
		1.8 V ≤ V _{DD} < 2.7 V					4	MHz
PCLBUZ0, or PCLBUZ1	f PCL	$4.0 \text{ V} \leq \text{V}_{\text{DD}} \leq 5$.5 V				16	MHz
output frequency		$2.7 \text{ V} \le \text{V}_{\text{DD}} < 4.0 \text{ V}$					8	MHz
		1.8 V ≤ V _{DD} < 2	.7 V				4	MHz
INTP0 to INTP5 input high- level width, low-level width	tinth, tintl				1			μs
KR0 to KR9 input available width	tkr.				250			ns
RESET low-level width	trsl				10			μs

Remark fMCK: Timer array unit operation clock frequency (Operation clock to be set by the timer clock select register 0 (TPS0) and the CKS0n bit of timer mode register 0n (TMR0n). n: Channel number (n = 0 to 7))

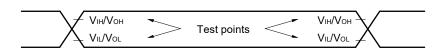


Minimum Instruction Execution Time during Main System Clock Operation

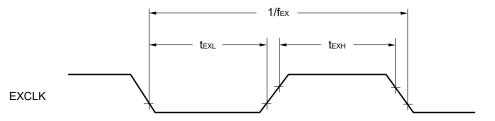




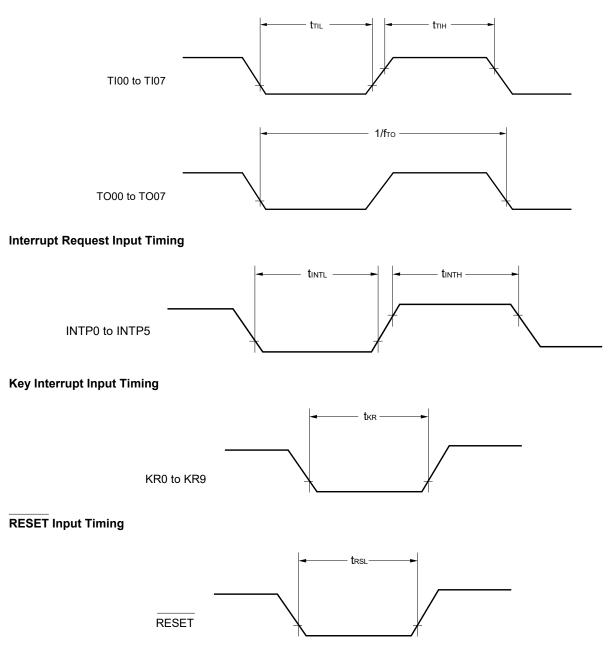
AC Timing Test Point



External Main System Clock Timing



TI/TO Timing





2.5 Peripheral Functions Characteristics

AC Timing Test Point

Vін/Vон VIH/VOH Test points Vil/Vol VIL/VOL

2.5.1 Serial array unit

(1) During communication at same potential (UART mode)

$(T_A = -40 \text{ to } +85^{\circ}\text{C}, 1.8 \text{ V} \le V_{DD} \le 5.5 \text{ V}, \text{ V}_{SS} = 0 \text{ V})$

Parameter	Symbol	Conditions		HS (high-speed main) Mode		LS (low-speed main) Mode	
			MIN.	MAX.	MIN.	MAX.	
Transfer rate				fмск/6		fмск/6	bps
Note 1		Theoretical value of the maximum transfer rate $f_{CLK} = f_{MCK}^{Note 2}$		4.0		1.3	Mbps

Notes 1. Transfer rate in the SNOOZE mode is 4800 bps only.

2. The maximum operating frequencies of the CPU/peripheral hardware clock (fcLK) are:

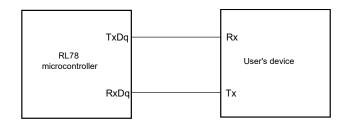
HS (high-speed main) mode: 24 MHz (2.7 V \leq V_{DD} \leq 5.5 V)

16 MHz (2.4 V \leq V_{DD} \leq 5.5 V)

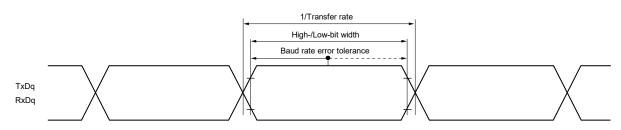
LS (low-speed main) mode: 8 MHz ($1.8 \text{ V} \le \text{V}_{DD} \le 5.5 \text{ V}$)

Caution Select the normal input buffer for the RxDq pin and the normal output mode for the TxDq pin by using port input mode register g (PIMg) and port output mode register g (POMg).

UART mode connection diagram (during communication at same potential)



UART mode bit width (during communication at same potential) (reference)



Remarks 1. q: UART number (q = 0 to 2), g: PIM, POM number (g = 0, 1)

2. fMCK: Serial array unit operation clock frequency

(Operation clock to be set by the serial clock select register m (SPSm) and the CKSmn bit of serial mode register mn (SMRmn).

m: Unit number, n: Channel number (mn = 00 to 03, 10, 11))

RENESAS

(2) During communication at same potential (CSI mode) (master mode, SCK00... internal clock output, corresponding CSI00 only)

Parameter	Symbol	Conditions	HS (high-speed main) Mode		LS (low-speed main) Mode		Unit
			MIN.	MAX.	MIN.	MAX.	
SCK00 cycle time	tKCY1	tκcγ1 ≥ 2/fc∟κ	83.3		250		ns
SCK00 high-/low-	t кн1,	$4.0 \text{ V} \leq \text{V}_{\text{DD}} \leq 5.5 \text{ V}$	tксү1/2–7		tксү1/2–50		ns
level width ti	t ĸ∟1	$2.7 \text{ V} \leq \text{V}_{\text{DD}} \leq 5.5 \text{ V}$	tксү1/2–10		tксү1/2–50		ns
SI00 setup time	tsik1	$4.0 \text{ V} \leq \text{V}_{\text{DD}} \leq 5.5 \text{ V}$	23		110		ns
(to SCK00↑) ^{Note 1}		$2.7 \text{ V} \leq \text{V}_{\text{DD}} \leq 5.5 \text{ V}$	33		110		ns
SI00 hold time (from SCK00↑) ^{Note 2}	tksi1		10		10		ns
Delay time from SCK00↓ to SO00 output ^{Note 3}	tĸso1	C = 20 pF ^{Note 4}		10		10	ns

 $(T_A = -40 \text{ to } +85^{\circ}\text{C}, 2.7 \text{ V} \le V_{DD} \le 5.5 \text{ V}, \text{ V}_{SS} = 0 \text{ V})$

- Notes 1. When DAP00 = 0 and CKP00 = 0, or DAP00 = 1 and CKP00 = 1. The SI00 setup time becomes "to SCK00↓" when DAP00 = 0 and CKP00 = 1, or DAP00 = 1 and CKP00 = 0.
 - When DAP00 = 0 and CKP00 = 0, or DAP00 = 1 and CKP00 = 1. The SI00 hold time becomes "from SCK00↓" when DAP00 = 0 and CKP00 = 1, or DAP00 = 1 and CKP00 = 0.
 - **3.** When DAP00 = 0 and CKP00 = 0, or DAP00 = 1 and CKP00 = 1. The delay time to SO00 output becomes "from SCK00↑" when DAP00 = 0 and CKP00 = 1, or DAP00 = 1 and CKP00 = 0.
 - 4. C is the load capacitance of the SCK00 and SO00 output lines.

Caution Select the normal input buffer for the SI00 pin and the normal output mode for the SO00 and SCK00 pins by using port input mode register 1 (PIM1) and port output mode register 1 (POM1).

- **Remarks 1.** This specification is valid only when CSI00's peripheral I/O redirect function is not used.
 - 2. fMCK: Serial array unit operation clock frequency
 - (Operation clock to be set by the serial clock select register 0 (SPS0) and the CKS00 bit of serial mode register 00 (SMR00).)



Parameter	Symbol	C	Conditions		speed ode	LS (low-speed main) Mode		Unit
				MIN.	MAX.	MIN.	MAX.	
SCKp cycle time	tkcy1	tĸcy1 ≥ 4/fclĸ	$2.7 \text{ V} \leq \text{V}_{\text{DD}} \leq 5.5 \text{ V}$	167		500		ns
			$2.4 \text{ V} \leq \text{V}_{\text{DD}} \leq 5.5 \text{ V}$	250		500		ns
			$1.8 \text{ V} \leq \text{V}_{\text{DD}} \leq 5.5 \text{ V}$	-		500		ns
SCKp high-/low-level width	CKp high-/low-level width t_{KH1} , $4.0 V \le V_{DD} \le 5.5 V$		tксү1/2–12		tксү1/2–50		ns	
	tĸ∟1	$2.7 \text{ V} \leq \text{V}_{\text{DD}} \leq 5.5 \text{ V}$		tксү1/2–18		tксү1/2–50		ns
		$2.4 \text{ V} \leq \text{V}_{\text{DD}} \leq 5.5 \text{ V}$		tксү1/2-38		tксү1/2–50		ns
		$1.8 \text{ V} \le \text{V}_{\text{DD}} \le 5.5 \text{ V}$		-		tксү1/2–50		ns
SIp setup time (to SCKp↑)	tsik1	$4.0 \text{ V} \leq \text{V}_{\text{DD}} \leq 5.5 \text{ V}$		44		110		ns
Note 1		$2.7 \text{ V} \leq \text{V}_{\text{DD}} \leq 5.5 \text{ V}$		44		110		ns
		$2.4 \text{ V} \leq \text{V}_{\text{DD}} \leq 5.5 \text{ V}$		75		110		ns
		$1.8 \text{ V} \leq \text{V}_{\text{DD}} \leq$	5.5 V	_		110		ns
SIp hold time (from SCKp↑) ^{Note 2}	tksi1			19		19		ns
Delay time from SCKp↓ to SOp output ^{Note 3}	tkso1	C = 30 pF ^{Note}	4		25		25	ns

(3) During communication at same potential (CSI mode) (master mode, SCKp... internal clock output) $(T_A = -40 \text{ to } +85^{\circ}\text{C}, 1.8 \text{ V} \le V_{DD} \le 5.5 \text{ V}, \text{ V}_{SS} = 0 \text{ V})$

- **Notes 1.** When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The SIp setup time becomes "to SCKp↓" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
 - **2.** When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The SIp hold time becomes "from SCKp↓" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
 - **3.** When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The delay time to SOp output becomes "from SCKp↑" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
 - **4.** C is the load capacitance of the SCKp and SOp output lines.

Caution Select the normal input buffer for the SIp pin and the normal output mode for the SOp and SCKp pins by using port input mode register 1 (PIM1) and port output mode registers 0, 1, 4 (POM0, POM1, POM4).

Remarks 1. p: CSI number (p = 00, 01, 11, 20), m: Unit number (m = 0, 1), n: Channel number (n = 0, 1, 3: "1, 3" is only for the R5F102 products)

 fMCK: Serial array unit operation clock frequency (Operation clock to be set by the serial clock select register m (SPSm) and the CKSmn bit of serial mode register mn (SMRmn). m: Unit number (m = 0, 1), n: Channel number (n = 0, 1, 3: "1, 3" is only for the R5F102 products.))



Parameter	Symbol	Conditions		HS (high- main) M	•	LS (low-spe Moo	,	Unit
			MIN.	MAX.	MIN.	MAX.		
SCKp cycle time Note 5	t ксү2	$4.0 \text{ V} \leq \text{V}_{\text{DD}} \leq 5.5 \text{ V}$	20 MHz < fмск	8/fмск		_		ns
			fмск ≤ 20 MHz	6/fмск		6/f мск		ns
		$2.7 \text{ V} \leq \text{V}_{\text{DD}} \leq 5.5 \text{ V}$	16 MHz < fмск	8/fмск		-		ns
			fмск ≤ 16 MHz	6/fмск		6/fмск		ns
		$2.4 \text{ V} \leq \text{V}_{\text{DD}} \leq 5.5 \text{ V}$		6/fмск		6/fмск		ns
				and 500		and 500		
		$1.8 \text{ V} \leq \text{V}_{\text{DD}} \leq 5.5 \text{ V}$		_		6/ f мск		ns
					and 750			
SCKp high-/low-level	tкн2,	$4.0 \text{ V} \leq \text{V}_{\text{DD}} \leq 5.5 \text{ V}$		tксү2/2-7		tксү2/2–7		ns
width	tĸ∟2	$2.7 \text{ V} \leq \text{V}_{\text{DD}} \leq 5.5 \text{ V}$	tксү2/2-8		tксү2/2-8		ns	
		$2.4 \text{ V} \leq \text{V}_{\text{DD}} \leq 5.5 \text{ V}$		tксү2/2–18		tксү2/2–18		ns
		$1.8 \text{ V} \leq \text{V}_{\text{DD}} \leq 5.5 \text{ V}$		_		tксү2/2–18		ns
SIp setup time	tsik2	$2.7 \text{ V} \leq \text{V}_{\text{DD}} \leq 5.5 \text{ V}$		1/fмск + 20		1/fмск + 30		ns
(to SCKp↑) ^{Note 1}		$2.4 \text{ V} \leq \text{V}_{\text{DD}} \leq 5.5 \text{ V}$		1/fмск + 30		1/fмск + 30		ns
		$1.8 \text{ V} \leq \text{V}_{\text{DD}} \leq 5.5 \text{ V}$		_		1/fмск + 30		ns
SIp hold time (from SCKp↑) ^{Note 2}	tksi2			1/fмск + 31		1/fмск + 31		ns
Delay time from SCKp↓ to	tĸso2	C = 30 pF ^{Note 4}	$2.7 \text{ V} \leq \text{V}_{\text{DD}} \leq 5.5 \text{ V}$		2/fмск + 44		2/fмск + 110	ns
SOp output Note 3			$2.4 \text{ V} \le \text{V}_{\text{DD}} \le 5.5 \text{ V}$		2/fмск + 75		2/fмск + 110	ns
			$1.8 \text{ V} \le \text{V}_{\text{DD}} \le 5.5 \text{ V}$		_		2/fмск + 110	ns

(4) During communication at same potential (CSI mode) (slave mode, SCKp... external clock input) ($T_A = -40$ to +85°C, 1.8 V $\leq V_{DD} \leq 5.5$ V, Vss = 0 V)

- Notes 1. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The SIp setup time becomes "to SCKp↓" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
 - When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The SIp hold time becomes "from SCKp↓" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
 - **3.** When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The delay time to SOp output becomes "from SCKp↑" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
 - 4. C is the load capacitance of the SOp output lines.
 - 5. Transfer rate in the SNOOZE mode: MAX. 1 Mbps.
- Caution Select the normal input buffer for the SIp and SCKp pins and the normal output mode for the SOp pin by using port input mode register 1 (PIM1) and port output mode registers 0, 1, 4 (POM0, POM1, POM4).

SO User's device

SI



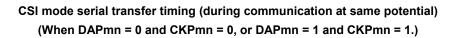
RL78

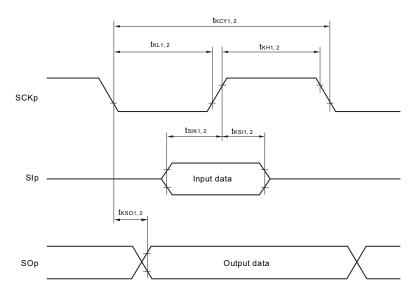
microcontroller

Slp

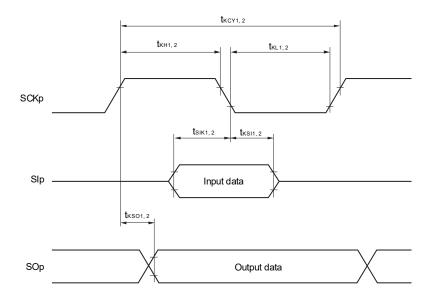
SOp

CSI mode connection diagram (during communication at same potential)





CSI mode serial transfer timing (during communication at same potential) (When DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.)



(Remarks are listed on the next page.)



- Remarks 1. p: CSI number (p = 00, 01, 11, 20), m: Unit number (m = 0, 1), n: Channel number (n = 0, 1, 3: "1, 3" is only for the R5F102 products.)
 - 2. fMCK: Serial array unit operation clock frequency (Operation clock to be set by the serial clock select register m (SPSm) and the CKSmn bit of serial mode register mn (SMRmn). m: Unit number (m = 0, 1), n: Channel number (n = 0, 1, 3: "1, 3" is only for the R5F102 products.))

(5) C	During communicatio	n at same potential	(simplified I ² C mode)
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Parameter	Symbol	Conditions	HS (high-speed	main) Mode	Unit	
			LS (low-speed i	main) Mode		
			MIN.	MAX.		
SCLr clock frequency	fsc∟	$1.8 \text{ V} \le \text{V}_{\text{DD}} \le 5.5 \text{ V},$		400 Note 1	kHz	
		C_b = 100 pF, R_b = 3 k Ω				
		$1.8 \text{ V} \le \text{V}_{\text{DD}} < 2.7 \text{ V},$		300 Note 1	kHz	
		C_b = 100 pF, R_b = 5 k Ω				
Hold time when SCLr = "L"	tLOW	$1.8 \text{ V} \le \text{V}_{\text{DD}} \le 5.5 \text{ V},$	1150		ns	
		C_b = 100 pF, R_b = 3 k Ω				
		$1.8 \text{ V} \le \text{V}_{\text{DD}} < 2.7 \text{ V},$	1550		ns	
		C_b = 100 pF, R_b = 5 k Ω				
Hold time when SCLr = "H"	tніgн	$1.8 \text{ V} \le \text{V}_{\text{DD}} \le 5.5 \text{ V},$	1150		ns	
		C_b = 100 pF, R_b = 3 k Ω				
		$1.8 \text{ V} \le \text{V}_{\text{DD}} < 2.7 \text{ V},$	1550		ns	
		C_b = 100 pF, R_b = 5 k Ω				
Data setup time (reception)	tsu:dat	$1.8 \text{ V} \le \text{V}_{\text{DD}} \le 5.5 \text{ V},$	1/fмск + 145 ^{Note 2}		ns	
		C_b = 100 pF, R_b = 3 k Ω				
		$1.8 \text{ V} \le \text{V}_{\text{DD}} < 2.7 \text{ V},$	1/fмск + 230 ^{Note 2}		ns	
		C_b = 100 pF, R_b = 5 k Ω				
Data hold time (transmission)	thd:dat	$1.8 \text{ V} \le \text{V}_{\text{DD}} \le 5.5 \text{ V},$	0	355	ns	
		C_b = 100 pF, R_b = 3 k Ω				
		$1.8 \text{ V} \le \text{V}_{\text{DD}} < 2.7 \text{ V},$	0	405	ns	
		C _b = 100 pF, R _b = 5 kΩ				

(5)	During co	ommuni	cation a	t same p	otential (simplified	I ² C m

Notes 1. The value must be equal to or less than fmck/4.

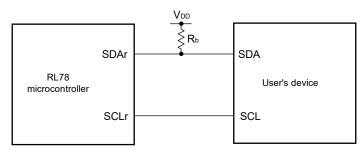
2. Set tsu:DAT so that it will not exceed the hold time when SCLr = "L" or SCLr = "H".

Caution Select the N-ch open drain output (Vob tolerance) mode for SDAr by using port output mode register h (POMh).

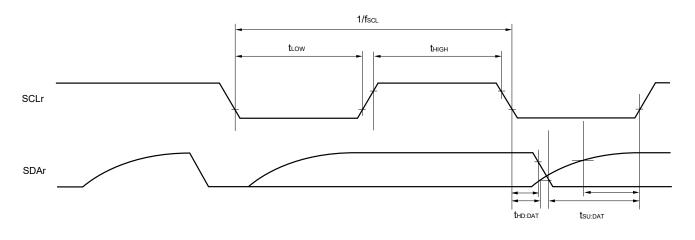
(Remarks are listed on the next page.)



Simplified I²C mode connection diagram (during communication at same potential)



Simplified I²C mode serial transfer timing (during communication at same potential)



Remarks 1. R_b [Ω]:Communication line (SDAr) pull-up resistance

Cb [F]: Communication line (SCLr, SDAr) load capacitance

- **2.** r: IIC number (r = 00, 01, 11, 20), h: = POM number (h = 0, 1, 4, 5)
- fMCK: Serial array unit operation clock frequency (Operation clock to be set by the serial clock select register m (SPSm) and the CKSmn bit of serial mode register mn (SMRmn). m: Unit number (m = 0, 1), n: Channel number (0, 1, 3))
- **4.** Simplified I²C mode is supported only by the R5F102 products.



(6) Communication at different potential (1.8 V, 2.5 V, 3 V) (UART mode) $(T_A = -40 \text{ to } +85^\circ\text{C}, 1.8 \text{ V} \le \text{V}_{DD} \le 5.5 \text{ V}, \text{V}_{SS} = 0 \text{ V})$

Parameter	Symbol			Conditions		igh-speed n) Mode		ow-speed n) Mode	Unit
					MIN.	MAX.	MIN.	MAX.	
Transfer rate ^{Note4}		Reception	$4.0 V \le V_{DI}$ $2.7 V \le V_{b}$			fмск/6 Note1		fмск/6 Note1	bps
			Theoretical value of the maximum transfer rate $f_{MCK} = f_{CLK}^{Note3}$		4.0		1.3	Mbps	
			2.7 V ≤ V _D 2.3 V ≤ V _b			fмск/6 Note1		fмск/6 Note1	bps
			Theoretical value of the maximum transfer rate $f_{MCK} = f_{CLK}$ ^{Note3}		4.0		1.3	Mbps	
		$1.8 V \le V_{DD} < 3.3 V,$ $1.6 V \le V_b \le 2.0 V$			fмск/6 Notes1, 2		fмск/6 Notes1, 2	bps	
				Theoretical value of the maximum transfer rate $f_{MCK} = f_{CLK}$ ^{Note3}		4.0		1.3	Mbps
		Transmission	4.0 V ≤ V _D 2.7 V ≤ V _b			Note4		Note4	bps
				Theoretical value of the maximum transfer rate C_b = 50 pF, R_b = 1.4 k Ω , V_b = 2.7 V		2.8 Note5		2.8 Note5	Mbps
			2.7 V ≤ V _{DE} 2.3 V ≤ V _b	,		Note6		Note6	bps
			Theoretical value of the maximum transfer rate C_b = 50 pF, R_b = 2.7 k Ω , V_b = 2.3 V		1.2 Note7		1.2 Note7	Mbps	
			1.8 V ≤ V _{DE} 1.6 V ≤ V _b			Notes 2, 8		Notes 2, 8	bps
				Theoretical value of the maximum transfer rate $C_b = 50 \text{ pF}, R_b = 5.5 \text{ k}\Omega, V_b = 1.6 \text{ V}$		0.43 Note9		0.43 Note9	Mbps

Notes 1. Transfer rate in the SNOOZE mode is 4800 bps only.

- **2.** Use it with $V_{DD} \ge V_b$.
- **3.** The maximum operating frequencies of the CPU/peripheral hardware clock (fcLκ) are: HS (high-speed main) mode: 24 MHz (2.7 V ≤ V_{DD} ≤ 5.5 V)

16 MHz (2.4 V ≤ V_{DD} ≤ 5.5 V)

- LS (low-speed main) mode: 8 MHz (1.8 V \leq VDD \leq 5.5 V)
- **4.** The smaller maximum transfer rate derived by using f_{MCK}/6 or the following expression is the valid maximum transfer rate.

Expression for calculating the transfer rate when 4.0 V \leq V_{DD} \leq 5.5 V and 2.7 V \leq V_b \leq 4.0 V

$$\frac{1}{\{-C_b \times R_b \times \ln (1 - \frac{2.2}{V_b})\} \times 3}$$
 [bps]

Baud rate error (theoretical value) = $\frac{\frac{1}{\text{Transfer rate} \times 2} - \{-C_b \times R_b \times \ln(1 - \frac{2.2}{V_b})\}}{(\frac{1}{\text{Transfer rate}}) \times \text{Number of transferred bits}} \times 100 [\%]$

* This value is the theoretical value of the relative difference between the transmission and reception sides.

- × 100 [%]

- This value as an example is calculated when the conditions described in the "Conditions" column are met. Refer to Note 4 above to calculate the maximum transfer rate under conditions of the customer.
- **6.** The smaller maximum transfer rate derived by using f_{MCK}/6 or the following expression is the valid maximum transfer rate.

Expression for calculating the transfer rate when 2.7 V \leq V_{DD} < 4.0 V and 2.3 V \leq V_b \leq 2.7 V

Maximum transfer rate =

$$\frac{1}{\{-C_b \times R_b \times \ln (1 - \frac{2.0}{V_b})\} \times 3}$$
 [bps]

Baud rate error (theoretical value) =

 $(\frac{1}{\text{Transfer rate}})$ × Number of transferred bits

 $\frac{1}{\text{Transfer rate } \times 2} - \{-C_b \times R_b \times \ln (1 - \frac{2.0}{V_b})\}$

- * This value is the theoretical value of the relative difference between the transmission and reception sides.
- This value as an example is calculated when the conditions described in the "Conditions" column are met. Refer to Note 6 above to calculate the maximum transfer rate under conditions of the customer.
- 8. The smaller maximum transfer rate derived by using fmck/6 or the following expression is the valid maximum transfer rate.

Expression for calculating the transfer rate when 1.8 V \leq V_{DD} < 3.3 V, 1.6 V \leq V_b \leq 2.0 V

Maximum transfer rate =

$$\frac{1}{\{-C_b \times R_b \times \ln (1 - \frac{1.5}{V_b})\} \times 3}$$
 [bps]

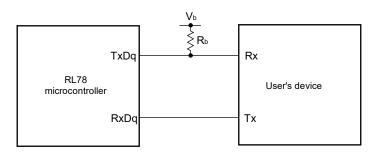
Baud rate error (theoretical value) =
$$\frac{\frac{1}{\text{Transfer rate} \times 2} - \{-C_b \times R_b \times \ln(1 - \frac{1.5}{V_b})\}}{(\frac{1}{\text{Transfer rate}}) \times \text{Number of transferred bits}} \times 100 [\%]$$

* This value is the theoretical value of the relative difference between the transmission and reception sides.

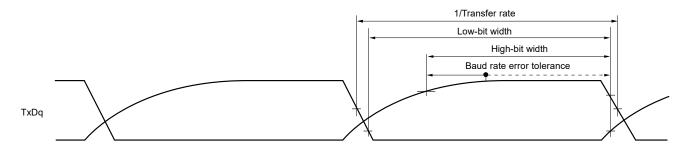
- **9.** This value as an example is calculated when the conditions described in the "Conditions" column are met. Refer to **Note 8** above to calculate the maximum transfer rate under conditions of the customer.
- Caution Select the TTL input buffer for the RxDq pin and the N-ch open drain output (V_{DD} tolerance) mode for the TxDq pin by using port input mode register g (PIMg) and port output mode register g (POMg). For V_{IH} and V_{IL}, see the DC characteristics with TTL input buffer selected.

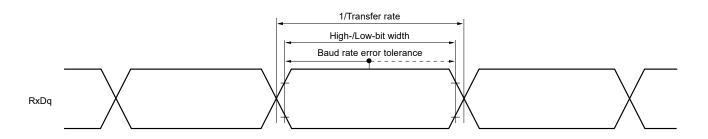


UART mode connection diagram (during communication at different potential)



UART mode bit width (during communication at different potential) (reference)





- **Remarks 1.** R_b[Ω]: Communication line (TxDq) pull-up resistance, C_b[F]: Communication line (TxDq) load capacitance, V_b[V]: Communication line voltage
 - **2.** q: UART number (q = 0 to 2), g: PIM and POM number (g = 0, 1)
 - **3.** fMCK: Serial array unit operation clock frequency
 - (Operation clock to be set by the serial clock select register m (SPSm) and the CKSmn bit of serial mode register mn (SMRmn).

m: Unit number, n: Channel number (mn = 00 to 03, 10, 11))

4. UART0 of the 20- and 24-pin products supports communication at different potential only when the peripheral I/O redirection function is not used.



(7) Communication at different potential (2.5 V, 3 V) (CSI mode) (master mode, SCK00... internal clock output, corresponding CSI00 only)

Parameter	Symbol		Conditions	HS (higł main)		LS (low main)		Unit
				MIN.	MAX.	MIN.	MAX.	-
SCK00 cycle time	tксү1	tĸcy1≥2/fcLK		200		1150		ns
			$\begin{array}{l} 2.7 \; V \leq V_{DD} < 4.0 \; V, \\ 2.3 \; V \leq V_b \leq 2.7 \; V, \\ C_b = 20 \; pF, \; R_b = 2.7 \; k\Omega \end{array}$	300		1150		ns
SCK00 high-level width	tкн1	$4.0 V \le V_{DD} \le 5.0$ $C_b = 20 \text{ pF}, R_b = 0.0$	5 V, 2.7 V ≤ V₅ ≤ 4.0 V, = 1.4 kΩ	tксү1/2 – 50		tксү1/2 – 50		ns
		$2.7 V \le V_{DD} < 4$ $C_b = 20 \text{ pF}, R_b = 100 \text{ pF}$.0 V, 2.3 V ≤ V₅ ≤ 2.7 V, = 2.7 kΩ	tксү1/2 – 120		tксү1/2 – 120		ns
SCK00 low-level width	tĸ∟ı	$4.0 V \le V_{DD} \le 5.0$ $C_b = 20 \text{ pF}, R_b \le 0.0$	5 V, 2.7 V ≤ V₅ ≤ 4.0 V, = 1.4 kΩ	tксү1/2 – 7		tксү1/2 – 50		ns
		$2.7 V \le V_{DD} < 4$ $C_b = 20 \text{ pF}, R_b = 100 \text{ pF}$.0 V, 2.3 V ≤ V _b ≤ 2.7 V, = 2.7 kΩ	tксү1/2 – 10		tксү1/2 – 50		ns
SI00 setup time (to SCK00↑) ^{Note 1}	tsıĸı	$4.0 V \le V_{DD} \le 5.$ $C_b = 20 \text{ pF}, R_b \le 5.$.5 V, 2.7 V ≤ V _b ≤ 4.0 V, = 1.4 kΩ	58		479		ns
		$2.7 V \le V_{DD} < 4$ $C_b = 20 \text{ pF}, R_b = 100 \text{ pF}$.0 V, 2.3 V ≤ V₅ ≤ 2.7 V, = 2.7 kΩ	121		479		ns
SI00 hold time (from SCK00↑) ^{Note 1}	tksi1	$4.0 V \le V_{DD} \le 5.$ $C_b = 20 \text{ pF}, R_b \le 5.$	5 V, 2.7 V ≤ V₅ ≤ 4.0 V, = 1.4 kΩ	10		10		ns
		2.7 V ≤ V _{DD} < 4 C _b = 20 pF, R _b =	.0 V, 2.3 V ≤ V₅ ≤ 2.7 V, = 2.7 kΩ	10		10		ns
Delay time from SCK00↓ to SO00 output ^{Note 1}	tkso1	$4.0 V \le V_{DD} \le 5.0$ $C_b = 20 \text{ pF}, R_b \le 0.0$	5 V, 2.7 V ≤ V₅ ≤ 4.0 V, = 1.4 kΩ		60		60	ns
		2.7 V ≤ V _{DD} < 4 C _b = 20 pF, R _b :	.0 V, 2.3 V ≤ V₅ ≤ 2.7 V, = 2.7 kΩ		130		130	ns
SI00 setup time (to SCK00↓) ^{Note 2}	tsıkı	4.0 V ≤ V _{DD} ≤ 5. C _b = 20 pF, R _b =	5 V, 2.7 V ≤ V₅ ≤ 4.0 V, = 1.4 kΩ	23		110		ns
		$2.7 V \le V_{DD} < 4$ $C_b = 20 \text{ pF}, R_b = 100 \text{ pF}$.0 V, 2.3 V ≤ V₅ ≤ 2.7 V, = 2.7 kΩ	33		110		ns
SI00 hold time (from SCK00↓) ^{Note 2}	tksi1	$4.0 V \le V_{DD} \le 5.$ $C_b = 20 \text{ pF}, R_b \le 5.$	5 V, 2.7 V ≤ V₅ ≤ 4.0 V, = 1.4 kΩ	10		10		ns
		$2.7 V \le V_{DD} < 4$ $C_b = 20 \text{ pF}, R_b = 100 \text{ pF}$.0 V, 2.3 V ≤ V₅ ≤ 2.7 V, = 2.7 kΩ	10		10		ns
Delay time from SCK00↑ to SO00 output ^{Note 2}	tkso1	$4.0 V \le V_{DD} \le 5.$ $C_b = 20 \text{ pF}, R_b \le 5.$	5 V, 2.7 V ≤ V₅ ≤ 4.0 V, = 1.4 kΩ		10		10	ns
		2.7 V ≤ V _{DD} < 4 C _b = 20 pF, R _b :	.0 V, 2.3 V ≤ V₅ ≤ 2.7 V, = 2.7 kΩ		10		10	ns

 $(T_A = -40 \text{ to } +85^{\circ}\text{C}, 2.7 \text{ V} \le \text{V}_{DD} \le 5.5 \text{ V}, \text{V}_{SS} = 0 \text{ V})$

(Notes, Caution, and Remarks are listed on the next page.)

Notes 1. When DAP00 = 0 and CKP00 = 0, or DAP00 = 1 and CKP00 = 1

- **2.** When DAP00 = 0 and CKP00 = 1, or DAP00 = 1 and CKP00 = 0.
- Caution Select the TTL input buffer for the SI00 pin and the N-ch open drain output (VDD tolerance) mode for the SO00 pin and SCK00 pin by using port input mode register 1 (PIM1) and port output mode register 1 (POM1). For VIH and VIL, see the DC characteristics with TTL input buffer selected.
- **Remarks 1.** R_b [Ω]:Communication line (SCK00, SO00) pull-up resistance, C_b [F]: Communication line (SCK00, SO00) load capacitance, V_b [V]: Communication line voltage
 - fMCK: Serial array unit operation clock frequency (Operation clock to be set by the serial clock select register 0 (SPS0) and the CKS00 bit of serial mode register 00 (SMR00).)



(8) Communication at different potential (1.8 V, 2.5 V, 3 V) (CSI mode) (master mode, SCKp... internal clock output) (1/3)

Parameter	Symbol		Conditions	HS (high-spe Mode	,	LS (low-spee Mode	'	Unit
				MIN.	MAX.	MIN.	MAX.	
SCKp cycle time	tксү	tксү1 ≥ 4/fclк	$4.0 \text{ V} \le \text{V}_{\text{DD}} \le 5.5 \text{ V},$	300		1150		ns
			$2.7 \text{ V} \leq \text{V}_{b} \leq 4.0 \text{ V},$					
			C_b = 30 pF, R_b = 1.4 k Ω					
			$2.7 \text{ V} \le \text{V}_{\text{DD}} < 4.0 \text{ V},$	500		1150		ns
			$2.3 \text{ V} \leq \text{V}_{\text{b}} \leq 2.7 \text{ V},$					
			C_b = 30 pF, R_b = 2.7 k Ω					
			$1.8 \text{ V} \le \text{V}_{\text{DD}} < 3.3 \text{ V},$	1150		1150		ns
			1.6 V \leq V _b \leq 2.0 V ^{Note} ,					
			C_b = 30 pF, R_b = 5.5 k Ω					
SCKp high-level width	t кн1	$\label{eq:VDD} \begin{array}{l} 4.0 \ V \leq V_{DD} \leq 5.5 \ V, \ 2.7 \ V \leq V_b \leq 4.0 \ V, \\ \\ C_b = 30 \ pF, \ R_b = 1.4 \ k\Omega \end{array}$		tксү1/2 –75		tксү1/2–75		ns
		$2.7 V \leq V_{DD} <$	4.0 V, 2.3 V \leq V _b \leq 2.7 V,	tксү1/2-170		tксү1/2–170		ns
		C _b = 30 pF, R	_b = 2.7 kΩ					
		1.8 V ≤ V _{DD} <	3.3 V, 1.6 V \leq V_b \leq 2.0 V ^{Note} ,	tксү1/2 –458		tkcy1/2-458		ns
		C _b = 30 pF, R	_b = 5.5 kΩ					
SCKp low-level width	t KL1	$4.0 \text{ V} \leq \text{V}_{\text{DD}} \leq$	5.5 V, 2.7 V \leq V _b \leq 4.0 V,	tксү1/2 –12		tксү1/2–50		ns
		C _b = 30 pF, R	_b = 1.4 kΩ					
		2.7 V ≤ V _{DD} <	4.0 V, 2.3 V \leq V _b \leq 2.7 V,	tксү1/2 –18		tксү1/2–50		ns
		C₀ = 30 pF, R	_b = 2.7 kΩ					
		1.8 V ≤ V _{DD} <	3.3 V, 1.6 V \leq V _b \leq 2.0 V ^{Note} ,	tксү1/2 –50		tксү1/2–50		ns
		C₀ = 30 pF, R	_b = 5.5 kΩ					

 $(T_A = -40 \text{ to } +85^{\circ}\text{C}, 1.8 \text{ V} \le \text{V}_{DD} \le \text{V}_{DD} \le 5.5 \text{ V}, \text{V}_{SS} = 0 \text{ V})$

Note Use it with $V_{DD} \ge V_b$.

- Cautions 1. Select the TTL input buffer for the SIp pin and the N-ch open drain output (V_{DD} tolerance) mode for the SOp pin and SCKp pin by using port input mode register 1 (PIM1) and port output mode register 1 (POM1). For V_{IH} and V_{IL}, see the DC characteristics with TTL input buffer selected.
 CSI01 and CSI11 cannot communicate at different potential.
- **Remarks 1.** R_b [Ω]: Communication line (SCKp, SOp) pull-up resistance, C_b [F]: Communication line (SCKp, SOp) load capacitance, V_b [V]: Communication line voltage
 - **2.** p: CSI number (p = 00, 20)



(8) Communication at different potential (1.8 V, 2.5 V, 3 V) (CSI mode) (master mode, SCKp... internal clock output) (2/3)

Parameter	Symbol	Conditions	、 U	h-speed Mode		v-speed Mode	Unit
			MIN.	MAX.	MIN.	MAX.	
SIp setup time (to SCKp↑) ^{Note 1}	tsıĸı	$\begin{array}{l} 4.0 \; V \leq V_{DD} \leq 5.5 \; V, \; 2.7 \; V \leq V_b \leq 4.0 \; V, \\ C_b = 30 \; pF, \; R_b = 1.4 \; k\Omega \end{array}$	81		479		ns
		$\begin{array}{l} 2.7 \; V \leq V_{DD} < 4.0 \; V, \; 2.3 \; V \leq V_b \leq 2.7 \; V, \\ C_b = 30 \; pF, \; R_b = 2.7 \; k\Omega \end{array}$	177		479		ns
		$\label{eq:VDD} \begin{split} 1.8 \ V \leq V_{DD} < 3.3 \ V, \ 1.6 \ V \leq V_b \leq 2.0 \ V^{\mbox{Note 2}}, \\ C_b = 30 \ pF, \ R_b = 5.5 \ k\Omega \end{split}$	479		479		ns
SIp hold time (from SCKp↑) ^{Note 1}	tksi1	$\begin{array}{l} 4.0 \; V \leq V_{DD} \leq 5.5 \; V, \; 2.7 \; V \leq V_b \leq 4.0 \; V, \\ C_b = 30 \; pF, \; R_b = 1.4 \; k\Omega \end{array}$	19		19		ns
		$\begin{array}{l} 2.7 \; V \leq V_{DD} < 4.0 \; V, \; 2.3 \; V \leq V_b \leq 2.7 \; V, \\ C_b = 30 \; pF, \; R_b = 2.7 \; k\Omega \end{array}$	19		19		ns
		$\label{eq:VDD} \begin{array}{l} 1.8 \mbox{ V} \leq \mbox{ V}_{\rm DD} < 3.3 \mbox{ V}, \ 1.6 \mbox{ V} \leq \mbox{ V}_{\rm b} \leq 2.0 \mbox{ V}^{\mbox{ Note } 2}, \\ C_{\rm b} = 30 \mbox{ pF}, \ R_{\rm b} = 5.5 \mbox{ k}\Omega \end{array}$	19		19		ns
Delay time from SCKp↓ to	tkso1			100		100	ns
SOp output ^{Note 1}		$\label{eq:VDD} \begin{array}{l} 2.7 \; V \leq V_{DD} < 4.0 \; V, \; 2.3 \; V \leq V_b \leq 2.7 \; V, \\ C_b = 30 \; pF, \; R_b = 2.7 \; k\Omega \end{array}$		195		195	ns
		$\label{eq:VDD} \begin{split} 1.8 \ V \leq V_{\text{DD}} < 3.3 \ V, \ 1.6 \ V \leq V_{\text{b}} \leq 2.0 \ V^{\text{Note 2}}, \\ C_{\text{b}} = 30 \ p\text{F}, \ R_{\text{b}} = 5.5 \ k\Omega \end{split}$		483		483	ns

 $(T_A = -40 \text{ to } +85^{\circ}\text{C}, 1.8 \text{ V} \le V_{DD} \le 5.5 \text{ V}, \text{ V}_{SS} = 0 \text{ V})$

Notes 1. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1.

2. Use it with $V_{DD} \ge V_b$.

(Cautions and Remarks are listed on the next page.)



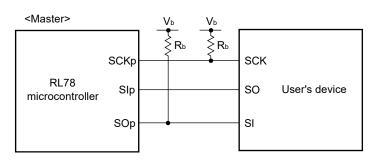
(8) Communication at different potential (1.8 V, 2.5 V, 3 V) (CSI mode) (master mode, SCKp... internal clock output) (3/3)

Parameter	Symbol	Conditions		HS (high-speed main) Mode		v-speed Mode	Unit
			MIN.	MAX.	MIN.	MAX.	
SIp setup time (to SCKp↓) ^{Note 1}	tsıĸı		44		110		ns
		$ \begin{array}{l} 2.7 \ V \leq V_{DD} < 4.0 \ V, \ 2.3 \ V \leq V_b \leq 2.7 \ V, \\ C_b = 30 \ pF, \ R_b = 2.7 \ k\Omega \end{array} $	44		110		ns
			110		110		ns
SIp hold time (from SCKp↓) ^{Note 1}	tksi1		19		19		ns
		$ 2.7 V \le V_{DD} < 4.0 V, 2.3 V \le V_b \le 2.7 V, \\ C_b = 30 \text{ pF}, R_b = 2.7 \text{ k}\Omega $	19		19		ns
		$\label{eq:VD} \begin{split} 1.8 \ V \leq V_{DD} < 3.3 \ V, \ 1.6 \ V \leq V_b \leq 2.0 \ V \ ^{\text{Note 2}}, \\ C_b = 30 \ pF, \ R_b = 5.5 \ k\Omega \end{split}$	19		19		ns
Delay time from SCKp↑ to	tkso1			25		25	ns
SOp output ^{Note 1}		$\label{eq:VD} \begin{array}{l} 2.7 \ V \leq V_{DD} < 4.0 \ V, \ 2.3 \ V \leq V_b \leq 2.7 \ V, \\ C_b = 30 \ pF, \ R_b = 2.7 \ k\Omega \end{array}$		25		25	ns
		$\label{eq:VD} \begin{split} 1.8 \ V \leq V_{\text{DD}} < 3.3 \ V, \ 1.6 \ V \leq V_{\text{b}} \leq 2.0 \ V^{\text{Note 2}}, \\ C_{\text{b}} = 30 \ p\text{F}, \ R_{\text{b}} = 5.5 \ k\Omega \end{split}$		25		25	ns

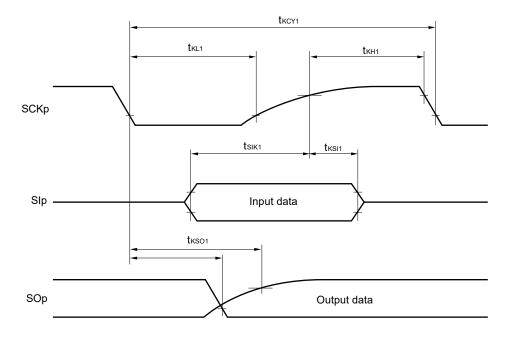
 $(T_A = -40 \text{ to } +85^{\circ}\text{C}, 1.8 \text{ V} \le \text{V}_{DD} \le 5.5 \text{ V}, \text{V}_{SS} = 0 \text{ V})$

- **Notes 1.** When DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
 - **2.** Use it with $V_{DD} \ge V_b$.
- Cautions 1. Select the TTL input buffer for the SIp pin and the N-ch open drain output (V_{DD} tolerance) mode for the SOp pin and SCKp pin by using port input mode register 1 (PIM1) and port output mode register 1 (POM1). For V_{IH} and V_{IL}, see the DC characteristics with TTL input buffer selected.
 - 2. CSI01 and CSI11 cannot communicate at different potential.
- **Remarks 1.** R_b [Ω]: Communication line (SCKp, SOp) pull-up resistance, C_b [F]: Communication line (SCKp, SOp) load capacitance, V_b [V]: Communication line voltage
 - **2.** p: CSI number (p = 00, 20), m: Unit number (m = 0, 1), n: Channel number (n = 0)

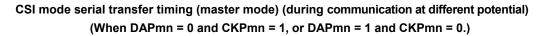
CSI mode connection diagram (during communication at different potential)

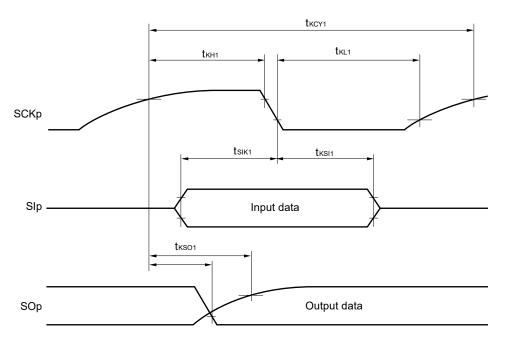






CSI mode serial transfer timing (master mode) (during communication at different potential) (When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1)







SCKp high-/low-level

SIp setup time

SIp hold time

(from SCKp↑) Note 4

Delay time from

SCKp↓ to SOp

output Note 5

(to SCKp↑) Note 3

width

Parameter	Symbol	Symbol Conditions		HS (high-speed main) Mode		LS (low-spe Moo	,	Unit
				MIN.	MAX.	MIN.	MAX.	
SCKp cycle time ^{Note 1}	t ксү2	$4.0 \text{ V} \le \text{V}_{\text{DD}} \le 5.5 \text{ V},$	20 MHz < fмск ≤ 24 MHz	12/f мск		_		ns
		$2.7~V \leq V_b \leq 4.0~V$	8 MHz < fмск ≤ 20 MHz	10/f мск		_		ns
			4 MHz < fмск ≤ 8 MHz	8/fмск		16/ f мск		ns
			fмск ≤ 4 MHz	6/fмск		10/ f мск		ns
		$2.7 \text{ V} \le \text{V}_{\text{DD}} < 4.0 \text{ V},$	20 MHz < fмск ≤ 24 MHz	16/f мск		_		ns
		$2.3~V \leq V_b \leq 2.7~V$	16 MHz < fмск ≤ 20 MHz	14/f мск		_		ns
			8 MHz < fмск ≤ 16 MHz	12/f мск		_		ns
			4 MHz < fмск ≤ 8 MHz	8/fмск		16/ f мск		ns
			fмск ≤ 4 MHz	6/fмск		10/ f мск		ns
		$1.8 V \le V_{DD} < 3.3 V$,	20 MHz < fмск ≤ 24 MHz	36/fмск		_		ns
		$1.6 \text{ V} \le \text{V}_{b} \le 2.0 \text{ V}$	16 MHz < fмск ≤ 20 MHz	32/fмск		_		ns
		Note 2	8 MHz < fмск ≤ 16 MHz	26/f мск		_		ns
			4 MHz < fмск ≤ 8 MHz	16/fмск		16/fмск		ns

fмск ≤ 4 MHz

 $4.0 \text{ V} \le \text{V}_{\text{DD}} \le 5.5 \text{ V}, 2.7 \text{ V} \le \text{V}_{\text{b}} \le 4.0 \text{ V}$

 $2.7 \text{ V} \le \text{V}_{\text{DD}} < 4.0 \text{ V}, 2.3 \text{ V} \le \text{V}_{\text{b}} \le 2.7 \text{ V}$

 $4.0 \text{ V} \le \text{V}_{\text{DD}} \le 5.5 \text{ V}, 2.7 \text{ V} \le \text{V}_{\text{DD}} \le 4.0 \text{ V}$

 $2.7 \text{ V} \le \text{V}_{\text{DD}} < 4.0 \text{ V}, 2.3 \text{ V} \le \text{V}_{\text{b}} \le 2.7 \text{ V}$

 $4.0 \text{ V} \le \text{V}_{\text{DD}} \le 5.5 \text{ V}, 2.7 \text{ V} \le \text{V}_{\text{b}} \le 4.0 \text{ V},$

 $2.7 \text{ V} \le \text{V}_{\text{DD}} < 4.0 \text{ V}, 2.3 \text{ V} \le \text{V}_{\text{b}} \le 2.7 \text{ V},$

 $1.8 \text{ V} \le \text{V}_{\text{DD}} < 3.3 \text{ V}, \ 1.6 \text{ V} \le \text{V}_{\text{b}} \le 2.0 \text{ V}^{\text{Note 2}},$

 $C_b = 30 \text{ pF}, R_b = 1.4 \text{ k}\Omega$

 $C_b = 30 \text{ pF}, R_b = 2.7 \text{ k}\Omega$

 $C_b = 30 \text{ pF}, R_b = 5.5 \text{ k}\Omega$

 $1.8 \text{ V} \le \text{V}_{\text{DD}} < 3.3 \text{ V}, 1.6 \text{ V} \le \text{V}_{\text{b}} \le 2.0 \text{ V}^{\text{Note 2}}$

 $1.8 \text{ V} \le \text{V}_{\text{DD}} < 3.3 \text{ V}, 1.6 \text{ V} \le \text{V}_{\text{DD}} \le 2.0 \text{ V}^{\text{Note 2}}$

10/fмск

tkcy2/2 - 12

tkcy2/2 - 18

tkcy2/2 - 50

1/fмск + 20

1/fмск + 20

1/fмск + 30

1/fмск + 31

2/fмск +

120

2/fмск +

214

2/fмск +

573

10/fмск

tkcy2/2 - 50

tkcy2/2-50

tkcy2/2 - 50

1/fмск + 30

1/fмск + 30

1/fмск + 30

1/fмск + 31

ns

2/fмск +

573

2/fмск +

573

2/fмск +

573

(9) Communication at different potential (1.8 V, 2.5 V, 3 V) (CSI mode) (slave mode, SCKp... external clock input) ($T_A = -40$ to +85°C, 1.8 V \leq V_{DD} \leq 5.5 V, V_{SS} = 0 V)

Notes 1. Transfer rate in the SNOOZE mode: MAX. 1 Mbps

2. Use it with $V_{DD} \ge V_b$.

t_{KH2}.

tKI 2

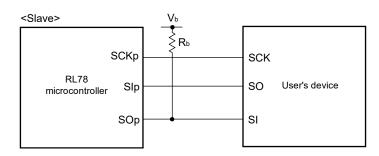
tsik2

tksi2

tĸso2

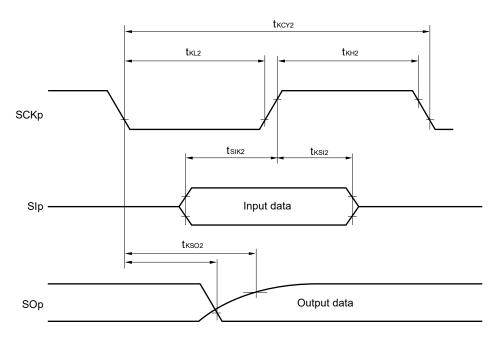
- **3.** When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The SIp setup time becomes "to SCKp↓" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
- **4.** When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The SIp hold time becomes "from SCKp↓" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
- 5. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The delay time to SOp output becomes "from SCKp↑" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
- Cautions 1. Select the TTL input buffer for the SIp and SCKp pins and the N-ch open drain output (VDD tolerance) mode for the SOp pin by using port input mode register 1 (PIM1) and port output mode register 1 (POM1). For VIH and VIL, see the DC characteristics with TTL input buffer selected.
 - 2. CSI01 and CSI11 cannot communicate at different potential.

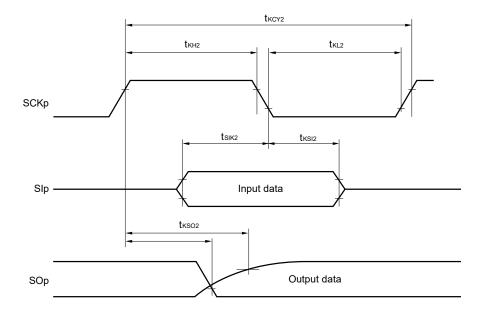
CSI mode connection diagram (during communication at different potential)



- **Remarks 1.** R_b [Ω]: Communication line (SOp) pull-up resistance, C_b [F]: Communication line (SOp) load capacitance, V_b [V]: Communication line voltage
 - **2.** p: CSI number (p = 00, 20), m: Unit number (m = 0, 1), n: Channel number (n = 0)
 - fMCK: Serial array unit operation clock frequency (Operation clock to be set by the serial clock select register m (SPSm) and the CKSmn bit of serial mode register mn (SMRmn). m: Unit number, n: Channel number (mn = 00, 10))

CSI mode serial transfer timing (slave mode) (during communication at different potential) (When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1.)





CSI mode serial transfer timing (slave mode) (during communication at different potential) (When DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.)

Remark p: CSI number (p = 00, 20), m: Unit number (m = 0, 1), n: Channel number (n = 0)



(10) Communication at different potential (1.8 V, 2.5 V, 3 V) (simplified l²C mode) (T_A = -40 to +85°C, 1.8 V \leq V_{DD} \leq 5.5 V, V_{SS} = 0 V)

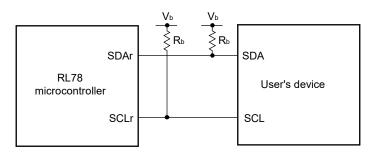
Parameter	Symbol	Conditions		h-speed Mode	-	v-speed Mode	Unit
			MIN.	MAX.	MIN.	MAX.	
SCLr clock frequency	fsc∟	$\begin{array}{l} 4.0 \ V \leq V_{\text{DD}} \leq 5.5 \ V, \ 2.7 \ V \leq V_{\text{b}} \leq 4.0 \ V, \\ C_{\text{b}} = 100 \ p\text{F}, \ R_{\text{b}} = 2.8 \ \text{k}\Omega \end{array}$		400 ^{Note1}		300 ^{Note1}	kHz
		$\begin{array}{l} 2.7 \ V \leq V_{DD} < 4.0 \ V, \ 2.3 \ V \leq V_b \leq 2.7 \ V, \\ C_b = 100 \ pF, \ R_b = 2.7 \ k\Omega \end{array}$		400 ^{Note1}		300 ^{Note1}	kHz
		$1.8 \text{ V} \le \text{V}_{\text{DD}} < 3.3 \text{ V}, 1.6 \text{ V} \le \text{V}_{\text{b}} \le 2.0 \text{ V}, \frac{\text{Note2}}{\text{C}_{\text{b}}} = 100 \text{ pF}, \text{R}_{\text{b}} = 5.5 \text{ k}\Omega$		300 ^{Note1}		300 ^{Note1}	kHz
Hold time when SCLr = "L"	tLow	$\begin{array}{l} 4.0 \ V \leq V_{\text{DD}} \leq 5.5 \ \text{V}, \ 2.7 \ \text{V} \leq V_{\text{b}} \leq 4.0 \ \text{V}, \\ \text{C}_{\text{b}} = 100 \ \text{pF}, \ \text{R}_{\text{b}} = 2.8 \ \text{k}\Omega \end{array}$	1150		1550		ns
		$\begin{array}{l} 2.7 \ V \leq V_{DD} < 4.0 \ V, \ 2.3 \ V \leq V_b \leq 2.7 \ V, \\ C_b = 100 \ pF, \ R_b = 2.7 \ k\Omega \end{array}$	1150		1550		ns
		$1.8 V \le V_{DD} < 3.3 V, 1.6 V \le V_b \le 2.0 V,^{Note2}$ C _b = 100 pF, R _b = 5.5 kΩ	1550		1550		ns
Hold time when SCLr = "H"	tніgн	$\begin{array}{l} 4.0 \; V \leq V_{DD} \leq 5.5 \; V, 2.7 \; V \leq V_b \leq 4.0 \; V, \\ C_b = 100 \; pF, \; R_b = 2.8 \; k\Omega \end{array}$	675		610		ns
		$\begin{array}{l} 2.7 \ V \leq V_{DD} < 4.0 \ V, \ 2.3 \ V \leq V_b \leq 2.7 \ V, \\ C_b = 100 \ pF, \ R_b = 2.7 \ k\Omega \end{array}$	600		610		ns
		1.8 V \leq V _{DD} < 3.3 V, 1.6 V \leq V _b \leq 2.0 V, ^{Note2} C _b = 100 pF, R _b = 5.5 kΩ	610		610		ns
Data setup time (reception)	tsu:dat	4.0 V \leq V _{DD} \leq 5.5 V, 2.7 V \leq V _b \leq 4.0 V, C _b = 100 pF, R _b = 2.8 kΩ	1/fмск + 190 Note3		1/fмск + 190 Note3		ns
		$2.7 V \le V_{DD} < 4.0 V, 2.3 V \le V_b \le 2.7 V,$ $C_b = 100 \text{ pF}, R_b = 2.7 \text{ k}\Omega$	1/fмск + 190 Note3		1/fмск + 190 Note3		ns
		$\label{eq:VDD} \begin{array}{l} 1.8 \ V \leq V_{\text{DD}} < 3.3 \ V, \ 1.6 \ V \leq V_{\text{b}} \leq 2.0 \ V, \\ Note2 \\ C_{\text{b}} = 100 \ p\text{F}, \ R_{\text{b}} = 5.5 \ \text{k}\Omega \end{array}$	1/fмск + 190 Note3		1/fмск + 190 Note3		ns
Data hold time (transmission)	thd:dat	$\begin{array}{l} 4.0 \; V \leq V_{DD} \leq 5.5 \; V, 2.7 \; V \leq V_b \leq 4.0 \; V, \\ C_b = 100 \; pF, \; R_b = 2.8 \; k\Omega \end{array}$	0	355	0	355	ns
		$\begin{array}{l} 2.7 \ V \leq V_{\text{DD}} < 4.0 \ V, \ 2.3 \ V \leq V_{\text{b}} \leq 2.7 \ V, \\ C_{\text{b}} = 100 \ \text{pF}, \ R_{\text{b}} = 2.7 \ \text{k}\Omega \end{array}$	0	355	0	355	ns
		$\begin{array}{l} 1.8 \ V \leq V_{DD} < 3.3 \ V, \ 1.6 \ V \leq V_b \leq 2.0 \ V, \\ \mbox{Note2} \\ C_b = 100 \ pF, \ R_b = 5.5 \ k\Omega \end{array}$	0	405	0	405	ns

Notes 1. The value must be equal to or less than $f_{MCK}/4$.

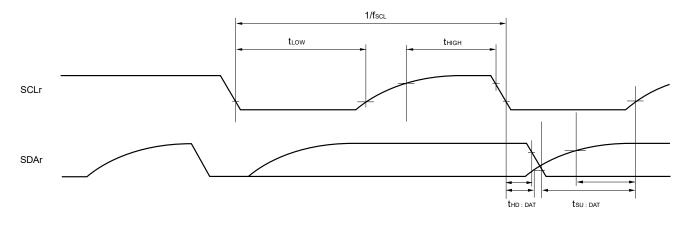
- **2.** Use it with $V_{DD} \ge V_b$.
- 3. Set tsu:DAT so that it will not exceed the hold time when SCLr = "L" or SCLr = "H".
- Cautions 1. Select the TTL input buffer and the N-ch open drain output (V_{DD} tolerance) mode for the SDAr pin and the N-ch open drain output (V_{DD} tolerance) mode for the SCLr pin by using port input mode register 1 (PIM1) and port output mode register 1 (POM1). For V_{IH} and V_{IL}, see the DC characteristics with TTL input buffer selected.
 - 2. IIC01 and IIC11 cannot communicate at different potential.

(**Remarks** are listed on the next page.)

Simplified I²C mode connection diagram (during communication at different potential)



Simplified I²C mode serial transfer timing (during communication at different potential)



- **Remarks 1.** R_b [Ω]: Communication line (SDAr, SCLr) pull-up resistance, C_b [F]: Communication line (SDAr, SCLr) load capacitance, V_b [V]: Communication line voltage
 - **2.** r: IIC Number (r = 00, 20)
 - fMCK: Serial array unit operation clock frequency (Operation clock to be set by the serial clock select register m (SPSm) and the CKSmn bit of serial mode register mn (SMRmn).
 m: Unit number (m = 0,1), n: Channel number (n = 0))
 - 4. Simplified I²C mode is supported only by the R5F102 products.



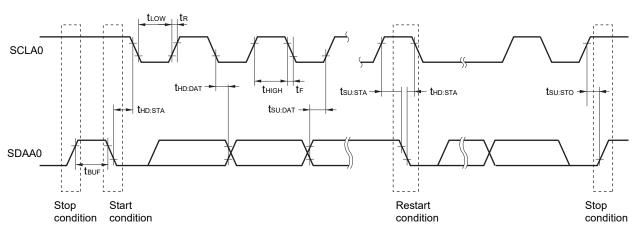
2.5.2 Serial interface IICA

Parameter	Symbol	Conditions	HS	(high-spee	ed main) m	node	Unit
			LS	(low-spee	d main) m	ode	
			Standa	rd Mode	Fast	Mode	
			MIN.	MAX.	MIN.	MAX.	
SCLA0 clock frequency	fscl	Fast mode: fc∟κ≥ 3.5 MHz			0	400	kHz
		Normal mode: fc∟κ≥ 1 MHz	0	100			kHz
Setup time of restart condition	tsu:sta		4.7		0.6		μs
Hold time ^{Note 1}	thd:sta		4.0		0.6		μs
Hold time when SCLA0 = "L"	t LOW		4.7		1.3		μs
Hold time when SCLA0 = "H"	tніgн		4.0		0.6		μs
Data setup time (reception)	tsu:dat		250		100		ns
Data hold time (transmission)Note 2	thd:dat		0	3.45	0	0.9	μs
Setup time of stop condition	tsu:sto		4.0		0.6		μs
Bus-free time	t BUF		4.7		1.3		μs

$(T_A = -40 \text{ to } +85^{\circ}\text{C}, 1.8 \text{ V} \le \text{V}_{DD} \le 5.5 \text{ V}, \text{V}_{SS} = 0 \text{ V})$

Notes 1. The first clock pulse is generated after this period when the start/restart condition is detected.

- Caution Only in the 30-pin products, the values in the above table are applied even when bit 2 (PIOR2) in the peripheral I/O redirection register (PIOR) is 1. At this time, the pin characteristics (IOH1, IOL1, VOH1, VOL1) must satisfy the values in the redirect destination.
- **Remark** The maximum value of Cb (communication line capacitance) and the value of Rb (communication line pull-up resistor) at that time in each mode are as follows.



IICA serial transfer timing



^{2.} The maximum value (MAX.) of the during normal transfer and a wait state is inserted in the ACK (acknowledge) timing.

2.6 Analog Characteristics

2.6.1 A/D converter characteristics

Classification of A/D converter characteristics

Input channel		Reference Voltage	
	Reference voltage (+) = AVREFP Reference voltage (–) = AVREFM	Reference voltage (+) = V _{DD} Reference voltage (–) = Vss	Reference voltage (+) = VBGR Reference voltage (–) = AVREFM
ANI0 to ANI3	Refer to 2.6.1 (1) .	Refer to 2.6.1 (3) .	Refer to 2.6.1 (4) .
ANI16 to ANI22	Refer to 2.6.1 (2) .		
Internal reference voltage	Refer to 2.6.1 (1) .		-
Temperature sensor output voltage			

(1) When reference voltage (+) = AV_{REFP}/ANI0 (ADREFP1 = 0, ADREFP0 = 1), reference voltage (-) = AV_{REFM}/ANI1 (ADREFM = 1), target pin: ANI2, ANI3, internal reference voltage, and temperature sensor output voltage

$(T_A = -40 \text{ to } +85^{\circ}\text{C}, 1.8 \text{ V} \le \text{AV}_{REFP} \le \text{VDD} \le 5.5 \text{ V}, \text{ V}_{SS} = 0 \text{ V}, \text{ Reference voltage (+)} = \text{AV}_{REFP}, \text{ Reference voltage (-)} = \text{AV}_{REFM} = 0 \text{ V})$

Parameter	Symbol	Cor	nditions	MIN.	TYP.	MAX.	Unit
Resolution	RES			8		10	bit
Overall error ^{Note 1}	AINL	10-bit resolution			1.2	±3.5	LSB
		AV _{REFP} = V _{DD} ^{Note 3}			1.2	±7.0 Note 4	LSB
Conversion time	t CONV	10-bit resolution	$3.6 \text{ V} \leq \text{V}_{\text{DD}} \leq 5.5 \text{ V}$	2.125		39	μs
		Target pin: ANI2, ANI3	2.7 V ≤ VDD ≤ 5.5 V	3.1875		39	μs
			1.8 V ≤ VDD ≤ 5.5 V	17		39	μs
				57		95	μs
		10-bit resolution	$3.6 \text{ V} \leq \text{V}_{DD} \leq 5.5 \text{ V}$	2.375		39	μs
		Target pin: Internal	2.7 V ≤ VDD ≤ 5.5 V	3.5625		39	μs
	output voltage (HS (high-speed m mode)	temperature sensor output voltage (HS (high-speed main)	2.4 V ≤ V _{DD} ≤ 5.5 V	17		39	μs
Zero-scale error ^{Notes 1, 2}	EZS	10-bit resolution				±0.25	%FSR
		AV _{REFP} = V _{DD} Note 3				±0.50 ^{Note 4}	%FSR
Full-scale error ^{Notes 1, 2}	EFS	10-bit resolution				±0.25	%FSR
		AV _{REFP} = V _{DD} ^{Note 3}				±0.50 ^{Note 4}	%FSR
Integral linearity error ^{Note 1}	ILE	10-bit resolution				±2.5	LSB
		AV _{REFP} = V _{DD} ^{Note 3}				±5.0 Note 4	LSB
Differential linearity error	DLE	10-bit resolution				±1.5	LSB
Note 1		AV _{REFP} = V _{DD} ^{Note 3}				±2.0 Note 4	LSB
Analog input voltage	VAIN	ANI2, ANI3		0		AVREFP	V
		Internal reference voltage (2.4 V ≤ V _{DD} ≤ 5.5 V, HS		VBGR Note 5		V	
		Temperature sensor outp (2.4 V \leq VDD \leq 5.5 V, HS	ut voltage (high-speed main) mode)	Ň	VTMPS25 Note	5	V

(Notes are listed on the next page.)



- **Notes 1.** Excludes quantization error (±1/2 LSB).
 - 2. This value is indicated as a ratio (%FSR) to the full-scale value.
 - 3. When AV_{REFP} < V_{DD}, the MAX. values are as follows. Overall error: Add ±1.0 LSB to the MAX. value when AV_{REFP} = V_{DD}. Zero-scale error/Full-scale error: Add ±0.05%FSR to the MAX. value when AV_{REFP} = V_{DD}. Integral linearity error/ Differential linearity error: Add ±0.5 LSB to the MAX. value when AV_{REFP} = V_{DD}.
 - 4. Values when the conversion time is set to 57 μs (min.) and 95 μs (max.).
 - 5. Refer to 2.6.2 Temperature sensor/internal reference voltage characteristics.
- (2) When reference voltage (+) = AVREFP/ANI0 (ADREFP1 = 0, ADREFP0 = 1), reference voltage (-) = AVREFM/ANI1 (ADREFM = 1), target pin: ANI16 to ANI22

 $(T_A = -40 \text{ to } +85^{\circ}\text{C}, 1.8 \text{ V} \le \text{AV}_{REFP} \le \text{V}_{DD} \le 5.5 \text{ V}, \text{ V}_{SS} = 0 \text{ V}, \text{ Reference voltage (+)} = \text{AV}_{REFP}, \text{ Reference voltage (-)} = \text{AV}_{REFM} = 0 \text{ V})$

Parameter	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Resolution	Res			8		10	bit
Overall error Note 1	AINL	10-bit resolution			1.2	±5.0	LSB
		AV _{REFP} = V _{DD} ^{Note 3}			1.2	±8.5 Note 4	LSB
Conversion time	tCONV	$3.6 V \le V_{DD} \le 5.5 V$		2.125		39	μs
		Target ANI pin: ANI16 to ANI22	2.7 V ≤ VDD ≤ 5.5 V	3.1875		39	μs
			1.8 V ≤ VDD ≤ 5.5 V	17		39	μs
				57		95	μs
Zero-scale error Notes 1, 2	EZS	10-bit resolution				±0.35	%FSR
		AV _{REFP} = V _{DD} ^{Note 3}				±0.60 Note 4	%FSR
Full-scale error Notes 1, 2	EFS	10-bit resolution				±0.35	%FSR
		AV _{REFP} = V _{DD} ^{Note 3}				±0.60 Note 4	%FSR
Integral linearity error Note 1	ILE	10-bit resolution				±3.5	LSB
		AV _{REFP} = V _{DD} ^{Note 3}				±6.0 Note 4	LSB
Differential linearity	DLE	10-bit resolution				±2.0	LSB
error Note 1		AV _{REFP} = V _{DD} ^{Note 3}				±2.5 Note 4	LSB
Analog input voltage	VAIN	ANI16 to ANI22		0		AV _{REFP} and V _{DD}	V

Notes 1. Excludes quantization error (±1/2 LSB).

- 2. This value is indicated as a ratio (%FSR) to the full-scale value.
- 3. When AV_{REFP} ≤ V_{DD}, the MAX. values are as follows. Overall error: Add ±4.0 LSB to the MAX. value when AV_{REFP} = V_{DD}. Zero-scale error/Full-scale error: Add ±0.20%FSR to the MAX. value when AV_{REFP} = V_{DD}. Integral linearity error/ Differential linearity error: Add ±2.0 LSB to the MAX. value when AV_{REFP} = V_{DD}.
- 4. When the conversion time is set to 57 μs (min.) and 95 μs (max.).

(3) When reference voltage (+) = V_{DD} (ADREFP1 = 0, ADREFP0 = 0), reference voltage (-) = V_{ss} (ADREFM = 0), target pin: ANI0 to ANI3, ANI16 to ANI22, internal reference voltage, and temperature sensor output voltage

Parameter	Symbol	Condition	าร	MIN.	TYP.	MAX.	Unit
Resolution	Res			8		10	bit
Overall error ^{Note 1}	AINL	10-bit resolution			1.2	±7.0	LSB
					1.2	±10.5 ^{Note 3}	LSB
Conversion time	t CONV	10-bit resolution	$3.6 \text{ V} \leq \text{V}_{\text{DD}} \leq 5.5 \text{ V}$	2.125		39	μs
		Target pin: ANI0 to ANI3,	$2.7 \text{ V} \leq \text{V}_{\text{DD}} \leq 5.5 \text{ V}$	3.1875		39	μs
		ANI16 to ANI22	1.8 V ≤ V _{DD} ≤ 5.5 V	17		39	μs
				57		95	μs
Conversion time	t CONV	10-bit resolution	$3.6 \text{ V} \leq \text{V}_{\text{DD}} \leq 5.5 \text{ V}$	2.375		39	μs
		Target pin: internal reference	2.7 V ≤ VDD ≤ 5.5 V	3.5625		39	μs
		voltage, and temperature sensor output voltage (HS (high-speed main) mode)	2.4 V ≤ VDD ≤ 5.5 V	17		39	μs
Zero-scale error ^{Notes 1, 2}	EZS	10-bit resolution				±0.60	%FSR
						±0.85 Note 3	%FSR
Full-scale error ^{Notes 1, 2}	EFS	10-bit resolution				±0.60	%FSR
						±0.85 Note 3	%FSR
Integral linearity error ^{Note 1}	ILE	10-bit resolution				±4.0	LSB
						±6.5 Note 3	LSB
Differential linearity error Note 1	DLE	10-bit resolution				±2.0	LSB
						±2.5 Note 3	LSB
Analog input voltage	VAIN	ANI0 to ANI3, ANI16 to ANI2	2	0		Vdd	V
	Internal reference voltage $(2.4 \text{ V} \le \text{V}_{DD} \le 5.5 \text{ V}, \text{ HS} \text{ (high-speed main) mode)}$			V _{BGR} Note 4		V	
			Temperature sensor output voltage V_{TMPS25} Note 4 (2.4 V ≤ VDD ≤ 5.5 V, HS (high-speed main) mode) V				V

Notes 1. Excludes quantization error (±1/2 LSB).

2. This value is indicated as a ratio (%FSR) to the full-scale value.

3. When the conversion time is set to 57 μs (min.) and 95 μs (max.).

4. Refer to 2.6.2 Temperature sensor/internal reference voltage characteristics.

(4) When reference voltage (+) = Internal reference voltage (ADREFP1 = 1, ADREFP0 = 0), reference voltage (-) = AV_{REFM} (ADREFM = 1), target pin: ANI0, ANI2, ANI3, and ANI16 to ANI22

 $(T_A = -40 \text{ to } +85^{\circ}\text{C}, 2.4 \text{ V} \le \text{V}_{\text{DD}} \le 5.5 \text{ V}, \text{ V}_{\text{SS}} = 0 \text{ V}, \text{ Reference voltage (+)} = \text{V}_{\text{BGR}}^{\text{Note 3}}, \text{ Reference voltage (-)} = \text{AV}_{\text{REFM}}^{\text{Note 4}}$ Note ⁴= 0 V, HS (high-speed main) mode)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Resolution	Res			8		bit
Conversion time	t CONV	8-bit resolution	17		39	μs
Zero-scale error ^{Notes 1, 2}	EZS	8-bit resolution			±0.60	%FSR
Integral linearity error ^{Note 1}	ILE	8-bit resolution			±2.0	LSB
Differential linearity error Note 1	DLE	8-bit resolution			±1.0	LSB
Analog input voltage	VAIN		0		$V_{\text{BGR}}{}^{\text{Note 3}}$	V

Notes 1. Excludes quantization error (±1/2 LSB).

2. This value is indicated as a ratio (%FSR) to the full-scale value.

3. Refer to 2.6.2 Temperature sensor/internal reference voltage characteristics.

4. When reference voltage (–) = Vss, the MAX. values are as follows.

Zero-scale error: Add $\pm 0.35\%$ FSR to the MAX. value when reference voltage (–) = AV_{REFM}. Integral linearity error: Add ± 0.5 LSB to the MAX. value when reference voltage (–) = AV_{REFM}. Differential linearity error: Add ± 0.2 LSB to the MAX. value when reference voltage (–) = AV_{REFM}.



2.6.2 Temperature sensor/internal reference voltage characteristics

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Temperature sensor output voltage	VTMPS25	Setting ADS register = 80H, TA = +25°C		1.05		V
Internal reference voltage	VBGR	Setting ADS register = 81H	1.38	1.45	1.50	V
Temperature coefficient	Fvtmps	Temperature sensor output voltage that depends on the temperature		-3.6		mV/°C
Operation stabilization wait time	tamp		5			μs

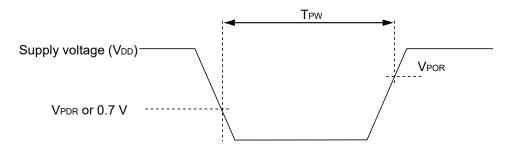
(T_A = -40 to +85°C, 2.4 V \leq V_{DD} \leq 5.5 V, V_{SS} = 0 V, HS (high-speed main) mode

2.6.3 POR circuit characteristics

$(T_A = -40 \text{ to } +85^{\circ}\text{C}, V_{\text{SS}} = 0 \text{ V})$

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Detection voltage	VPOR	Power supply rise time	1.47	1.51	1.55	V
	VPDR	Power supply fall time	1.46	1.50	1.54	V
Minimum pulse width Note	T _{PW}		300			μs

Note Minimum time required for a POR reset when V_{DD} exceeds below V_{PDR}. This is also the minimum time required for a POR reset from when V_{DD} exceeds below 0.7 V to when V_{DD} exceeds V_{POR} while STOP mode is entered or the main system clock is stopped through setting bit 0 (HIOSTOP) and bit 7 (MSTOP) in the clock operation status control register (CSC).





2.6.4 LVD circuit characteristics

LVD Detection Voltage of Reset Mode and Interrupt Mode

(T_A = -40 to +85°C, V_{PDR} \leq V_{DD} \leq 5.5 V, V_{SS} = 0 V)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Detection supply voltage	VLVD0	Power supply rise time	3.98	4.06	4.14	V
		Power supply fall time	3.90	3.98	4.06	V
	VLVD1	Power supply rise time	3.68	3.75	3.82	V
		Power supply fall time	3.60	3.67	3.74	V
	VLVD2	Power supply rise time	3.07	3.13	3.19	V
		Power supply fall time	3.00	3.06	3.12	V
	VLVD3	Power supply rise time	2.96	3.02	3.08	V
		Power supply fall time	2.90	2.96	3.02	V
	VLVD4	Power supply rise time	2.86	2.92	2.97	V
		Power supply fall time	2.80	2.86	2.91	V
	VLVD5	Power supply rise time	2.76	2.81	2.87	V
		Power supply fall time	2.70	2.75	2.81	V
	VLVD6	Power supply rise time	2.66	2.71	2.76	V
		Power supply fall time	2.60	2.65	2.70	V
	VLVD7	Power supply rise time	2.56	2.61	2.66	V
		Power supply fall time	2.50	2.55	2.60	V
	VLVD8	Power supply rise time	2.45	2.50	2.55	V
		Power supply fall time	2.40	2.45	2.50	V
	VLVD9	Power supply rise time	2.05	2.09	2.13	V
		Power supply fall time	2.00	2.04	2.08	V
	VLVD10	Power supply rise time	1.94	1.98	2.02	V
		Power supply fall time	1.90	1.94	1.98	V
	VLVD11	Power supply rise time	1.84	1.88	1.91	V
		Power supply fall time	1.80	1.84	1.87	V
Minimum pulse width	t∟w		300			μs
Detection delay time					300	μs



LVD detection voltage of interrupt & reset mode $(T_A = -40 \text{ to } +85^{\circ}\text{C}, V_{PDR} \le V_{DD} \le 5.5 \text{ V}, V_{SS} = 0 \text{ V})$

Parameter	Symbol		Con	ditions	MIN.	TYP.	MAX.	Unit
Interrupt and reset	VLVDB0	Vpoc2,	VPOC1, VPOC0 = 0, 0, 1, fal	ling reset voltage	1.80	1.84	1.87	V
mode	VLVDB1		LVIS1, LVIS0 = 1, 0	Rising reset release voltage	1.94	1.98	2.02	V
				Falling interrupt voltage	1.90	1.94	1.98	V
	VLVDB2		LVIS1, LVIS0 = 0, 1	Rising reset release voltage	2.05	2.09	2.13	V
				Falling interrupt voltage	2.00	2.04	2.08	V
	VLVDB3		LVIS1, LVIS0 = 0, 0	Rising reset release voltage	3.07	3.13	3.19	V
				Falling interrupt voltage	3.00	3.06	3.12	V
	VLVDC0	Vpoc2,	VPOC1, VPOC0 = 0, 1, 0, fal	ling reset voltage	2.40	2.45	2.50	V
	VLVDC1		LVIS1, LVIS0 = 1, 0	Rising reset release voltage	2.56	2.61	2.66	V
				Falling interrupt voltage	2.50	2.55	2.60	V
	VLVDC2		LVIS1, LVIS0 = 0, 1	Rising reset release voltage	2.66	2.71	2.76	V
				Falling interrupt voltage	2.60	2.65	2.70	V
	VLVDC3		LVIS1, LVIS0 = 0, 0	Rising reset release voltage	3.68	3.75	3.82	V
				Falling interrupt voltage	3.60	3.67	3.74	V
	VLVDD0	Vpoc2,	VPOC1, VPOC1 = 0, 1, 1, fal	ling reset voltage	2.70	2.75	2.81	V
	VLVDD1		LVIS1, LVIS0 = 1, 0	Rising reset release voltage	2.86	2.92	2.97	V
				Falling interrupt voltage	2.80	2.86	2.91	V
	VLVDD2		LVIS1, LVIS0 = 0, 1	Rising reset release voltage	2.96	3.02	3.08	V
				Falling interrupt voltage	2.90	2.96	3.02	V
	VLVDD3		LVIS1, LVIS0 = 0, 0	Rising reset release voltage	3.98	4.06	4.14	V
				Falling interrupt voltage	3.90	3.98	4.06	V

2.6.5 Power supply voltage rising slope characteristics

$(T_A = -40 \text{ to } +85^{\circ}C, V_{SS} = 0 \text{ V})$

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Power supply voltage rising slope	SVDD				54	V/ms

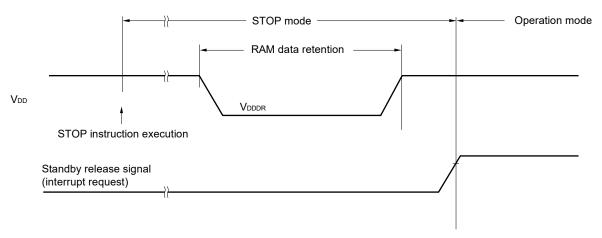
Caution Make sure to keep the internal reset state by the LVD circuit or an external reset until V_{DD} reaches the operating voltage range shown in 2.4 AC Characteristics.

2.7 RAM Data Retention Characteristics

$(T_A = -40 \text{ to } +85^{\circ}\text{C}, V_{SS} = 0 \text{ V})$

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Data retention supply voltage	VDDDR		1.46 Note		5.5	V

Note This depends on the POR detection voltage. For a falling voltage, data in RAM are retained until the voltage reaches the level that triggers a POR reset but not once it reaches the level at which a POR reset is generated.



2.8 Flash Memory Programming Characteristics

$(T_A = -40 \text{ to } +85^{\circ}\text{C}, 1.8 \text{ V} \le V_{DD} \le 5.5 \text{ V}, \text{ V}_{SS} = 0 \text{ V})$

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
System clock frequency	fclĸ		1		24	MHz
Code flash memory rewritable times Notes 1, 2, 3	Cerwr	Retained for 20 years T _A = 85°C	1,000			Times
Data flash memory rewritable times Notes 1, 2, 3		Retained for 1 year T _A = 25°C		1,000,000		
		Retained for 5 years T _A = 85°C	100,000			
		Retained for 20 years T _A = 85°C	10,000			

Notes 1. 1 erase + 1 write after the erase is regarded as 1 rewrite. The retaining years are until next rewrite after the rewrite.

- 2. When using flash memory programmer and Renesas Electronics self programming library
- **3.** These are the characteristics of the flash memory and the results obtained from reliability testing by Renesas Electronics Corporation.

2.9 Dedicated Flash Memory Programmer Communication (UART)

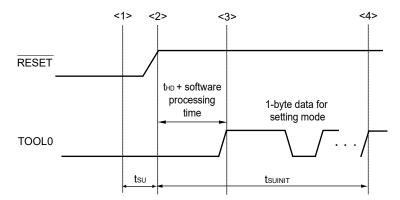
1	$(1_{A} = -40 \text{ to } +85^{\circ}\text{C}, 1.8 \text{ V} \le \text{V}_{DD} \le 5.5 \text{ V}, \text{ V}_{SS} = 0 \text{ V})$										
	Parameter Symbol Conditions		MIN.	TYP.	MAX.	Unit					
	Transfer rate		During serial programming	115,200		1,000,000	bps				

· 0 = 0 0 4 0 1/ 4 1/

2.10 Timing of Entry to Flash Memory Programming Modes

$(T_A = -40 \text{ to } +85^{\circ}\text{C}, 1.8 \text{ V} \le \text{V}_{DD} \le 5.5 \text{ V}, \text{V}_{SS} = 0 \text{ V})$

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Time to complete the communication for the initial setting after the external reset is released	tsuinit	POR and LVD reset are released before external reset release			100	ms
Time to release the external reset after the TOOL0 pin is set to the low level	tsu	POR and LVD reset are released before external reset release	10			μs
Time to hold the TOOL0 pin at the low level after the external reset is released (excluding the processing time of the firmware to control the flash memory)	tнd	POR and LVD reset are released before external reset release	1			ms



- <1> The low level is input to the TOOL0 pin.
- <2> The external reset is released (POR and LVD reset must be released before the external reset is released.).
- <3> The TOOL0 pin is set to the high level.
- <4> Setting of the flash memory programming mode by UART reception and complete the baud rate setting.
- Remark tsuinit: Communication for the initial setting must be completed within 100 ms after the external reset is released during this period.
 - Time to release the external reset after the TOOL0 pin is set to the low level tsu:
 - Time to hold the TOOL0 pin at the low level after the external reset is released (excluding the processing thd: time of the firmware to control the flash memory)



3. ELECTRICAL SPECIFICATIONS (G: INDUSTRIAL APPLICATIONS $T_A = -40$ to +105°C)

This chapter describes the following electrical specifications.

Target products G: Industrial applications T_A = -40 to +105°C

R5F102xxGxx

- Cautions 1. The RL78 microcontrollers have an on-chip debug function, which is provided for development and evaluation. Do not use the on-chip debug function in products designated for mass production, because the guaranteed number of rewritable times of the flash memory may be exceeded when this function is used, and product reliability therefore cannot be guaranteed. Renesas Electronics is not liable for problems occurring when the on-chip debug function is used.
 - 2. The pins mounted depend on the product. Refer to 2.1 Port Functions to 2.2.1 Functions for each product in the RL78/G12 User's Manual.
 - 3. Please contact Renesas Electronics sales office for derating of operation under $T_A = +85^{\circ}C$ to $+105^{\circ}C$. Derating is the systematic reduction of load for the sake of improved reliability.

Remark When the RL78 microcontroller is used in the range of $T_A = -40$ to $+85^{\circ}$ C, see 2. ELECTRICAL SPECIFICATIONS ($T_A = -40$ to $+85^{\circ}$ C).

There are following differences between the products "G: Industrial applications ($T_A = -40$ to +105°C)" and the products "A: Consumer applications, and D: Industrial applications".

Parameter	Applic	ation
	A: Consumer applications, D: Industrial applications	G: Industrial applications
Operating ambient temperature	T _A = -40 to +85°C	T _A = -40 to +105°C
Operating mode	HS (high-speed main) mode:	HS (high-speed main) mode only:
Operating voltage range	2.7 V ≤ V _{DD} ≤ 5.5 V@1 MHz to 24 MHz	2.7 V ≤ V _{DD} ≤ 5.5 V@1 MHz to 24 MHz
	2.4 V ≤ V _{DD} ≤ 5.5 V@1 MHz to 16 MHz	2.4 V ≤ V _{DD} ≤ 5.5 V@1 MHz to 16 MHz
	LS (low-speed main) mode:	
	1.8 V ≤ V _{DD} ≤ 5.5 V@1 MHz to 8 MHz	
High-speed on-chip oscillator	R5F102 products, 1.8 V ≤ V _{DD} ≤ 5.5 V:	R5F102 products, 2.4 V ≤ V _{DD} ≤ 5.5 V:
clock accuracy	±1.0%@ T _A = -20 to +85°C	±2.0%@ T _A = +85 to +105°C
	±1.5%@ T _A = -40 to -20°C	±1.0%@ T _A = -20 to +85°C
	R5F103 products, 1.8 V ≤ V _{DD} ≤ 5.5 V:	±1.5%@ T _A = -40 to -20°C
	±5.0%@ T _A = -40 to +85°C	
Serial array unit	UART	UART
	CSI: fcLk/2 (supporting 12 Mbps), fcLk/4	CSI: fclk/4
	Simplified I ² C communication	Simplified I ² C communication
Voltage detector	Rise detection voltage: 1.88 V to 4.06 V (12 levels)	Rise detection voltage: 2.61 V to 4.06 V
	Fall detection voltage: 1.84 V to 3.98 V (12 levels)	(8 levels)
		Fall detection voltage: 2.55 V to 3.98 V (8 levels)

Remark The electrical characteristics of the products G: Industrial applications (TA = -40 to +105°C) are different from those of the products "A: Consumer applications, and D: Industrial applications". For details, refer to 3.1 to 3.10.

RENESAS

3.1 Absolute Maximum Ratings

Absolute Maximum Ratings (T_A = 25°C)

Parameter	Symbols		Conditions	Ratings	Unit
Supply Voltage	VDD			-0.5 to + 6.5	V
REGC terminal input voltage ^{Note1}	VIREGC	REGC		-0.3 to +2.8 and -0.3 to V _{DD} + 0.3 _{Note 2}	V
Input Voltage	VI1	Other than P60, F	261	-0.3 to V _{DD} + 0.3 ^{Note 3}	V
	V ₁₂	P60, P61 (N-ch o	pen drain)	-0.3 to 6.5	V
Output Voltage	Vo			-0.3 to V _{DD} + 0.3 ^{Note 3}	V
Analog input voltage	Vai	20, 24-pin produc	ts: ANI0 to ANI3, ANI16 to ANI22	-0.3 to V _{DD} + 0.3	V
		30-pin products: A	ANI0 to ANI3, ANI16 to ANI19	and –0.3 to AV _{REF} (+)+0.3 ^{Notes 3, 4}	
Output current, high	Іон1	Per pin	Other than P20 to P23	-40	mA
		Total of all pins	All the terminals other than P20 to P23	-170	mA
			20-, 24-pin products: P40 to P42 30-pin products: P00, P01, P40, P120	-70	mA
			20-, 24-pin products: P00 to P03 ^{Note 5} , P10 to P14 30-pin products: P10 to P17, P30, P31, P50, P51, P147	-100	mA
	Іон2	Per pin	P20 to P23	-0.5	mA
		Total of all pins		-2	mA
Output current, low	IOL1	Per pin	Other than P20 to P23	40	mA
		Total of all pins	All the terminals other than P20 to P23	170	mA
			20-, 24-pin products: P40 to P42 30-pin products: P00, P01, P40, P120	70	mA
			20-, 24-pin products: P00 to P03 ^{Note 5} , P10 to P14, P60, P61 30-pin products: P10 to P17, P30, P31, P50, P51, P60, P61, P147	100	mA
	IOL2	Per pin	P20 to P23	1	mA
		Total of all pins		5	mA
Operating ambient temperature	TA			-40 to +105	°C
Storage temperature	Tstg			-65 to +150	°C

Notes 1. 30-pin product only.

- 2. Connect the REGC pin to Vss via a capacitor (0.47 to 1 μ F). This value determines the absolute maximum rating of the REGC pin. Do not use it with voltage applied.
- 3. Must be 6.5 V or lower.
- 4. Do not exceed AVREF(+) + 0.3 V in case of A/D conversion target pin.
- 5. 24-pin products only.
- Caution Product quality may suffer if the absolute maximum rating is exceeded even momentarily for any parameter. That is, the absolute maximum ratings are rated values at which the product is on the verge of suffering physical damage, and therefore the product must be used under conditions that ensure that the absolute maximum ratings are not exceeded.
- **Remarks 1.** Unless specified otherwise, the characteristics of alternate-function pins are the same as those of the port pins.
 - **2.** AVREF(+): + side reference voltage of the A/D converter.
 - 3. Vss : Reference voltage

3.2 Oscillator Characteristics

3.2.1 X1 oscillator characteristics

$(T_A = -40 \text{ to } +105^{\circ}\text{C}, 2.4 \text{ V} \le \text{V}_{DD} \le \text{V}_{DD} \le 5.5 \text{ V}, \text{V}_{SS} = 0 \text{ V})$

Parameter	Resonator	Conditions	MIN.	TYP.	MAX.	Unit
X1 clock oscillation frequency (fx) ^{Note}	Ceramic resonator /	$2.7 \text{ V} \leq \text{V}_{\text{DD}} \leq 5.5 \text{ V}$	1.0		20.0	MHz
	crystal oscillator	$2.4 \text{ V} \le \text{V}_{\text{DD}} < 2.7 \text{ V}$	1.0		8.0	

Note Indicates only permissible oscillator frequency ranges. Refer to AC Characteristics for instruction execution time. Request evaluation by the manufacturer of the oscillator circuit mounted on a board to check the oscillator characteristics.

- Caution Since the CPU is started by the high-speed on-chip oscillator clock after a reset release, check the X1 clock oscillation stabilization time using the oscillation stabilization time counter status register (OSTC) by the user. Determine the oscillation stabilization time of the OSTC register and the oscillation stabilization time select register (OSTS) after sufficiently evaluating the oscillation stabilization time with the resonator to be used.
- Remark When using the X1 oscillator, refer to 5.4 System Clock Oscillator in the RL78/G12 User's Manual.

3.2.2 On-chip oscillator characteristics

$(T_A = -40 \text{ to } +105^{\circ}\text{C}, 2.4 \text{ V} \le \text{V}_{DD} \le 5.5 \text{ V}, \text{V}_{SS} = 0 \text{ V})$

· · ·							
Oscillators	Parameters	Conc	litions	MIN.	TYP.	MAX.	Unit
High-speed on-chip oscillator clock frequency ^{Notes 1, 2}	fін			1		24	MHz
High-speed on-chip oscillator		R5F102 products	T _A = -20 to +85°C	-1.0		+1.0	%
clock frequency accuracy			T _A = -40 to -20°C	-1.5		+1.5	%
			T _A = +85 to +105°C	-2.0		+2.0	%
Low-speed on-chip oscillator clock frequency	fı∟				15		kHz
Low-speed on-chip oscillator clock frequency accuracy				-15		+15	%

Notes 1. High-speed on-chip oscillator frequency is selected by bits 0 to 3 of option byte (000C2H) and bits 0 to 2 of HOCODIV register.

2. This only indicates the oscillator characteristics. Refer to AC Characteristics for instruction execution time.



3.3 DC Characteristics

3.3.1 Pin characteristics

$(T_A = -40 \text{ to } +105^{\circ}\text{C}, 2.4 \text{ V} \le \text{V}_{DD} \le 5.5 \text{ V}, \text{V}_{SS} = 0 \text{ V})$

	(1	/4)

Parameter	Symbol	Conditions	Conditions				Unit
Output current, high ^{Note 1}	Іон1	20-, 24-pin products: Per pin for P00 to P03 ^{Note 4} , P10 to P14, P40 to P42				-3.0 Note 2	mA
		30-pin products: Per pin for P00, P01, P10 to P17, P30, P31, P40, P50, P51, P120, P147					
		20-, 24-pin products:	$4.0 \text{ V} \leq \text{V}_{\text{DD}} \leq 5.5 \text{ V}$			-9.0	mA
		30 pip products:	$2.7 \text{ V} \le \text{V}_{\text{DD}} < 4.0 \text{ V}$			-6.0	mA
			$2.4 \text{ V} \le \text{V}_{\text{DD}} < 2.7 \text{ V}$			-4.5	mA
		20-, 24-pin products:	$4.0 \text{ V} \leq \text{V}_{\text{DD}} \leq 5.5 \text{ V}$			-27.0	mA
		Total of P00 to P03 ^{Note 4} , P10 to P14	$2.7 \text{ V} \le \text{V}_{\text{DD}} < 4.0 \text{ V}$			-18.0	mA
		30-pin products: Total of P10 to P17, P30, P31, P50, P51, P147 (When duty ≤ 70% ^{Note 3})	2.4 V ≤ V _{DD} < 2.7 V			-10.0	mA
		Total of all pins (When duty ≤ 70% ^{Note 3})				-36.0	mA
	Іон2	Per pin for P20 to P23				-0.1	mA
		Total of all pins				-0.4	mA

Notes 1. value of current at which the device operation is guaranteed even if the current flows from the VDD pin to an output pin.

2. However, do not exceed the total current value.

3. The output current value under conditions where the duty factor ≤ 70%. If duty factor > 70%: The output current value can be calculated with the following expression (where n represents the duty factor as a percentage).

• Total output current of pins = (I_{OH} × 0.7)/(n × 0.01) <Example> Where n = 80% and I_{OH} = -10.0 mA

Total output current of pins = $(-10.0 \times 0.7)/(80 \times 0.01) \approx -8.7$ mA

However, the current that is allowed to flow into one pin does not vary depending on the duty factor. A current higher than the absolute maximum rating must not flow into one pin.

- 4. 24-pin products only.
- Caution P10 to P12 and P41 for 20-pin products, P01, P10 to P12, and P41 for 24-pin products, and P00, P10 to P15, P17, and P50 for 30-pin products do not output high level in N-ch open-drain mode.
- **Remark** Unless specified otherwise, the characteristics of alternate-function pins are the same as those of the port pins.

$(I_A = -40 \text{ to } +105^{\circ}\text{C})$, 2.4 V ≤	V DD \leq 5.5 V, Vss = 0 V)					(2/4)
Parameter	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Output current, low ^{Note 1}	Iol1	20-, 24-pin products: Per pin for P00 to P03 ^{Note 4} , P10 to P14, P40 to P42 30-pin products: Per pin for P00, P01, P10 to P17, P30, P31, P40, P50, P51, P120, P147				8.5 Note 2	mA
		Per pin for P60, P61				15.0 Note 2	mA
		20-, 24-pin products:	$4.0 \text{ V} \leq \text{V}_{\text{DD}} \leq 5.5 \text{ V}$			25.5	mA
		Total of P40 to P42	$2.7~\text{V} \leq \text{V}_{\text{DD}} < 4.0~\text{V}$			9.0	mA
		30-pin products: Total of P00, P01, P40, P120 (When duty ≤ 70% ^{Note 3})	$2.4 \text{ V} \leq \text{V}_{\text{DD}} < 2.7 \text{ V}$			1.8	mA
		20-, 24-pin products:	$4.0~V \leq V_{\text{DD}} \leq 5.5~V$			40.0	mA
		Total of P00 to P03 ^{Note 4} ,	$2.7~V \leq V_{\text{DD}} < 4.0~V$			27.0	mA
		P10 to P14, P60, P61 30-pin products: Total of P10 to P17, P30, P31, P50, P51, P60, P61, P147 (When duty ≤ 70% ^{Note 3})	$2.4 \text{ V} \le \text{V}_{\text{DD}} \le 2.7 \text{ V}$			5.4	mA
		Total of all pins (When duty $\leq 70\%^{\text{Note 3}}$)				65.5	mA
	IOL2	Per pin for P20 to P23				0.4	mA
		Total of all pins				1.6	mA

$(T_A = -40 \text{ to } +105^{\circ}\text{C}, 2.4 \text{ V} \le \text{V}_{DD} \le 5.5 \text{ V}, \text{V}_{SS} = 0 \text{ V})$

(2/4)

Notes 1. Value of current at which the device operation is guaranteed even if the current flows from an output pin to the Vss pin.

2. However, do not exceed the total current value.

3. The output current value under conditions where the duty factor \leq 70%.

If duty factor > 70%: The output current value can be calculated with the following expression (where n represents the duty factor as a percentage).

• Total output current of pins = $(I_{OL} \times 0.7)/(n \times 0.01)$

<Example> Where n = 80% and I_{OL} = 10.0 mA

Total output current of pins = $(10.0 \times 0.7)/(80 \times 0.01) \cong 8.7 \text{ mA}$

However, the current that is allowed to flow into one pin does not vary depending on the duty factor. A current higher than the absolute maximum rating must not flow into one pin.

- **4.** 24-pin products only.
- **Remark** Unless specified otherwise, the characteristics of alternate-function pins are the same as those of the port pins.



$(T_A = -40 \text{ to } +105^{\circ}\text{C}, 2.4 \text{ V} \le \text{V}_{DD} \le 5.5 \text{ V}, \text{V}_{SS} = 0 \text{ V})$

(3/4)

Parameter	Symbol	Condition	S	MIN.	TYP.	MAX.	Unit
Input voltage, high	VIH1	Normal input buffer 20-, 24-pin products: P00 to P0)3 ^{Note 2} , P10 to P14,	0.8Vdd		Vdd	V
		P40 to P42 30-pin products: P00, P01, P1 P40, P50, P51, P120, P147	0 to P17, P30, P31,				
	VIH2	TTL input buffer	$4.0 \text{ V} \leq \text{V}_{\text{DD}} \leq 5.5 \text{ V}$	2.2		Vdd	V
		20-, 24-pin products: P10, P11	$3.3 \text{ V} \leq \text{V}_{\text{DD}} < 4.0 \text{ V}$	2.0		Vdd	V
		30-pin products: P01, P10, P11, P13 to P17	$2.4 \text{ V} \le \text{V}_{\text{DD}} < 3.3 \text{ V}$	1.5		Vdd	V
	Vінз	Normal input buffer P20 to P23		0.7Vdd		Vdd	V
	VIH4	P60, P61		0.7Vdd		6.0	V
	VIH5	P121, P122, P125 ^{Note 1} , P137,	EXCLK, RESET	0.8Vdd		Vdd	V
Input voltage, low	ViL1	Normal input buffer 20-, 24-pin products: P00 to P03 ^{Note 2} , P10 to P14, P40 to P42 30-pin products: P00, P01, P10 to P17, P30, P31,		0		0.2V _{DD}	V
		30-pin products: P00, P01, P10 P40, P50, P51, P120, P147					
	VIL2	TTL input buffer	$4.0 \text{ V} \leq \text{V}_{\text{DD}} \leq 5.5 \text{ V}$	0		0.8	V
		20-, 24-pin products: P10, P11	$3.3 \text{ V} \leq \text{V}_{\text{DD}} < 4.0 \text{ V}$	0		0.5	V
		30-pin products: P01, P10, P11, P13 to P17	$2.4 \text{ V} \leq \text{V}_{\text{DD}} < 3.3 \text{ V}$	0		0.32	V
	VIL3	P20 to P23		0		0.3V _{DD}	V
	VIL4	P60, P61		0		0.3VDD	V
	VIL5	P121, P122, P125 ^{Note 1} , P137,	EXCLK, RESET	0		0.2V _{DD}	V
Output voltage, high	Vон1	20-, 24-pin products: P00 to P03 ^{Note 2} , P10 to P14,	4.0 V ≤ V _{DD} ≤ 5.5 V, Іон1 = −3.0 mA	Vdd-0.7			V
		P40 to P42 30-pin products:	2.7 V ≤ V _{DD} ≤ 5.5 V, Іон1 = −2.0 mA	VDD-0.6			V
		P00, P01, P10 to P17, P30, P31, P40, P50, P51, P120, P147	2.4 V ≤ V _{DD} ≤ 5.5 V, Іон1 = −1.5 mA	V _{DD} -0.5			V
	Vон2	P20 to P23	Іон2 = –100 µА	Vdd-0.5			V

Notes 1. 20, 24-pin products only.

2. 24-pin products only.

Caution The maximum value of V_{IH} of pins P10 to P12 and P41 for 20-pin products, P01, P10 to P12, and P41 for 24-pin products, and P00, P10 to P15, P17, and P50 for 30-pin products is V_{DD} even in N-ch opendrain mode.

High level is not output in the N-ch open-drain mode.

Remark Unless specified otherwise, the characteristics of alternate-function pins are the same as those of the port pins.

$(T_A = -40 \text{ to } +105^{\circ}\text{C}, 2.4 \text{ V} \le \text{V}_{DD} \le 5.5 \text{ V}, \text{V}_{SS} = 0 \text{ V})$

(4/4)

TA = -40 to +105°C, Parameter	Symbol		, Conditio	ins	MIN.	TYP.	MAX.	(4/4 Unit
Output voltage, low	V _{OL1}	20-, 24-pin product P00 to P03 ^{Note} , P1	s:	$4.0 V \le V_{DD} \le 5.5 V,$ $I_{OL1} = 8.5 mA$			0.7	V
		P40 to P42 30-pin products: P0	00, P01,	$2.7 \text{ V} \le \text{V}_{\text{DD}} \le 5.5 \text{ V},$ Iol1 = 3.0 mA			0.6	V
		P10 to P17, P30, P31, P40, P50, P51, P120, P147		$2.7 \text{ V} \le \text{V}_{\text{DD}} \le 5.5 \text{ V},$ $I_{\text{OL1}} = 1.5 \text{ mA}$			0.4	V
				$2.4 \text{ V} \le \text{V}_{\text{DD}} \le 5.5 \text{ V},$ $I_{\text{OL1}} = 0.6 \text{ mA}$			0.4	V
	Vol2	P20 to P23		Iol2 = 400 μA			0.4	V
	Vol3	,		$4.0 \text{ V} \le \text{V}_{\text{DD}} \le 5.5 \text{ V},$ Iol1 = 15.0 mA			2.0	V
				$4.0 \text{ V} \le \text{V}_{\text{DD}} \le 5.5 \text{ V},$ IOL1 = 5.0 mA			0.4	V
				$2.7 \text{ V} \le \text{V}_{\text{DD}} \le 5.5 \text{ V},$ Iol1 = 3.0 mA			0.4	V
				$2.4 \text{ V} \le \text{V}_{\text{DD}} \le 5.5 \text{ V},$ Iol1 = 2.0 mA			0.4	V
Input leakage current, high	Ilih1	Other than P121, P122	VI = VDD	VI = VDD			1	μA
	Ilih2	P121, P122 (X1, X2/EXCLK)	VI = VDD	Input port or external clock input			1	μA
				When resonator connected			10	μA
Input leakage current, low	Ilil1	Other than P121, P122	VI = Vss				-1	μA
	Ilil2	P121, P122 (X1, X2/EXCLK)	VI = Vss	Input port or external clock input			-1	μA
				When resonator connected			-10	μA
On-chip pull-up resistance	Ru	20-, 24-pin products: P00 to P03 ^{Note} , P10 to P14, P40 to P42, P125, RESET		VI = Vss, input port	10	20	100	kΩ
		30-pin products: P0 P10 to P17, P30, F P50, P51, P120, P	P31, P40,					

Note 24-pin products only.

Remark Unless specified otherwise, the characteristics of alternate-function pins are the same as those of the port pins.

3.3.2 Supply current characteristics

(1) 20-, 24-pin products

(T _A = -40 to	+105°C,	2.4 V ≤	Vdd ≤	5.5 V,	Vss = 0	V)

Parameter	Symbol			Conditions			MIN.	TYP.	MAX.	Unit
Supply	IDD1	Operating	HS (High-speed	f⊪ = 24 MHz ^{Note 3}	Basic	V _{DD} = 5.0 V		1.5		mA
current ^{Note 1}		mode	main) mode ^{Note 4}		operation	V _{DD} = 3.0 V		1.5		
					Normal	V _{DD} = 5.0 V		3.3	5.3	mA
					operation	V _{DD} = 3.0 V		3.3	5.3	
				f⊮ = 16 MHz ^{Note 3}		V _{DD} = 5.0 V		2.5	3.9	mA
				V _{DD} = 3.0 V		2.5	3.9			
			f _{MX} = 20 MHz ^{Note 2}		Square wave input		2.8	4.7	mA	
				V _{DD} = 5.0 V	Resonator con	Resonator connection		3.0	4.8	
				$f_{MX} = 20 \text{ MHz}^{\text{Note 2}},$		Square wave input		2.8	4.7	mA
				V _{DD} = 3.0 V	V _{DD} = 3.0 V	Resonator connection		3.0	4.8	
				$f_{MX} = 10 \text{ MHz}^{\text{Note 2}},$		Square wave input		1.8	2.8	mA
			V _{DD} = 5.0 V		Resonator connection		1.8	2.8		
		$f_{MX} = 10 \text{ MHz}^{\text{Note 2}},$		Square wave input		1.8	2.8	mA		
				V _{DD} = 3.0 V		Resonator connection		1.8	2.8	

Notes 1. Total current flowing into V_{DD}, including the input leakage current flowing when the level of the input pin is fixed to V_{DD} or V_{SS}. The values below the MAX. column include the peripheral operation current. However, not including the current flowing into the A/D converter, LVD circuit, I/O port, and on-chip pull-up/pull-down resistors and the current flowing during data flash rewrite.

- 2. When high-speed on-chip oscillator clock is stopped.
- 3. When high-speed system clock is stopped
- **4.** Relationship between operation voltage width, operation frequency of CPU and operation mode is as follows.

HS (High speed main) mode: V_{DD} = 2.7 V to 5.5 V @1 MHz to 24 MHz V_{DD} = 2.4 V to 5.5 V @1 MHz to 16 MHz

- **Remarks 1.** f_{MX}: High-speed system clock frequency (X1 clock oscillation frequency or external main system clock frequency)
 - 2. fin: high-speed on-chip oscillator clock frequency
 - **3.** Temperature condition of the TYP. value is $T_A = 25^{\circ}C$.



(1/2)

(1) 20-, 24-pin products

$(T_A = -40 \text{ to } +105^{\circ}\text{C}, 2.4 \text{ V} \le \text{V}_{\text{DD}} \le 5.5 \text{ V}, \text{ V}_{\text{SS}} = 0 \text{ V}) $ (2/2)									
Parameter	Symbol			Conditions		MIN.	TYP.	MAX.	Unit
Supply	DD2 Note 2	HALT	HS (High-speed	f _{IH} = 24 MHz ^{Note 4}	V _{DD} = 5.0 V		440	2230	μA
current ^{Note 1}		mode	main) mode ^{Note 6}		V _{DD} = 3.0 V		440	2230	
				file = 16 MHz ^{Note 4}	V _{DD} = 5.0 V		400	1650	μA
					V _{DD} = 3.0 V		400	1650	
				$f_{MX} = 20 \text{ MHz}^{\text{Note 3}},$	Square wave input		280	1900	μA
				V _{DD} = 5.0 V	Resonator connection		450	2000	
				$f_{MX} = 20 \text{ MHz}^{\text{Note 3}},$ $V_{\text{DD}} = 3.0 \text{ V}$	Square wave input		280	1900	μA
					Resonator connection		450	2000	
				f _{MX} = 10 MHz ^{Note 3} ,	Square wave input		190	1010	μA
			V _{DD} = 5.0 V	Resonator connection		260	1090		
				$f_{MX} = 10 \text{ MHz}^{\text{Note 3}},$ $V_{\text{DD}} = 3.0 \text{ V}$	Square wave input		190	1010	μA
					Resonator connection		260	1090	
	DD3 Note 5	STOP	$T_A = -40^{\circ}C$				0.19	0.50	μA
		mode	T _A = +25°C				0.24	0.50	
			T _A = +50°C				0.32	0.80	
			T _A = +70°C T _A = +85°C				0.48	1.20	
							0.74	2.20	
			T _A = +105°C				1.50	10.20	

Notes 1. Total current flowing into V_{DD}, including the input leakage current flowing when the level of the input pin is fixed to V_{DD} or V_{SS}. The values below the MAX. column include the peripheral operation current. However, not including the current flowing into the A/D converter, LVD circuit, I/O port, and on-chip pull-up/pull-down resistors and the current flowing during data flash rewrite.

- 2. During HALT instruction execution by flash memory.
- 3. When high-speed on-chip oscillator clock is stopped.
- 4. When high-speed system clock is stopped.
- **5.** Not including the current flowing into the 12-bit interval timer and watchdog timer.
- 6. Relationship between operation voltage width, operation frequency of CPU and operation mode is as follows.

HS (High speed main) mode: $V_{DD} = 2.7 \text{ V}$ to 5.5 V @1 MHz to 24 MHz

VDD = 2.4 V to 5.5 V @1 MHz to 16 MHz

- Remarks 1. fmx: High-speed system clock frequency (X1 clock oscillation frequency or external main system clock frequency)
 - 2. fill: high-speed on-chip oscillator clock frequency
 - 3. Except temperature condition of the TYP. value is $T_A = 25^{\circ}C$, other than STOP mode



(0)0)

(2) 30-pin products

$(T_A = -40 \text{ to } +105^{\circ}\text{C}, 2.4 \text{ V} \le \text{V}_{DD} \le$	5.5 V, Vss = 0 V)
--	-------------------

T _A = −40 to +105°C, 2.4 V ≤ V _{DD} ≤ 5.5 V, Vss = 0 V)							(1/2)			
Parameter	Symbol	Conditions				MIN.	TYP.	MAX.	Unit	
current ^{Note 1} mode main) mode ^{Note 4} operation				f⊪ = 24 MHz ^{Note 3}		V _{DD} = 5.0 V		1.5		mA
						V _{DD} = 3.0 V		1.5		
	V _{DD} = 5.0 V		3.7	5.8	mA					
					operation	V _{DD} = 3.0 V		3.7	5.8	
				f⊮ = 16 MHz ^{Note 3}		V _{DD} = 5.0 V		2.7	4.2	mA
						V _{DD} = 3.0 V		2.7	4.2	
				$f_{MX} = 20 \text{ MHz}^{\text{Note 2}},$		Square wave input		3.0	4.9	mA
	V _{DD} = 5.0 V	Resonator connection		3.2	5.0					
				$f_{MX} = 20 \text{ MHz}^{\text{Note 2}},$		Square wave input		3.0	4.9	mA
			$V_{DD} = 3.0 \text{ V}$ f _{MX} = 10 MHz ^{Note 2} , V _{DD} = 5.0 V	V _{DD} = 3.0 V		Resonator connection		3.2	5.0]
					Square wave input		1.9	2.9	mA	
				V _{DD} = 5.0 V		Resonator connection		1.9	2.9	
				$f_{MX} = 10 \text{ MHz}^{\text{Note 2}},$]	Square wave input		1.9	2.9	mA
				V _{DD} = 3.0 V		Resonator connection		1.9	2.9	

Notes 1. Total current flowing into VDD, including the input leakage current flowing when the level of the input pin is fixed to VDD or Vss. The values below the MAX. column include the peripheral operation current. However, not including the current flowing into the A/D converter, LVD circuit, I/O port, and on-chip pull-up/pull-down resistors and the current flowing during data flash rewrite.

- 2. When high-speed on-chip oscillator clock is stopped.
- 3. When high-speed system clock is stopped
- 4. Relationship between operation voltage width, operation frequency of CPU and operation mode is as follows.

HS (High speed main) mode: VDD = 2.7 V to 5.5 V @1 MHz to 24 MHz VDD = 2.4 V to 5.5 V @1 MHz to 16 MHz

- Remarks 1. fmx: High-speed system clock frequency (X1 clock oscillation frequency or external main system clock frequency)
 - 2. fin: high-speed on-chip oscillator clock frequency
 - **3.** Temperature condition of the TYP. value is $T_A = 25^{\circ}C$.



(2) 30-pin products

$(T_A = -40 \text{ to } +105^{\circ}\text{C}, 2.4 \text{ V} \le \text{V}_{DD} \le 5.5 \text{ V}, \text{V}_{SS} = 0 \text{ V})$
--

IA = -40 tO		∠.4 V ≦ V	′DD ≤ 5.5 V, V ss =	*		MIN.		1	(2/2)
Parameter	Symbol	Conditions					TYP.	MAX.	Unit
Supply current ^{Note 1}	IDD2 Note 2	• ² HALT mode		$f_{IH} = 24 \text{ MHz}^{Note 4}$	V _{DD} = 5.0 V		440	2300	μA
					V _{DD} = 3.0 V		440	2300	
				f _{IH} = 16 MHz ^{Note 4}	V _{DD} = 5.0 V		400	1700	μA
					V _{DD} = 3.0 V		400	1700	
				$f_{MX} = 20 \text{ MHz}^{\text{Note 3}},$ $V_{\text{DD}} = 5.0 \text{ V}$	Square wave input		280	1900	μA
					Resonator connection		450	2000	
				f _{MX} = 20 MHz ^{Note 3} , V _{DD} = 3.0 V	Square wave input		280	1900	μA
					Resonator connection		450	2000	
				f _{MX} = 10 MHz ^{Note 3} , V _{DD} = 5.0 V	Square wave input		190	1020	μΑ
					Resonator connection		260	1100	
				$f_{MX} = 10 \text{ MHz}^{Note 3},$ $V_{DD} = 3.0 \text{ V}$	Square wave input		190	1020	
					Resonator connection		260	1100	
	_{DD3} Note 5	STOP mode	T _A = -40°C				0.18	0.50	μA
			T _A = +25°C				0.23	0.50	
			$T_{A} = +50^{\circ}C$ $T_{A} = +70^{\circ}C$				0.30	1.10	
							0.46	1.90	
			T _A = +85°C	T _A = +85°C			0.75	3.30	
			T _A = +105°C				2.94	15.30	

Notes 1. Total current flowing into VDD, including the input leakage current flowing when the level of the input pin is fixed to VDD or Vss. The values below the MAX. column include the peripheral operation current. However, not including the current flowing into the A/D converter, LVD circuit, I/O port, and on-chip pull-up/pull-down resistors and the current flowing during data flash rewrite.

- 2. During HALT instruction execution by flash memory.
- 3. When high-speed on-chip oscillator clock is stopped.
- 4. When high-speed system clock is stopped.
- 5. Not including the current flowing into the 12-bit interval timer and watchdog timer.
- 6. Relationship between operation voltage width, operation frequency of CPU and operation mode is as follows.

HS (High speed main) mode: VDD = 2.7 V to 5.5 V @1 MHz to 24 MHz

VDD = 2.4 V to 5.5 V @1 MHz to 16 MHz

- Remarks 1. fmx: High-speed system clock frequency (X1 clock oscillation frequency or external main system clock frequency)
 - 2. fin: high-speed on-chip oscillator clock frequency
 - 3. Except STOP mode, temperature condition of the TYP. value is $T_A = 25^{\circ}C$.



(3) Peripheral functions (Common to all products)

$(T_A = -40 \text{ to } +105^{\circ}\text{C}, 2.4 \text{ V} \le \text{V}_{DD} \le 5.5 \text{ V}, \text{V}_{SS} = 0 \text{ V})$

Parameter	Symbol		Conditions	MIN.	TYP.	MAX.	Unit
Low-speed onchip oscillator operating current	_{FIL} Note 1				0.20		μA
12-bit interval timer operating current	ITMKA Notes 1, 2, 3				0.02		μA
Watchdog timer operating current	IWDT Notes 1, 2, 4	fı∟ = 15 kHz			0.22		μA
A/D converter	IADC	When conversion	Normal mode, AV _{REFP} = V _{DD} = 5.0 V		1.30	1.70	mA
operating current	Notes 1, 5	at maximum speed	Low voltage mode, AV _{REFP} = V _{DD} = 3.0 V		0.50	0.70	mA
A/D converter reference voltage operating current	IADREF Note 1				75.0		μA
Temperature sensor operating current	ITMPS Note 1				75.0		μA
LVD operating current	ILVD Notes 1, 6				0.08		μA
Self-programming operating current	IFSP Notes 1, 8				2.00	12.20	mA
BGO operating current	IBGO Notes 1, 7				2.00	12.20	mA
SNOOZE operating	Isnoz	ADC operation	The mode is performed Note 9		0.50	1.10	mA
current Note 1		The A/D conversion operations are performed, Low voltage mode, AV_{REFP} = V_{DD} = 3.0 V		1.20	2.04	mA	
		CSI/UART operation	<u>ו</u>		0.70	1.54	mA

Notes 1. Current flowing to the VDD.

- 2. When high speed on-chip oscillator and high-speed system clock are stopped.
- 3. Current flowing only to the 12-bit interval timer (excluding the operating current of the low-speed on-chip oscillator). The current value of the RL78 microcontrollers is the sum of IDD1, IDD2 or IDD3, and IFIL and ITMKA when the 12-bit interval timer operates.
- 4. Current flowing only to the watchdog timer (including the operating current of the low-speed on-chip oscillator). The current value of the RL78 microcontrollers is the sum of IDD1, IDD2 or IDD3 and IWDT when the watchdog timer operates.
- **5.** Current flowing only to the A/D converter. The current value of the RL78 microcontrollers is the sum of IDD1 or IDD2 and IADC when the A/D converter operates in an operation mode or the HALT mode.
- 6. Current flowing only to the LVD circuit. The current value of the RL78 microcontrollers is the sum of IDD1, IDD2 or IDD3 and ILVD when the LVD circuit operates.
- 7. Current flowing only during data flash rewrite.
- **8.** Current flowing only during self programming.
- 9. For shift time to the SNOOZE mode, see 17.3.3 SNOOZE mode in the RL78/G12 User's Manual.

Remarks 1. fil: Low-speed on-chip oscillator clock frequency

2. Temperature condition of the TYP. value is $T_A = 25^{\circ}C$



3.4 AC Characteristics

$(T_A = -40 \text{ to } +105^{\circ}\text{C}, 2.4 \text{ V} \le \text{V}_{DD} \le 5.5 \text{ V}, \text{V}_{SS} = 0 \text{ V})$

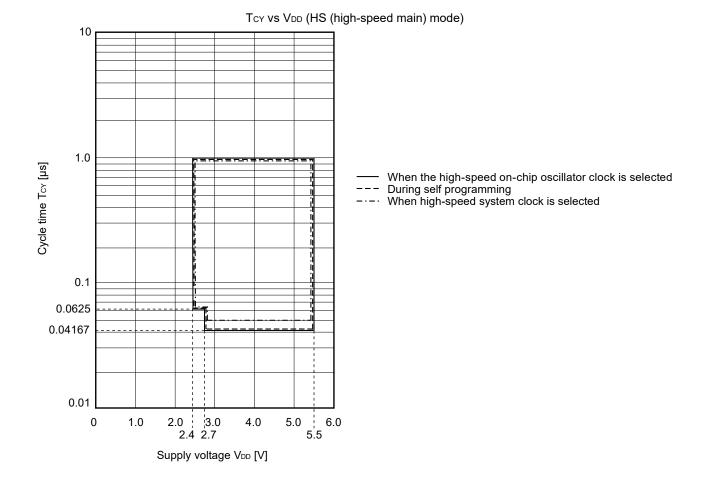
Items	Symbol		Condition	IS	MIN.	TYP.	MAX.	Unit
Instruction cycle (minimum	Тсч	Main system	HS (High-	$2.7 \text{ V} \leq \text{V}_{\text{DD}} \leq 5.5 \text{ V}$	0.04167		1	μs
nstruction execution time)		clock (fMAIN) operation	speed main) mode	$2.4 \text{ V} \leq \text{V}_{\text{DD}} \leq 2.7 \text{ V}$	0.0625		1	μs
		During self	HS (High-	$2.7 \text{ V} \leq \text{V}_{\text{DD}} \leq 5.5 \text{ V}$	0.04167		1	μs
		programming speed main) 2 mode	$2.4 \text{ V} \leq \text{V}_{\text{DD}} < 2.7 \text{ V}$	0.0625		1	μs	
External main system clock	fex	$2.7 \text{ V} \leq \text{V}_{\text{DD}} \leq 5.7 \text{ V}$.5 V		1.0		20.0	MHz
frequency		$2.4 \text{ V} \leq \text{V}_{\text{DD}} < 2$.7 V		1.0		16.0	MHz
External main system clock	texh, texl	$2.7 \text{ V} \leq \text{V}_{\text{DD}} \leq 5$.5 V		24			ns
input high-level width, low- level width		$2.4 \text{ V} \leq \text{V}_{\text{DD}} \leq 2$.7 V		30			ns
TI00 to TI07 input high-level width, low-level width	t⊓∺, t⊓∟				1/fмск + 10			ns
TO00 to TO07 output	fто	$4.0 \text{ V} \leq \text{V}_{\text{DD}} \leq 5$.5 V				12	MHz
frequency		$2.7 V \le V_{DD} < 4$.0 V				8	MHz
		$2.4 \text{ V} \leq \text{V}_{\text{DD}} < 2$.7 V				4	MHz
PCLBUZ0, or PCLBUZ1	f PCL	$4.0 V \le V_{DD} \le 5$.5 V				16	MHz
output frequency		$2.7 \text{ V} \leq \text{V}_{\text{DD}} < 4$.0 V				8	MHz
		$2.4 \text{ V} \leq \text{V}_{\text{DD}} < 2$.7 V				4	MHz
INTP0 to INTP5 input high- level width, low-level width	tinth, tintl				1			μs
KR0 to KR9 input available width	tkr				250			ns
RESET low-level width	trsl				10			μs

Remark fmck: Timer array unit operation clock frequency

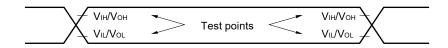
(Operation clock to be set by the timer clock select register 0 (TPS0) and the CKS0n bit of timer mode register 0n (TMR0n). n: Channel number (n = 0 to 7))



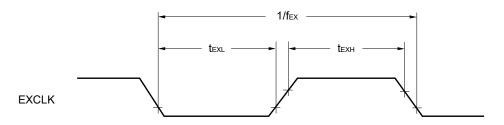
Minimum Instruction Execution Time during Main System Clock Operation



AC Timing Test Point

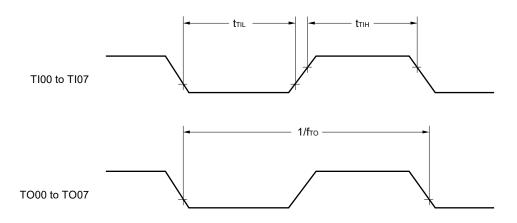


External Main System Clock Timing

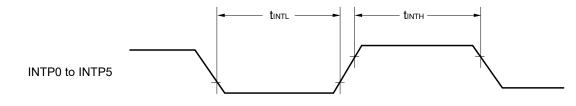




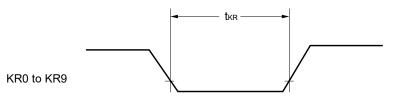
TI/TO Timing



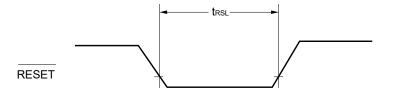
Interrupt Request Input Timing



Key Interrupt Input Timing



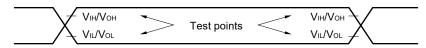
RESET Input Timing





3.5 Peripheral Functions Characteristics

AC Timing Test Point



3.5.1 Serial array unit

(1) During communication at same potential (UART mode) ($T_A = -40$ to +105°C, 2.4 V $\leq V_{DD} \leq 5.5$ V, V_{SS} = 0 V)

<u>(1A 4010 - </u>					
Parameter	Symbol	Conditions	HS (high-spee	ed main) Mode	Unit
			MIN.	MAX.	
Transfer rate				fмск/12	bps
Note 1		Theoretical value of the maximum transfer rate $f_{CLK} = f_{MCK}^{Note 2}$		2.0	Mbps

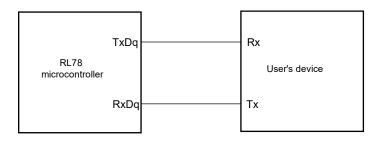
Notes 1. Transfer rate in the SNOOZE mode is 4800 bps only.

- 2. The maximum operating frequencies of the CPU/peripheral hardware clock (fclk) are:
 - HS (high-speed main) mode: 24 MHz (2.7 V \leq V_{DD} \leq 5.5 V)

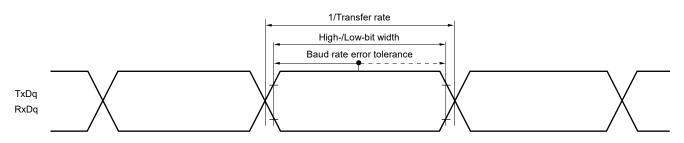
```
16 MHz (2.4 V \leq V<sub>DD</sub> \leq 5.5 V)
```

Caution Select the normal input buffer for the RxDq pin and the normal output mode for the TxDq pin by using port input mode register g (PIMg) and port output mode register g (POMg).

UART mode connection diagram (during communication at same potential)



UART mode bit width (during communication at same potential) (reference)



Remarks 1. q: UART number (q = 0 to 2), g: PIM, POM number (g = 0, 1)

2. fMCK: Serial array unit operation clock frequency

(Operation clock to be set by the serial clock select register m (SPSm) and the CKSmn bit of serial mode register mn (SMRmn).

m: Unit number, n: Channel number (mn = 00 to 03, 10, 11))

Parameter	Symbol	Conditions		HS (high-spee	d main) Mode	Unit
				MIN.	MAX.	
SCKp cycle time	t ксү1	tĸcy1 ≥ 4/fcLĸ	$2.7 \text{ V} \leq \text{V}_{\text{DD}} \leq 5.5 \text{ V}$	334		ns
			$2.4 \text{ V} \leq \text{V}_{\text{DD}} \leq 5.5 \text{ V}$	500		ns
SCKp high-/low-level width	tкнı,	$4.0 \text{ V} \leq \text{V}_{\text{DD}} \leq 5.5$	V	tксү1/2–24		ns
	tĸL1	2.7 V ≤ V _{DD} ≤ 5.5	V	tксү1/2–36		ns
		$2.4 \text{ V} \le \text{V}_{\text{DD}} \le 5.5 \text{ V}$		tксү1/2–76		ns
SIp setup time (to SCKp↑) ^{Note 1}	tsik1	$4.0 \text{ V} \leq \text{V}_{\text{DD}} \leq 5.5$	V	66		ns
		2.7 V ≤ V _{DD} ≤ 5.5	V	66		ns
		$2.4 V \le V_{DD} \le 5.5 V$		113		ns
SIp hold time (from SCKp↑) Note 2	tksi1			38		ns
Delay time from SCKp↓ to SOp output ^{Note 3}	tkso1	C = 30 pF ^{Note 4}			50	ns

(2) During communication at same potential (CSI mode) (master mode, SCKp internal clock output)
$(T_A = -40 \text{ to } +105^{\circ}\text{C}, 2.4 \text{ V} \le \text{V}_{\text{DD}} \le 5.5 \text{ V}, \text{V}_{\text{SS}} = 0 \text{ V})$

- Notes 1. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The SIp setup time becomes "to SCKp↓" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
 - **2.** When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The SIp hold time becomes "from SCKp↓" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
 - **3.** When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The delay time to SOp output becomes "from SCKp↑" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
 - 4. C is the load capacitance of the SCKp and SOp output lines.
- Caution Select the normal input buffer for the SIp pin and the normal output mode for the SOp and SCKp pins by using port input mode register 1 (PIM1) and port output mode registers 0, 1, 4 (POM0, POM1, POM4).
- **Remarks 1.** p: CSI number (p = 00, 01, 11, 20), m: Unit number (m = 0, 1), n: Channel number (n = 0, 1, 3)
 - 2. fMck: Serial array unit operation clock frequency
 - (Operation clock to be set by the serial clock select register m (SPSm) and the CKSmn bit of serial mode register mn (SMRmn). m: Unit number (m = 0, 1), n: Channel number (n = 0, 1, 3))

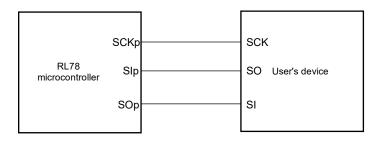


Parameter	Symbol	Conditions		HS (high-speed	main) Mode	Unit
				MIN.	MAX.	
SCKp cycle time Note 5	tксү2	$4.0 \text{ V} \leq \text{V}_{\text{DD}} \leq 5.5 \text{ V}$	20 MHz < fмск	16/ f мск		ns
			fмск ≤ 20 MHz	12/fмск		ns
		$2.7 \text{ V} \leq \text{V}_{\text{DD}} \leq 5.5 \text{ V}$	16 MHz < fмск	16/ f мск		ns
			fмск ≤ 16 MHz	12/fмск		ns
		$2.4 \text{ V} \leq \text{V}_{\text{DD}} \leq 5.5 \text{ V}$		12/fмск		ns
				and 1000		
SCKp high-/low-level width	tкн2,	$4.0 \text{ V} \leq \text{V}_{\text{DD}} \leq 5.5 \text{ V}$	tксү2/2–14		ns	
	tĸ∟2	$2.7 \text{ V} \leq \text{V}_{\text{DD}} \leq 5.5 \text{ V}$	tксү2/2–16		ns	
		$2.4 \text{ V} \leq \text{V}_{\text{DD}} \leq 5.5 \text{ V}$		tксү2/2–36		ns
SIp setup time (to SCKp↑)	tsik2	$2.7 \text{ V} \leq \text{V}_{\text{DD}} \leq 5.5 \text{ V}$		1/fмск + 40		ns
Note 1		$2.4 \text{ V} \leq \text{V}_{\text{DD}} \leq 5.5 \text{ V}$		1/fмск + 60		ns
SIp hold time (from SCKp↑) ^{Note 2}	tksi2			1/fмск + 62		ns
Delay time from SCKp↓ to	tĸso2	C = 30 pF Note 4	$2.7 \text{ V} \leq \text{V}_{\text{DD}} \leq 5.5 \text{ V}$		2/fмск + 66	ns
SOp output Note 3			$2.4 \text{ V} \leq \text{V}_{\text{DD}} \leq 5.5 \text{ V}$		2/fмск + 113	ns

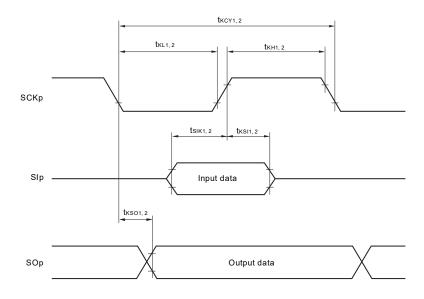
(3) During communication at same potential (CSI mode) (slave mode, SCKp... external clock input) ($T_A = -40$ to $+105^{\circ}C$, 2.4 V $\leq V_{DD} \leq 5.5$ V, V_{SS} = 0 V)

- Notes 1. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The SIp setup time becomes "to SCKp↓" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
 - **2.** When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The SIp hold time becomes "from SCKp↓" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
 - **3.** When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The delay time to SOp output becomes "from SCKp↑" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
 - 4. C is the load capacitance of the SOp output lines.
 - 5. Transfer rate in the SNOOZE mode: MAX. 1 Mbps.
- Caution Select the normal input buffer for the SIp and SCKp pins and the normal output mode for the SOp pin by using port input mode register 1 (PIM1) and port output mode registers 0, 1, 4 (POM0, POM1, POM4).

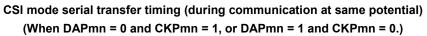
CSI mode connection diagram (during communication at same potential)

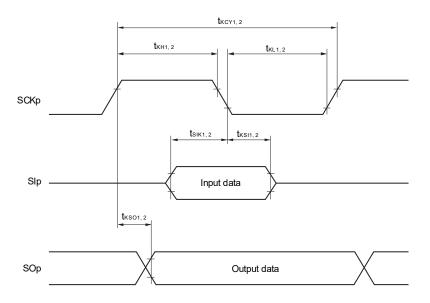






CSI mode serial transfer timing (during communication at same potential) (When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1.)





- Remarks 1. p: CSI number (p = 00, 01, 11, 20), m: Unit number (m = 0, 1), n: Channel number (n = 0, 1, 3)
 2. f_{MCK}: Serial array unit operation clock frequency
 - (Operation clock to be set by the serial clock select register m (SPSm) and the CKSmn bit of serial mode register mn (SMRmn). m: Unit number (m = 0,1), n: Channel number (n = 0, 1, 3))

Parameter	Symbol	Conditions	HS (high-speed main) Mode		Unit
			MIN.	MAX.	
SCLr clock frequency	fsc∟	C_b = 100 pF, R_b = 3 k Ω		100 Note 1	kHz
Hold time when SCLr = "L"	tLow	C_b = 100 pF, R_b = 3 k Ω	4600		ns
Hold time when SCLr = "H"	tнıgн	C_b = 100 pF, R_b = 3 k Ω	4600		ns
Data setup time (reception)	tsu:dat	C_b = 100 pF, R_b = 3 k Ω	1/f _{MCK} + 580 ^{Note 2}		ns
Data hold time (transmission)	thd:dat	C_b = 100 pF, R_b = 3 k Ω	0	1420	ns

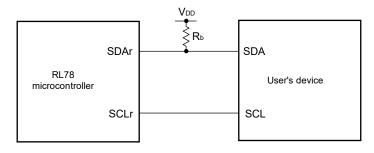
(4) During communication at same potential (simplified l²C mode)

$(T_A = -40 \text{ to } +105^{\circ}\text{C}, 2.4 \text{ V} \le \text{V}_{DD} \le 5.5 \text{ V}, \text{V}_{SS} = 0 \text{ V})$

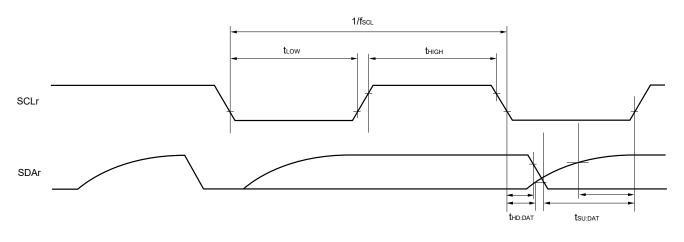
Notes 1. The value must be equal to or less than $f_{MCK}/4$.

- 2. Set tsu:DAT so that it will not exceed the hold time when SCLr = "L" or SCLr = "H".
- Caution Select the N-ch open drain output (VDD tolerance) mode for SDAr by using port output mode register h (POMh).

Simplified I²C mode connection diagram (during communication at same potential)



Simplified I²C mode serial transfer timing (during communication at same potential)



Remarks 1. R_b [Ω]:Communication line (SDAr) pull-up resistance

 C_b [F]: Communication line (SCLr, SDAr) load capacitance

2. r: IIC number (r = 00, 01, 11, 20), h: = POM number (h = 0, 1, 4, 5)

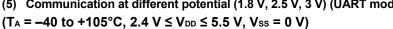
fMCK: Serial array unit operation clock frequency (Operation clock to be set by the serial clock select register m (SPSm) and the CKSmn bit of serial mode register mn (SMRmn). m: Unit number (m = 0, 1), p: Channel number (0, 1, 3))

m: Unit number (m = 0, 1), n: Channel number (0, 1, 3))

RENESAS

Parameter	Parameter Symbol		Conditions		speed main) ode	Unit
				MIN.	MAX.	
Transfer rate ^{Note4}		Reception	$4.0 V \le V_{DD} \le 5.5 V,$ $2.7 V \le V_b \le 4.0 V$		fмск/12 Note 1	bps
			Theoretical value of the maximum transfer rate f _{MCK} = f _{CLK} Note 2		2.0	Mbps
			$2.7 V \le V_{DD} < 4.0 V,$ $2.3 V \le V_b \le 2.7 V$		fмск/12 Note 1	bps
			Theoretical value of the maximum transfer rate $f_{MCK} = f_{CLK}$ Note 2		2.0	Mbps
			$2.4 V \le V_{DD} < 3.3 V,$ $1.6 V \le V_b \le 2.0 V$		fмск/12 Note 1	bps
			Theoretical value of the maximum transfer rate $f_{MCK} = f_{CLK}^{Note 2}$		2.0	Mbps
		Transmission	$4.0 V \le V_{DD} \le 5.5 V,$ $2.7 V \le V_b \le 4.0 V$		Note 3	bps
			Theoretical value of the maximum transfer rate $C_b = 50 \text{ pF}, R_b = 1.4 \text{ k}\Omega, V_b = 2.7 \text{ V}$		2.0 Note 4	Mbps
			$2.7 V \le V_{DD} < 4.0 V,$ $2.3 V \le V_b \le 2.7 V,$		Note 5	bps
			Theoretical value of the maximum transfer rate $C_b = 50 \text{ pF}, R_b = 2.7 \text{ k}\Omega, V_b = 2.3 \text{ V}$		1.2 Note 6	Mbps
			$2.4 V \le V_{DD} < 3.3 V,$ $1.6 V \le V_b \le 2.0 V$		Notes 2, 7	bps
			Theoretical value of the maximum transfer rate $C_b = 50 \text{ pF}, R_b = 5.5 \text{ k}\Omega, V_b = 1.6 \text{ V}$		0.43 Note 8	Mbps

(5) Communication at different potential (1.8 V, 2.5 V, 3 V) (UART mode)



Notes 1. Transfer rate in the SNOOZE mode is 4800 bps only.

2. The maximum operating frequencies of the CPU/peripheral hardware clock (fcLK) are: HS (high-speed main) mode: 24 MHz (2.7 V \leq VDD \leq 5.5 V)

16 MHz (2.4 V \leq V_{DD} \leq 5.5 V)

3. The smaller maximum transfer rate derived by using fmck/12 or the following expression is the valid maximum transfer rate.

Expression for calculating the transfer rate when $4.0 \text{ V} \le \text{V}_{DD} \le 5.5 \text{ V}$ and $2.7 \text{ V} \le \text{V}_{b} \le 4.0 \text{ V}$

Maximum transfer rate =

 $\frac{1}{\{-C_b \times R_b \times ln \ (1 - \frac{2.2}{V_b})\} \times 3}$ [bps]

Baud rate error (theoretical value) =

$$\frac{\frac{1}{\text{Transfer rate} \times 2} - \{-C_b \times R_b \times \ln (1 - \frac{2.2}{V_b})\}}{(\frac{1}{\text{Transfer rate}}) \times \text{Number of transferred bits}} \times 100 [\%]$$

* This value is the theoretical value of the relative difference between the transmission and reception sides.

- 4. This value as an example is calculated when the conditions described in the "Conditions" column are met. Refer to Note 3 above to calculate the maximum transfer rate under conditions of the customer.
- 5. The smaller maximum transfer rate derived by using fMCK/12 or the following expression is the valid maximum transfer rate.

Expression for calculating the transfer rate when 2.7 V \leq V_{DD} < 4.0 V and 2.3 V \leq V_b \leq 2.7 V

Maximum transfer rate =
$$\frac{1}{\{-C_b \times R_b \times \ln (1 - \frac{2.0}{V_b})\} \times 3}$$
 [bps]

Baud rate error (theoretical value) =

 $\frac{1}{\text{Transfer rate } \times 2} - \{-C_b \times R_b \times \ln (1 - \frac{2.0}{V_b})\}$ $(\frac{1}{(\text{Transfer rate})} \times \text{Number of transferred bits} \times 100 [\%]$

- * This value is the theoretical value of the relative difference between the transmission and reception sides.
- 6. This value as an example is calculated when the conditions described in the "Conditions" column are met. Refer to Note 5 above to calculate the maximum transfer rate under conditions of the customer.
- 7. The smaller maximum transfer rate derived by using fMCK/12 or the following expression is the valid maximum transfer rate.

Expression for calculating the transfer rate when 2.4 V \leq V_{DD} < 3.3 V, 1.6 V \leq V_b \leq 2.0 V

Maximum transfer rate =

$$\frac{1}{b \times R_b \times \ln (1 - \frac{1.5}{V_b})} \times 3$$
 [bps]

Baud rate error (theoretical value) =

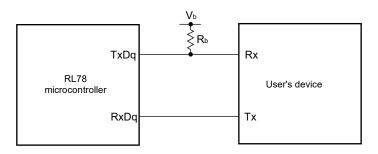
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 $\frac{\frac{1}{\text{Transfer rate} \times 2} - \{-C_b \times R_b \times \ln (1 - \frac{1.5}{V_b})\}}{(\frac{1}{\text{Transfer rate}}) \times \text{Number of transferred bits}} \times 100 [\%]$

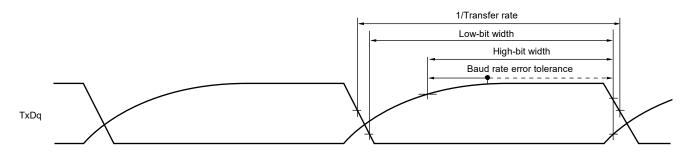
- * This value is the theoretical value of the relative difference between the transmission and reception sides.
- This value as an example is calculated when the conditions described in the "Conditions" column are met. Refer to Note 7 above to calculate the maximum transfer rate under conditions of the customer.
- Caution Select the TTL input buffer for the RxDq pin and the N-ch open drain output (V_{DD} tolerance) mode for the TxDq pin by using port input mode register g (PIMg) and port output mode register g (POMg). For V_{IH} and V_{IL}, see the DC characteristics with TTL input buffer selected.

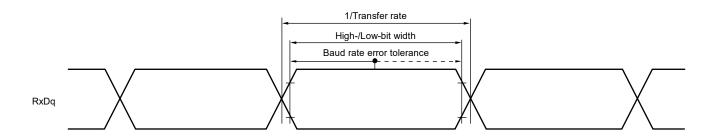


UART mode connection diagram (during communication at different potential)



UART mode bit width (during communication at different potential) (reference)





- **Remarks 1.** R_b[Ω]: Communication line (TxDq) pull-up resistance, C_b[F]: Communication line (TxDq) load capacitance, V_b[V]: Communication line voltage
 - 2. q: UART number (q = 0 to 2), g: PIM and POM number (g = 0, 1)

 fMCK: Serial array unit operation clock frequency (Operation clock to be set by the serial clock select register m (SPSm) and the CKSmn bit of serial mode register mn (SMRmn).

m: Unit number, n: Channel number (mn = 00 to 03, 10, 11))

4. UART0 of the 20- and 24-pin products supports communication at different potential only when the peripheral I/O redirection function is not used.



(6) Communication at different potential (1.8 V, 2.5 V, 3 V) (CSI mode) (master mode, SCKp... internal clock output) (1/3)

Symbol		Conditions	HS (high-speed	l main) Mode	Unit
			MIN.	MAX.	
tkCY1	t _{KCY1} ≥ 4/f _{CLK}	$4.0 V \le V_{DD} \le 5.5 V$,	600		ns
		$2.7 V \le V_b \le 4.0 V$,			
		C_b = 30 pF, R_b = 1.4 k Ω			
		$2.7 \text{ V} \le \text{V}_{\text{DD}} < 4.0 \text{ V},$	1000		ns
		$2.3 V \le V_b \le 2.7 V$,			
		C_b = 30 pF, R_b = 2.7 k Ω			
		$2.4 \text{ V} \le \text{V}_{\text{DD}} < 3.3 \text{ V},$	2300		ns
		$1.6 V \le V_b \le 2.0 V$,			
		C_b = 30 pF, R_b = 5.5 k Ω			
tкнı	$4.0 V \leq V_{DD} \leq$	5.5 V, 2.7 V ≤ V₅ ≤ 4.0 V,	tксү1/2 –150		ns
	$C_{b} = 30 \text{ pF}, R_{b} = 1.4 \text{ k}\Omega$				
	$2.7 V \le V_{DD} < 4.0 V, 2.3 V \le V_b \le 2.7 V,$ $C_b = 30 \text{ pF}, R_b = 2.7 \text{ k}\Omega$ $2.4 V \le V_{DD} < 3.3 V, 1.6 V \le V_b \le 2.0 V,$		tксү1/2 —340		ns
			tксү1/2 —916		ns
t _{KL1}	$4.0 V \leq V_{DD} \leq$	5.5 V, 2.7 V ≤ V _b ≤ 4.0 V,	tксү1/2 –24		ns
			tkcy1/2 –36		ns
			tkcy1/2 –100		ns
		, , ,			110
	tксү1	tkcy1 tkcy1 ≥ 4/fcLk tkH1 4.0 V ≤ VDD ≤ Cb = 30 pF, R 2.7 V ≤ VDD <	tkcy1 tkcy1 ≥ 4/fcLK 4.0 V ≤ VDD ≤ 5.5 V, 2.7 V ≤ Vb ≤ 4.0 V, 2.7 V ≤ Vb ≤ 4.0 V, Cb = 30 pF, Rb = 1.4 kΩ 2.7 V ≤ VDD < 4.0 V,	Item MIN. tree tree 4.0 V ≤ VDD ≤ 5.5 V, 2.7 V ≤ Vb ≤ 4.0 V, Cb = 30 pF, Rb = 1.4 kΩ 600 2.7 V ≤ Vb ≤ 4.0 V, Cb = 30 pF, Rb = 1.4 kΩ 1000 2.3 V ≤ Vb ≤ 2.7 V, Cb = 30 pF, Rb = 2.7 kΩ 1000 2.3 V ≤ Vb ≤ 2.7 V, Cb = 30 pF, Rb = 2.7 kΩ 2300 1.6 V ≤ Vb ≤ 2.0 V, Cb = 30 pF, Rb = 5.5 kΩ 2300 texh 4.0 V ≤ VDD ≤ 5.5 V, 2.7 V ≤ Vb ≤ 4.0 V, Cb = 30 pF, Rb = 1.4 kΩ texh texh texh Veh 2.7 V ≤ VDD < 4.0 V, 2.3 V ≤ Vb ≤ 2.7 V, Cb = 30 pF, Rb = 1.4 kΩ texh texh texh texh 4.0 V ≤ VDD ≤ 5.5 V, 2.7 V ≤ Vb ≤ 4.0 V, Cb = 30 pF, Rb = 5.5 kΩ texh texh texh texh 4.0 V ≤ VDD ≤ 5.5 V, 2.7 V ≤ Vb ≤ 2.0 V, Cb = 30 pF, Rb = 5.5 kΩ texh texh texh texh 4.0 V ≤ VDD ≤ 5.5 V, 2.7 V ≤ Vb ≤ 4.0 V, Cb = 30 pF, Rb = 5.5 kΩ texh texh texh texh texh 4.0 V ≤ VDD ≤ 5.5 V, 2.7 V ≤ Vb ≤ 4.0 V, Cb = 30 pF, Rb = 5.5 kΩ texh texh texh texh texh texh 4.0 V ≤ VDD ≤ 4.0 V, 2.3 V ≤ Vb ≤ 2.0 V, texh texh texh texh texh texh texh	Instrume Instrume

 $(T_A = -40 \text{ to } +105^{\circ}\text{C}, 2.4 \text{ V} \le \text{V}_{DD} \le \text{V}_{DD} \le 5.5 \text{ V}, \text{V}_{SS} = 0 \text{ V})$

- Cautions 1. Select the TTL input buffer for the SIp pin and the N-ch open drain output (V_{DD} tolerance) mode for the SOp pin and SCKp pin by using port input mode register 1 (PIM1) and port output mode register 1 (POM1). For V_H and V_{IL}, see the DC characteristics with TTL input buffer selected.
 - 2. CSI01 and CSI11 cannot communicate at different potential.
- **Remarks 1.** R_b [Ω]: Communication line (SCKp, SOp) pull-up resistance, C_b [F]: Communication line (SCKp, SOp) load capacitance, V_b [V]: Communication line voltage
 - **2.** p: CSI number (p = 00, 20)



(6) Communication at different potential (1.8 V, 2.5 V, 3 V) (CSI mode) (master mode, SCKp... internal clock output) (2/3)

Parameter	Symbol	Conditions	HS (high-spee	HS (high-speed main) Mode		
			MIN.	MAX.		
SIp setup time (to SCKp↑) _{Note}	tsik1	$\begin{array}{l} 4.0 \; V \leq V_{DD} \leq 5.5 \; V, \; 2.7 \; V \leq V_b \leq 4.0 \; V, \\ C_b = 30 \; pF, \; R_b = 1.4 \; k\Omega \end{array}$	162		ns	
		$\label{eq:VD} \begin{array}{l} 2.7 \ V \leq V_{DD} < 4.0 \ V, \ 2.3 \ V \leq V_b \leq 2.7 \ V, \\ C_b = 30 \ pF, \ R_b = 2.7 \ k\Omega \end{array}$	354		ns	
		$\label{eq:VDD} \begin{array}{l} 2.4 \ V \leq V_{DD} < 3.3 \ V, \ 1.6 \ V \leq V_b \leq 2.0 \ V, \\ C_b = 30 \ pF, \ R_b = 5.5 \ k\Omega \end{array}$	958		ns	
SIp hold time (from SCKp↑) ^{Note}	tksii		38		ns	
		$\begin{array}{l} 2.7 \ V \leq V_{DD} < 4.0 \ V, \ 2.3 \ V \leq V_b \leq 2.7 \ V, \\ C_b = 30 \ pF, \ R_b = 2.7 \ k\Omega \end{array}$	38		ns	
		$\begin{array}{l} 2.4 \ V \leq V_{DD} < 3.3 \ V, \ 1.6 \ V \leq V_b \leq 2.0 \ V, \\ C_b = 30 \ pF, \ R_b = 5.5 \ k\Omega \end{array}$	38		ns	
Delay time from SCKp↓ to SOp output ^{Note}	tkso1			200	ns	
		$\label{eq:VD} \begin{array}{l} 2.7 \ V \leq V_{DD} < 4.0 \ V, \ 2.3 \ V \leq V_b \leq 2.7 \ V, \\ C_b = 30 \ pF, \ R_b = 2.7 \ k\Omega \end{array}$		390	ns	
		$\begin{array}{l} 2.4 \ V \leq V_{DD} < 3.3 \ V, \ 1.6 \ V \leq V_b \leq 2.0 \ V, \\ C_b = 30 \ pF, \ R_b = 5.5 \ k\Omega \end{array}$		966	ns	

$(T_A = -40 \text{ to } +105^{\circ}\text{C}, 2.4 \text{ V} \le \text{V}_{\text{DD}} \le 5.5 \text{ V}, \text{V}_{\text{SS}} = 0 \text{ V})$

Note When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1.

(Cautions and Remarks are listed on the next page.)



(6) Communication at different potential (1.8 V, 2.5 V, 3 V) (CSI mode) (master mode, SCKp... internal clock output) (3/3)

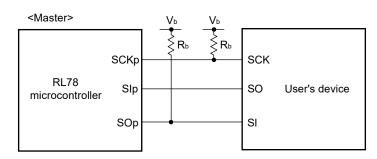
Parameter	Symbol	Conditions	HS (high-speed main) Mode	Unit
			MIN. MAX.	
SIp setup time (to SCKp↓) _{Note}	tsıĸı		88	ns
		$\label{eq:2.7} \begin{array}{l} 2.7 \ V \leq V_{DD} < 4.0 \ V, \ 2.3 \ V \leq V_b \leq 2.7 \ V, \\ C_b = 30 \ pF, \ R_b = 2.7 \ k\Omega \end{array}$	88	ns
		$\begin{array}{l} 2.4 \ V \leq V_{DD} < 3.3 \ V, \ 1.6 \ V \leq V_b \leq 2.0 \ V, \\ C_b = 30 \ pF, \ R_b = 5.5 \ k\Omega \end{array}$	220	ns
SIp hold time (from SCKp↓) ^{Note}	tksi1		38	ns
		$\begin{array}{l} 2.7 \ V \leq V_{DD} < 4.0 \ V, \ 2.3 \ V \leq V_b \leq 2.7 \ V, \\ C_b = 30 \ pF, \ R_b = 2.7 \ k\Omega \end{array}$	38	ns
		$\begin{array}{l} 2.4 \ V \leq V_{DD} < 3.3 \ V, \ 1.6 \ V \leq V_b \leq 2.0 \ V, \\ C_b = 30 \ pF, \ R_b = 5.5 \ k\Omega \end{array}$	38	ns
Delay time from SCKp↑ to SOp output ^{Note}	tkso1		50	ns
		$\label{eq:2.7} \begin{array}{l} 2.7 \ V \leq V_{DD} < 4.0 \ V, \ 2.3 \ V \leq V_b \leq 2.7 \ V, \\ C_b = 30 \ pF, \ R_b = 2.7 \ k\Omega \end{array}$	50	ns
		$\begin{array}{l} 2.4 \ V \leq V_{DD} < 3.3 \ V, \ 1.6 \ V \leq V_b \leq 2.0 \ V, \\ C_b = 30 \ pF, \ R_b = 5.5 \ k\Omega \end{array}$	50	ns

$(T_A = -40 \text{ to } +105^{\circ}\text{C}, 2.4 \text{ V} \le \text{V}_{\text{DD}} \le 5.5 \text{ V}, \text{V}_{\text{SS}} = 0 \text{ V})$

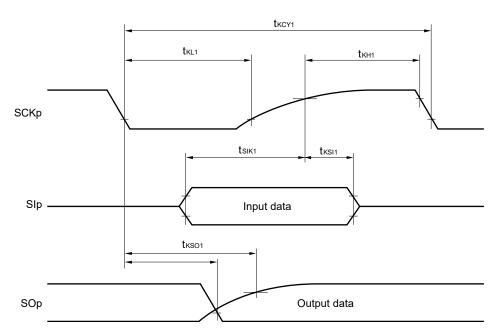
Note When DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.

- Cautions 1. Select the TTL input buffer for the SIp pin and the N-ch open drain output (VDD tolerance) mode for the SOp pin and SCKp pin by using port input mode register 1 (PIM1) and port output mode register 1 (POM1). For VIH and VIL, see the DC characteristics with TTL input buffer selected.
 - 2. CSI01 and CSI11 cannot communicate at different potential.
- **Remarks 1.** R_b [Ω]: Communication line (SCKp, SOp) pull-up resistance, C_b [F]: Communication line (SCKp, SOp) load capacitance, V_b [V]: Communication line voltage
 - **2.** p: CSI number (p = 00, 20), m: Unit number (m = 0, 1), n: Channel number (n = 0)

CSI mode connection diagram (during communication at different potential)

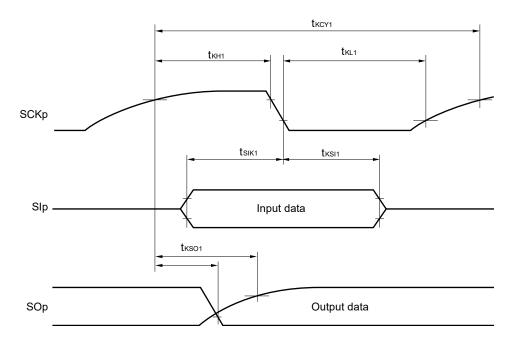


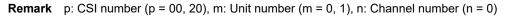




CSI mode serial transfer timing (master mode) (during communication at different potential) (When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1)

CSI mode serial transfer timing (master mode) (during communication at different potential) (When DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.)





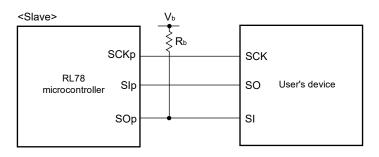
(7) Communication at different potential (1.8 V, 2.5 V, 3 V) (CSI mode) (slave mode, SCKp... external clock input) ($T_A = -40$ to $+105^{\circ}$ C, 2.4 V \leq V_{DD} \leq 5.5 V, V_{SS} = 0 V)

Parameter	Symbol		Conditions	HS (high-spe Mod	,	Unit	
				MIN. MAX.			
SCKp cycle time Note 1	tксү2	$4.0 \text{ V} \leq \text{V}_{\text{DD}} \leq 5.5 \text{ V},$	20 MHz < fмск ≤ 24 MHz	24/f мск		ns	
		$2.7~V \leq V_b \leq 4.0~V$	8 MHz < fмск ≤ 20 MHz	20/f мск		ns	
			4 MHz < fмск ≤ 8 MHz	16/f мск		ns	
			fмск ≤ 4 MHz	12/f мск		ns	
		$2.7 \text{ V} \le \text{V}_{\text{DD}} < 4.0 \text{ V},$	20 MHz < fмск ≤ 24 MHz	32/fмск		ns	
		$2.3~V \leq V_b \leq 2.7~V$	16 MHz < fмск ≤ 20 MHz	28/f мск		ns	
			8 MHz < fмск ≤ 16 MHz	24/fмск		ns	
			4 MHz < fмск ≤ 8 MHz	16/f мск		ns	
			fмск ≤ 4 MHz	12/f мск		ns	
		$2.4 V \le V_{DD} < 3.3 V$,	20 MHz < fмск ≤ 24 MHz	72/f мск		ns	
		$1.6 \text{ V} \le \text{V}_{b} \le 2.0 \text{ V}$	16 MHz < fмск ≤ 20 MHz	64/f мск		ns	
			8 MHz < fмск ≤ 16 MHz	52/f мск		ns	
			4 MHz < fмск ≤ 8 MHz	32/fмск		ns	
			fмск ≤ 4 MHz	20/f мск		ns	
SCKp high-/low-level	t кн2,	$4.0 \text{ V} \leq \text{V}_{\text{DD}} \leq 5.5 \text{ V}, 2.7 \text{ V} \leq \text{V}_{\text{b}} \leq 4.0 \text{ V}$		tkcy2/2 – 24		ns	
width	tĸL2	$2.7 \text{ V} \le \text{V}_{\text{DD}} \le 4.0 \text{ V}, 2.$	$3 \text{ V} \leq \text{V}_{b} \leq 2.7 \text{ V}$	tkcy2/2 – 36		ns	
		$2.4 \text{ V} \le \text{V}_{\text{DD}} < 3.3 \text{ V}, 1.$	$6 \text{ V} \leq \text{V}_{\text{b}} \leq 2.0 \text{ V}$	tĸcy2/2 – 100		ns	
SIp setup time	tsik2	$4.0 \text{ V} \le \text{V}_{\text{DD}} \le 5.5 \text{ V}, 2.$	$7 \text{ V} \leq \text{V}_{\text{DD}} \leq 4.0 \text{ V}$	1/fмск + 40		ns	
(to SCKp↑) ^{Note 2}		$2.7 \text{ V} \le \text{V}_{\text{DD}} < 4.0 \text{ V}, 2.$	$3 \text{ V} \leq \text{V}_{b} \leq 2.7 \text{ V}$	1/fмск + 40		ns	
		$2.4 \text{ V} \le \text{V}_{\text{DD}} < 3.3 \text{ V}, 1.$	$6 \text{ V} \leq \text{V}_{\text{DD}} \leq 2.0 \text{ V}$	1/fмск + 60		ns	
SIp hold time (from SCKp↑) ^{Note 3}	tksi2			1/fмск + 62		ns	
Delay time from SCKp↓ to	tĸso2	$4.0 \text{ V} \le \text{V}_{\text{DD}} \le 5.5 \text{ V}, 2.$	$7 \text{ V} \leq \text{V}_{b} \leq 4.0 \text{ V},$		2/fмск +	ns	
SOp output Note 4		C _b = 30 pF, R _b = 1.4 ks	Ω		240		
		$2.7 \text{ V} \le \text{V}_{\text{DD}} < 4.0 \text{ V}, 2.$	$3 \text{ V} \leq \text{V}_{\text{b}} \leq 2.7 \text{ V},$		2/fмск +	ns	
		C_b = 30 pF, R_b = 2.7 ks	Ω		428		
		$2.4 \text{ V} \le \text{V}_{\text{DD}} < 3.3 \text{ V}, 1.$	$6 \text{ V} \leq \text{V}_{\text{b}} \leq 2.0 \text{ V},$		2/fмск +	ns	
		C _b = 30 pF, R _b = 5.5 ks	Ω		1146		

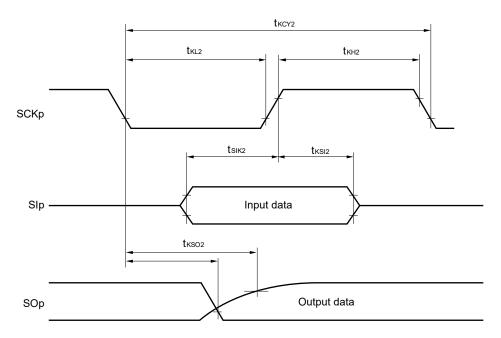
Notes 1. Transfer rate in the SNOOZE mode: MAX. 1 Mbps

- 2. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The SIp setup time becomes "to SCKp↓" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
- 3. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The SIp hold time becomes "from SCKp↓" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
- **4.** When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The delay time to SOp output becomes "from SCKp↑" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
- Cautions 1. Select the TTL input buffer for the SIp and SCKp pins and the N-ch open drain output (V_{DD} tolerance) mode for the SOp pin by using port input mode register 1 (PIM1) and port output mode register 1 (POM1). For V_{IH} and V_{IL}, see the DC characteristics with TTL input buffer selected.
 - 2. CSI01 and CSI11 cannot communicate at different potential.

CSI mode connection diagram (during communication at different potential)



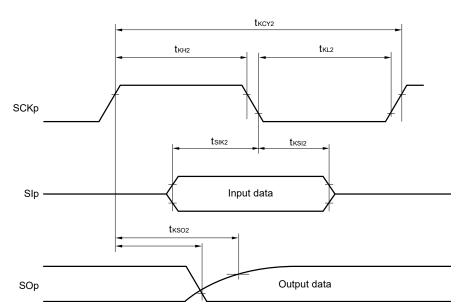
CSI mode serial transfer timing (slave mode) (during communication at different potential) (When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1.)



- Remarks 1.
 R_b [Ω]: Communication line (SOp) pull-up resistance, C_b [F]: Communication line (SOp) load capacitance,

 V_b [V]: Communication line voltage
 - **2.** p: CSI number (p = 00, 20), m: Unit number (m = 0, 1), n: Channel number (n = 0)
 - fMCK: Serial array unit operation clock frequency (Operation clock to be set by the serial clock select register m (SPSm) and the CKSmn bit of serial mode register mn (SMRmn))





CSI mode serial transfer timing (slave mode) (during communication at different potential) (When DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.)

Remark p: CSI number (p = 00, 20), m: Unit number (m = 0, 1), n: Channel number (n = 0)



Conditions Symbol HS (high-speed main) Unit Parameter Mode MAX. MIN. 100^{Note1} SCLr clock frequency **f**scl $4.0 \text{ V} \le \text{V}_{\text{DD}} \le 5.5 \text{ V}, 2.7 \text{ V} \le \text{V}_{\text{b}} \le 4.0 \text{ V},$ kHz $C_b = 100 \text{ pF}, R_b = 2.8 \text{ k}\Omega$ $2.7 \text{ V} \le \text{V}_{\text{DD}} < 4.0 \text{ V}, 2.3 \text{ V} \le \text{V}_{\text{b}} \le 2.7 \text{ V},$ 100^{Note1} kHz C_{b} = 100 pF, R_{b} = 2.7 k Ω 100^{Note1} $2.4 \text{ V} \le \text{V}_{\text{DD}} < 3.3 \text{ V}, 1.6 \text{ V} \le \text{V}_{\text{b}} \le 2.0 \text{ V},$ kHz $C_b = 100 \text{ pF}, R_b = 5.5 \text{ k}\Omega$ Hold time when SCLr = "L" $4.0 \text{ V} \le \text{V}_{\text{DD}} \le 5.5 \text{ V}, 2.7 \text{ V} \le \text{V}_{\text{b}} \le 4.0 \text{ V},$ **t**LOW 4600 ns C_{b} = 100 pF, R_{b} = 2.8 k Ω $2.7 \text{ V} \le \text{V}_{\text{DD}} < 4.0 \text{ V}, 2.3 \text{ V} \le \text{V}_{\text{b}} \le 2.7 \text{ V},$ 4600 ns C_b = 100 pF, R_b = 2.7 k Ω $2.4 \text{ V} \le \text{V}_{\text{DD}} < 3.3 \text{ V}, 1.6 \text{ V} \le \text{V}_{\text{b}} \le 2.0 \text{ V},$ 4650 ns $C_b = 100 \text{ pF}, R_b = 5.5 \text{ k}\Omega$ $4.0 \text{ V} \le \text{V}_{\text{DD}} \le 5.5 \text{ V}, 2.7 \text{ V} \le \text{V}_{\text{b}} \le 4.0 \text{ V},$ Hold time when SCLr = "H" **t**HIGH 2700 ns C_{b} = 100 pF, R_{b} = 2.8 k Ω $2.7 \text{ V} \le \text{V}_{\text{DD}} < 4.0 \text{ V}, 2.3 \text{ V} \le \text{V}_{\text{b}} \le 2.7 \text{ V},$ 2400 ns C_{b} = 100 pF, R_{b} = 2.7 k Ω $2.4 \text{ V} \le \text{V}_{\text{DD}} < 3.3 \text{ V}, 1.6 \text{ V} \le \text{V}_{\text{b}} \le 2.0 \text{ V},$ 1830 ns $C_b = 100 \text{ pF}, R_b = 5.5 \text{ k}\Omega$ $4.0 \text{ V} \le \text{V}_{\text{DD}} \le 5.5 \text{ V}, 2.7 \text{ V} \le \text{V}_{\text{b}} \le 4.0 \text{ V},$ Data setup time (reception) tsu:dat 1/fмск ns + 760 Note2 C_b = 100 pF, R_b = 2.8 k Ω $2.7 \text{ V} \le \text{V}_{\text{DD}} < 4.0 \text{ V}, 2.3 \text{ V} \le \text{V}_{\text{b}} \le 2.7 \text{ V},$ 1/fmck ns + 760 Note2 $C_b = 100 \text{ pF}, R_b = 2.7 \text{ k}\Omega$ $2.4 \text{ V} \le \text{V}_{\text{DD}} < 3.3 \text{ V}, 1.6 \text{ V} \le \text{V}_{\text{b}} \le 2.0 \text{ V},$ 1/fмск ns + 570 Note2 C_b = 100 pF, R_b = 5.5 k Ω $4.0 \text{ V} \le \text{V}_{\text{DD}} \le 5.5 \text{ V}, 2.7 \text{ V} \le \text{V}_{\text{b}} \le 4.0 \text{ V},$ 1420 Data hold time (transmission) thd:dat 0 ns C_b = 100 pF, R_b = 2.8 k Ω $2.7 \text{ V} \le \text{V}_{\text{DD}} < 4.0 \text{ V}, 2.3 \text{ V} \le \text{V}_{\text{b}} \le 2.7 \text{ V},$ 0 1420 ns C_b = 100 pF, R_b = 2.7 k Ω 0 $2.4 \text{ V} \le \text{V}_{\text{DD}} < 3.3 \text{ V}, 1.6 \text{ V} \le \text{V}_{\text{b}} \le 2.0 \text{ V},$ 1215 ns

(8) Communication at different potential (1.8 V, 2.5 V, 3 V) (simplified I²C mode)

 $(T_A = -40 \text{ to } +105^{\circ}\text{C}, 2.4 \text{ V} \le \text{V}_{DD} \le 5.5 \text{ V}, \text{V}_{SS} = 0 \text{ V})$

Notes 1. The value must be equal to or less than $f_{MCK}/4$.

2. Set tsu:DAT so that it will not exceed the hold time when SCLr = "L" or SCLr = "H".

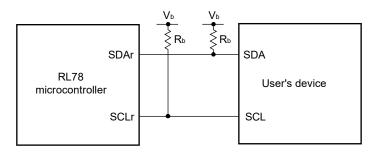
 $C_b = 100 \text{ pF}, R_b = 5.5 \text{ k}\Omega$

- Cautions 1. Select the TTL input buffer and the N-ch open drain output (V_{DD} tolerance) mode for the SDAr pin and the N-ch open drain output (V_{DD} tolerance) mode for the SCLr pin by using port input mode register 1 (PIM1) and port output mode register 1 (POM1). For V_{IH} and V_{IL}, see the DC characteristics with TTL input buffer selected.
 - 2. IIC01 and IIC11 cannot communicate at different potential.

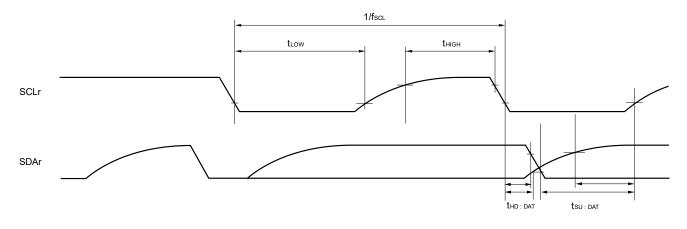
(**Remarks** are listed on the next page.)



Simplified I²C mode connection diagram (during communication at different potential)



Simplified I²C mode serial transfer timing (during communication at different potential)



- Remarks 1. R_b [Ω]: Communication line (SDAr, SCLr) pull-up resistance, C_b [F]: Communication line (SDAr, SCLr) load capacitance, Vb [V]: Communication line voltage
 - **2.** r: IIC Number (r = 00, 20)
 - 3. fMCK: Serial array unit operation clock frequency (Operation clock to be set by the serial clock select register m (SPSm) and the CKSmn bit of serial mode register mn (SMRmn).

m: Unit number (m = 0,1), n: Channel number (n = 0))



3.5.2 Serial interface IICA

$(T_A = -40 \text{ to } +105^{\circ}\text{C}, 2.4 \text{ V} \le \text{V}_{\text{DD}} \le 5.5 \text{ V}, \text{V}_{\text{S}}$	= 0 V)
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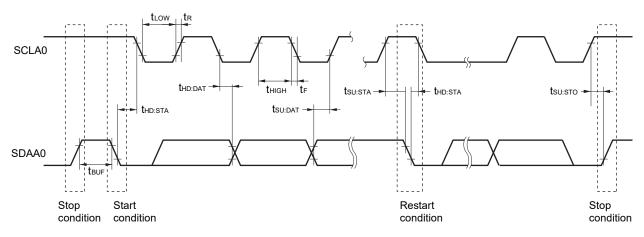
Parameter	Symbol	Conditions	HS	HS (high-speed main) mode				
			Standa	rd Mode	Fast Mode			
			MIN.	MAX.	MIN.	MAX.		
SCLA0 clock frequency	fscl	Fast mode: fclк≥ 3.5 MHz			0	400	kHz	
		Normal mode: fc∟κ≥ 1 MHz	0	100			kHz	
Setup time of restart condition	tsu:sta		4.7		0.6		μs	
Hold time ^{Note 1}	thd:sta		4.0		0.6		μs	
Hold time when SCLA0 = "L"	tLOW		4.7		1.3		μs	
Hold time when SCLA0 = "H"	t HIGH		4.0		0.6		μs	
Data setup time (reception)	tsu:dat		250		100		ns	
Data hold time (transmission) ^{Note 2}	thd:dat		0	3.45	0	0.9	μs	
Setup time of stop condition	tsu:sto		4.0		0.6		μs	
Bus-free time	t BUF		4.7		1.3		μs	

Notes 1. The first clock pulse is generated after this period when the start/restart condition is detected.

2. The maximum value (MAX.) of tHD:DAT is during normal transfer and a wait state is inserted in the ACK (acknowledge) timing.

- Caution Only in the 30-pin products, the values in the above table are applied even when bit 2 (PIOR2) in the peripheral I/O redirection register (PIOR) is 1. At this time, the pin characteristics (IOH1, IOL1, VOH1, VOL1) must satisfy the values in the redirect destination.
- **Remark** The maximum value of Cb (communication line capacitance) and the value of Rb (communication line pull-up resistor) at that time in each mode are as follows.

IICA serial transfer timing





3.6 Analog Characteristics

3.6.1 A/D converter characteristics

Classification of A/D converter characteristics

Input channel	Reference Voltage								
	Reference voltage (+) = AVREFP Reference voltage (–) = AVREFM	Reference voltage (+) = V _{DD} Reference voltage (–) = Vss	Reference voltage (+) = VBGR Reference voltage (–) = AVREFM						
ANI0 to ANI3	Refer to 3.6.1 (1) .	Refer to 3.6.1 (3) .	Refer to 3.6.1 (4) .						
ANI16 to ANI22	Refer to 3.6.1 (2) .								
Internal reference voltage Temperature sensor output voltage	Refer to 3.6.1 (1) .		_						

(1) When reference voltage (+) = AV_{REFP}/ANI0 (ADREFP1 = 0, ADREFP0 = 1), reference voltage (-) = AV_{REFM}/ANI1 (ADREFM = 1), target pin: ANI2, ANI3, internal reference voltage, and temperature sensor output voltage

 $(T_A = -40 \text{ to } +105^{\circ}\text{C}, 2.4 \text{ V} \le \text{AV}_{REFP} \le \text{VDD} \le 5.5 \text{ V}, \text{Vss} = 0 \text{ V}, \text{Reference voltage (+)} = \text{AV}_{REFP}, \text{Reference voltage (-)} = \text{AV}_{REFM} = 0 \text{ V})$

Parameter	Symbol	Cor	nditions	MIN.	TYP.	MAX.	Unit
Resolution	RES		8		10	bit	
Overall error ^{Note 1}	AINL	10-bit resolution AV _{REFP} = V _{DD} ^{Note 3}				±3.5	LSB
Conversion time	t CONV	10-bit resolution	$3.6 \text{ V} \leq \text{V}_{\text{DD}} \leq 5.5 \text{ V}$	2.125		39	μs
		Target pin: ANI2, ANI3	$2.7 \text{ V} \leq \text{V}_{\text{DD}} \leq 5.5 \text{ V}$	3.1875		39	μs
			$2.4 \text{ V} \leq \text{V}_{\text{DD}} \leq 5.5 \text{ V}$	17		39	μs
		10-bit resolution	$3.6 \text{ V} \leq \text{V}_{\text{DD}} \leq 5.5 \text{ V}$	2.375		39	μs
		Target pin: Internal	$2.7 \text{ V} \leq \text{V}_{\text{DD}} \leq 5.5 \text{ V}$	3.5625		39	μs
		reference voltage, and temperature sensor output voltage (HS (high-speed main) mode)	$2.4 \text{ V} \leq \text{V}_{DD} \leq 5.5 \text{ V}$	17		39	μs
Zero-scale error ^{Notes 1, 2}	EZS	10-bit resolution AV _{REFP} = V _{DD} ^{Note 3}				±0.25	%FSR
Full-scale error ^{Notes 1, 2}	EFS	10-bit resolution AV _{REFP} = V _{DD} ^{Note 3}				±0.25	%FSR
Integral linearity error ^{Note 1}	ILE	10-bit resolution AV _{REFP} = V _{DD} ^{Note 3}				±2.5	LSB
Differential linearity error	DLE	10-bit resolution AV _{REFP} = V _{DD} ^{Note 3}				±1.5	LSB
Analog input voltage	VAIN	ANI2, ANI3		0		AVREFP	V
		Internal reference voltage (HS (high-speed main) m		VBGR Note 4			V
		Temperature sensor outp (HS (high-speed main) m	V _{TMPS25} Note 4			V	

(**Notes** are listed on the next page.)



- **Notes 1.** Excludes quantization error (±1/2 LSB).
 - $\ensuremath{\textbf{2}}.$ This value is indicated as a ratio (%FSR) to the full-scale value.
 - 3. When AV_{REFP} < V_{DD}, the MAX. values are as follows. Overall error: Add ±1.0 LSB to the MAX. value when AV_{REFP} = V_{DD}. Zero-scale error/Full-scale error: Add ±0.05%FSR to the MAX. value when AV_{REFP} = V_{DD}. Integral linearity error/ Differential linearity error: Add ±0.5 LSB to the MAX. value when AV_{REFP} = V_{DD}.
 - 4. Refer to 3.6.2 Temperature sensor/internal reference voltage characteristics.
- (2) When reference voltage (+) = AV_{REFP}/ANI0 (ADREFP1 = 0, ADREFP0 = 1), reference voltage (-) = AV_{REFM}/ANI1 (ADREFM = 1), target pin: ANI16 to ANI22

$(T_A = -40 \text{ to } +105^{\circ}\text{C}, 2.4 \text{ V} \le \text{AV}_{\text{REFP}} \le \text{V}_{\text{DD}} \le 5.5 \text{ V}, \text{V}_{\text{SS}} = 0 \text{ V}, \text{Reference voltage (+)} = \text{AV}_{\text{REFP}}, \text{Reference voltage (-)} = 100^{\circ}\text{C}, 1$	
AVREFM = 0 V)	

Parameter	Symbol	Conditio	ns	MIN.	TYP.	MAX.	Unit
Resolution	Res			8		10	bit
Overall error Note 1	AINL	10-bit resolution AV _{REFP} = V _{DD} ^{Note 3}		1.2	±5.0	LSB	
Conversion time	tconv	10-bit resolution	$3.6 \text{ V} \leq \text{Vdd} \leq 5.5 \text{ V}$	2.125		39	μs
		Target ANI pin: ANI16 to AN	2.7 V ≤ VDD ≤ 5.5 V	3.1875		39	μs
			$2.4 \text{ V} \leq \text{V}_{\text{DD}} \leq 5.5 \text{ V}$	17		39	μs
Zero-scale error Notes 1, 2	EZS	10-bit resolution AV _{REFP} = V _{DD} ^{Note 3}			±0.35	%FSR	
Full-scale error Notes 1, 2	EFS	10-bit resolution AV _{REFP} = V _{DD} ^{Note 3}				±0.35	%FSR
Integral linearity error Note 1	ILE	10-bit resolution AV _{REFP} = V _{DD} ^{Note 3}				±3.5	LSB
Differential linearity error ^{Note 1}	DLE	10-bit resolution AV _{REFP} = V _{DD} ^{Note 3}				±2.0	LSB
Analog input voltage	Vain	ANI16 to ANI22		0		AVREFP and VDD	V

Notes 1. Excludes quantization error (±1/2 LSB).

- **2.** This value is indicated as a ratio (%FSR) to the full-scale value.
- **3.** When $AV_{REFP} \leq V_{DD}$, the MAX. values are as follows.

Overall error: Add ± 4.0 LSB to the MAX. value when AV_{REFP} = V_{DD}.

Zero-scale error/Full-scale error: Add $\pm 0.20\%$ FSR to the MAX. value when AV_{REFP} = V_{DD}.

Integral linearity error/ Differential linearity error: Add ±2.0 LSB to the MAX. value when AVREFP = VDD.



(3) When reference voltage (+) = V_{DD} (ADREFP1 = 0, ADREFP0 = 0), reference voltage (-) = V_{ss} (ADREFM = 0), target pin: ANI0 to ANI3, ANI16 to ANI22, internal reference voltage, and temperature sensor output voltage

Parameter	Symbol	Condition	ns	MIN.	TYP.	MAX.	Unit
Resolution	Res			8		10	bit
Overall error ^{Note 1}	AINL	10-bit resolution			1.2	±7.0	LSB
Conversion time	t CONV	10-bit resolution	$3.6 \text{ V} \leq \text{V}_{\text{DD}} \leq 5.5 \text{ V}$	2.125		39	μs
		Target pin: ANI0 to ANI3,	2.7 V ≤ V _{DD} ≤ 5.5 V	3.1875		39	μs
		ANI16 to ANI22	2.4 V ≤ V _{DD} ≤ 5.5 V	17		39	μs
Conversion time	t CONV	10-bit resolution	$3.6 \text{ V} \leq \text{V}_{\text{DD}} \leq 5.5 \text{ V}$	2.375		39	μs
		Target pin: internal reference voltage, and temperature sensor output voltage (HS (high-speed main) mode)	2.7 V ≤ VDD ≤ 5.5 V	3.5625		39	μs
			2.4 V ≤ V _{DD} ≤ 5.5 V	17		39	μs
Zero-scale error ^{Notes 1, 2}	EZS	10-bit resolution			±0.60	%FSR	
Full-scale error ^{Notes 1, 2}	EFS	10-bit resolution				±0.60	%FSR
Integral linearity error ^{Note 1}	ILE	10-bit resolution				±4.0	LSB
Differential linearity error Note 1	DLE	10-bit resolution				±2.0	LSB
Analog input voltage	VAIN	ANI0 to ANI3, ANI16 to ANI2	2	0		VDD	V
		Internal reference voltage (HS (high-speed main) mode)		V _{BGR} Note 3			V
		Temperature sensor output v (HS (high-speed main) mode)	emperature sensor output voltage HS (high-speed main) mode)		VTMPS25 Note 3	3	V

$(T_{A} = -40 \text{ to } \pm 105^{\circ}\text{C} 2.4 \text{ V} \le \text{V}_{PP} \le 5.5$	V, Vss = 0 V, Reference voltage (+) = VDD	Poforonco voltago $(-) = V_{cc}$
(1A40 10 + 105 C, 2.4 V - VDD - 5.5	v, vss – v v, relefence vollage (+) – vuu	, Reference vollage (-) - vss)

Notes 1. Excludes quantization error (±1/2 LSB).

2. This value is indicated as a ratio (%FSR) to the full-scale value.

3. Refer to 3.6.2 Temperature sensor/internal reference voltage characteristics.



(4) When reference voltage (+) = Internal reference voltage (ADREFP1 = 1, ADREFP0 = 0), reference voltage (-) = AV_{REFM} (ADREFM = 1), target pin: ANI0, ANI2, ANI3, and ANI16 to ANI22

$(T_A = -40 \text{ to } +105^{\circ}\text{C}, 2.4 \text{ V} \le \text{V}_{DD} \le 5.5 \text{ V}, \text{ Vss} = 0 \text{ V}, \text{ Reference voltage (+)} = \text{V}_{BGR} \text{ Note 3}, \text{ Reference voltage (-)} = 0 \text{ V}_{BGR} \text{ Note 3}$
AVREFM Note 4 = 0 V, HS (high-speed main) mode)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Resolution	Res			8		bit
Conversion time	t CONV	8-bit resolution	17		39	μs
Zero-scale error ^{Notes 1, 2}	EZS	8-bit resolution			±0.60	%FSR
Integral linearity error ^{Note 1}	ILE	8-bit resolution			±2.0	LSB
Differential linearity error Note 1	DLE	8-bit resolution			±1.0	LSB
Analog input voltage	VAIN		0		$V_{\text{BGR}}{}^{\text{Note 3}}$	V

Notes 1. Excludes quantization error (±1/2 LSB).

2. This value is indicated as a ratio (%FSR) to the full-scale value.

3. Refer to 3.6.2 Temperature sensor/internal reference voltage characteristics.

4. When reference voltage (–) = Vss, the MAX. values are as follows.

Zero-scale error: Add $\pm 0.35\%$ FSR to the MAX. value when reference voltage (–) = AV_{REFM}. Integral linearity error: Add ± 0.5 LSB to the MAX. value when reference voltage (–) = AV_{REFM}. Differential linearity error: Add ± 0.2 LSB to the MAX. value when reference voltage (–) = AV_{REFM}.



3.6.2 Temperature sensor/internal reference voltage characteristics

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Temperature sensor output voltage	VTMPS25	Setting ADS register = 80H, TA = +25°C		1.05		V
Internal reference voltage	VBGR	Setting ADS register = 81H	1.38	1.45	1.50	V
Temperature coefficient	Fvtmps	Temperature sensor output voltage that depends on the temperature		-3.6		mV/°C
Operation stabilization wait time	tamp		5			μs

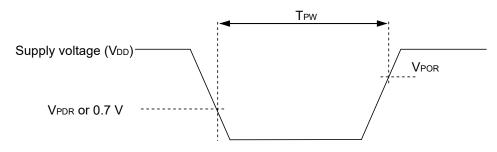
$(T_A = -40 \text{ to } +105^{\circ}\text{C}, 2.4 \text{ V} \le V_{DD} \le 5.5 \text{ V}, V_{SS} = 0 \text{ V}, \text{HS (high-speed main) mode}$

3.6.3 POR circuit characteristics

$(T_A = -40 \text{ to } +105^{\circ}\text{C}, V_{SS} = 0 \text{ V})$

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Detection voltage	VPOR	Power supply rise time	1.45	1.51	1.57	V
	VPDR	Power supply fall time	1.44	1.50	1.56	V
Minimum pulse width Note	TPW		300			μs

Note Minimum time required for a POR reset when V_{DD} exceeds below V_{PDR}. This is also the minimum time required for a POR reset from when V_{DD} exceeds below 0.7 V to when V_{DD} exceeds V_{POR} while STOP mode is entered or the main system clock is stopped through setting bit 0 (HIOSTOP) and bit 7 (MSTOP) in the clock operation status control register (CSC).





3.6.4 LVD circuit characteristics

LVD Detection Voltage of Reset Mode and Interrupt Mode

 $(T_A = -40 \text{ to } +105^{\circ}\text{C}, \text{ VPDR} \le \text{VDD} \le 5.5 \text{ V}, \text{ Vss} = 0 \text{ V})$

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Detection supply voltage	VLVD0	Power supply rise time	3.90	4.06	4.22	V
		Power supply fall time	3.83	3.98	4.13	V
	VLVD1	Power supply rise time	3.60	3.75	3.90	V
		Power supply fall time	3.53	3.67	3.81	V
	VLVD2	Power supply rise time	3.01	3.13	3.25	V
		Power supply fall time	2.94	3.06	3.18	V
	VLVD3	Power supply rise time	2.90	3.02	3.14	V
		Power supply fall time	2.85	2.96	3.07	V
	VLVD4	Power supply rise time	2.81	2.92	3.03	V
		Power supply fall time	2.75	2.86	2.97	V
	VLVD5	Power supply rise time	2.70	2.81	2.92	V
		Power supply fall time	2.64	2.75	2.86	V
	VLVD6	Power supply rise time	2.61	2.71	2.81	V
		Power supply fall time	2.55	2.65	2.75	V
	VLVD7	Power supply rise time	2.51	2.61	2.71	V
		Power supply fall time	2.45	2.55	2.65	V
Minimum pulse width	t∟w		300			μs
Detection delay time					300	μs



LVD detection voltage of interrupt & reset mode

Parameter	Symbol		Con	ditions	MIN.	TYP.	MAX.	Unit
Interrupt and reset	VLVDD0	VPOC2,	VPOC1, VPOC1 = 0, 1, 1, fa	lling reset voltage	2.64	2.75	2.86	V
mode	VLVDD1		LVIS1, LVIS0 = 1, 0	Rising reset release voltage	2.81	2.92	3.03	V
				Falling interrupt voltage	2.75	2.86	2.97	V
	VLVDD2		LVIS1, LVIS0 = 0, 1	Rising reset release voltage	2.90	3.02	3.14	V
				Falling interrupt voltage	2.85	2.96	3.07	V
	VLVDD3]	LVIS1, LVIS0 = 0, 0	Rising reset release voltage	3.90	4.06	4.22	V
				Falling interrupt voltage	3.83	3.98	4.13	V

3.6.5 Power supply voltage rising slope characteristics

$(T_A = -40 \text{ to } +105^{\circ}\text{C}, \text{Vss} = 0 \text{ V})$

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Power supply voltage rising slope	SVDD				54	V/ms

Caution Make sure to keep the internal reset state by the LVD circuit or an external reset until V_{DD} reaches the operating voltage range shown in 3.4 AC Characteristics.

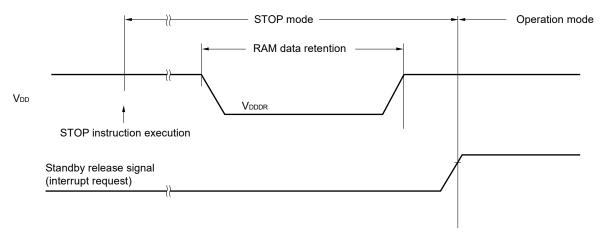


3.7 RAM Data Retention Characteristics

$(T_A = -40 \text{ to } +105^{\circ}\text{C}, V_{SS} = 0 \text{ V})$

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Data retention supply voltage	VDDDR		1.44 Note		5.5	V

Note This depends on the POR detection voltage. For a falling voltage, data in RAM are retained until the voltage reaches the level that triggers a POR reset but not once it reaches the level at which a POR reset is generated.



3.8 Flash Memory Programming Characteristics

$(T_A = -40 \text{ to } +105^{\circ}\text{C}, 2.4 \text{ V} \le \text{V}_{DD} \le 5.5 \text{ V}, \text{V}_{SS} = 0 \text{ V})$

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
System clock frequency	fclк		1		24	MHz
Code flash memory rewritable times Notes 1, 2, 3	Cerwr	Retained for 20 years $T_A = 85^{\circ}C^{Note 4}$	1,000			Times
Data flash memory rewritable times Notes 1, 2, 3		Retained for 1 year T _A = 25°C		1,000,000		
		Retained for 5 years T _A = 85°C Note 4	100,000			
		Retained for 20 years T _A = 85°C ^{Note 4}	10,000			

Notes 1. 1 erase + 1 write after the erase is regarded as 1 rewrite. The retaining years are until next rewrite after the rewrite.

- 2. When using flash memory programmer and Renesas Electronics self programming library
- **3.** These are the characteristics of the flash memory and the results obtained from reliability testing by Renesas Electronics Corporation.
- 4. This temperature is the average value at which data are retained.



3.9 Dedicated Flash Memory Programmer Communication (UART)

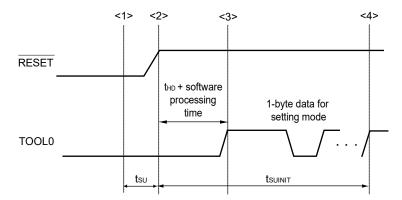
$(T_A = -40 \text{ to } +105^{\circ}\text{C}, 2.4 \text{ V} \le \text{V}_{\text{DD}} \le 5.5 \text{ V}, \text{V}_{\text{SS}} = 0 \text{ V})$

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Transfer rate		During serial programming	115,200		1,000,000	bps

3.10 Timing of Entry to Flash Memory Programming Modes

$(T_A = -40 \text{ to } +105^{\circ}\text{C}, 2.4 \text{ V} \le \text{V}_{DD} \le 5.5 \text{ V}, \text{V}_{SS} = 0 \text{ V})$

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Time to complete the communication for the initial setting after the external reset is released	tsuinit	POR and LVD reset are released before external release			100	ms
Time to release the external reset after the TOOL0 pin is set to the low level	t su	POR and LVD reset are released before external release	10			μs
Time to hold the TOOL0 pin at the low level after the external reset is released	tнd	POR and LVD reset are released before external release	1			ms
(excluding the processing time of the firmware to control the flash memory)						



- <1> The low level is input to the TOOL0 pin.
- <2> The external reset is released (POR and LVD reset must be released before the external reset is released.).
- <3> The TOOL0 pin is set to the high level.
- <4> Setting of the flash memory programming mode by UART reception and complete the baud rate setting.
- **Remark** tsuinit: Communication for the initial setting must be completed within 100 ms after the external reset is released during this period.
 - $t_{\text{SU:}}$ Time to release the external reset after the TOOL0 pin is set to the low level
 - the: Time to hold the TOOL0 pin at the low level after the external reset is released (excluding the processing time of the firmware to control the flash memory)

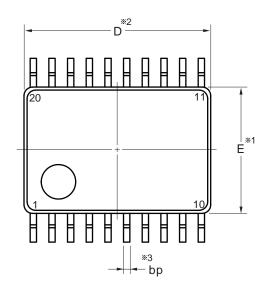


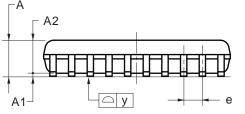
4. PACKAGE DRAWINGS

4.1 20-pin products

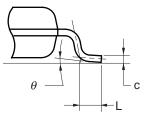
R5F1026AASP, R5F10269ASP, R5F10268ASP, R5F10267ASP, R5F10266ASP R5F1036AASP, R5F10369ASP, R5F10368ASP, R5F10367ASP, R5F10366ASP R5F1026ADSP, R5F10269DSP, R5F10268DSP, R5F10267DSP, R5F10266DSP R5F1036ADSP, R5F10369DSP, R5F10368DSP, R5F10367DSP, R5F10366DSP R5F1026AGSP, R5F10269GSP, R5F10268GSP, R5F10267GSP, R5F10266GSP

JEITA Package Code	RENESAS Code	Previous Code	MASS (TYP.) [g]
P-LSSOP20-4.4x6.5-0.65	PLSP0020JB-A	P20MA-65-NAA-1	0.1





detail of lead end





	(UNIT:mm)
ITEM	DIMENSIONS
D	6.50±0.10
E	4.40±0.10
HE	6.40±0.20
А	1.45 MAX.
A1	0.10±0.10
A2	1.15
е	0.65±0.12
bp	0.22 + 0.10 - 0.05
С	$0.15 \pm 0.05 \\ -0.02$
L	0.50±0.20
У	0.10
θ	0° to 10°

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NOTE

1.Dimensions "%1" and "%2" do not include mold flash.

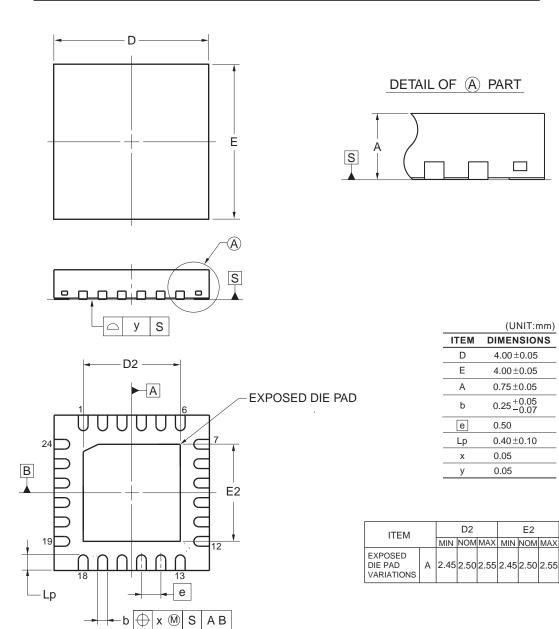
2.Dimension "%3" does not include trim offset.



4.2 24-pin products

R5F1027AANA, R5F10279ANA, R5F10278ANA, R5F10277ANA R5F1037AANA, R5F10379ANA, R5F10378ANA, R5F10377ANA R5F1027ADNA, R5F10279DNA, R5F10278DNA, R5F10277DNA R5F1037ADNA, R5F10379DNA, R5F10378DNA, R5F10377DNA R5F1027AGNA, R5F10279GNA, R5F10278GNA, R5F10277GNA

JEITA Package Code	RENESAS Code	Previous Code	MASS (TYP.) [g]
P-HWQFN24-4x4-0.50	PWQN0024KE-A	P24K8-50-CAB-1	0.04



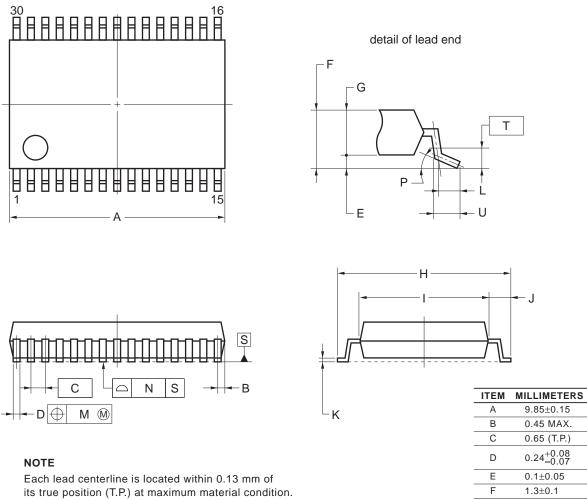
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4.3 30-pin products

R5F102AAASP, R5F102A9ASP, R5F102A8ASP, R5F102A7ASP R5F103AAASP, R5F103A9ASP, R5F103A8ASP, R5F103A7ASP R5F102AADSP, R5F102A9DSP, R5F102A8DSP, R5F102A7DSP R5F103AADSP, R5F103A9DSP, R5F103A8DSP, R5F103A7DSP R5F102AAGSP, R5F102A9GSP, R5F102A8GSP, R5F102A7GSP

ſ	JEITA Package Code	RENESAS Code	Previous Code	MASS (TYP.) [g]
	P-LSSOP30-0300-0.65	PLSP0030JB-B	S30MC-65-5A4-3	0.18



D	$0.24_{-0.07}^{+0.08}$
E	0.1±0.05
F	1.3±0.1
G	1.2
Н	8.1±0.2
I	6.1±0.2
J	1.0±0.2
K	0.17±0.03
L	0.5
Μ	0.13
Ν	0.10
Р	3° ^{+5°} _3°
Т	0.25
U	0.6±0.15

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Revision History

RL78/G12 Datasheet

			Description
Rev.	Date	Page	Summary
1.00	Dec 10, 2012	-	First Edition issued
2.00	Sep 06, 2013	1	Modification of 1.1 Features
		3	Modification of 1.2 List of Part Numbers
		4	Modification of Table 1-1. List of Ordering Part Numbers, Note, and Caution
		7 to 9	Modification of package name in 1.4.1 to 1.4.3
		14	Modification of tables in 1.7 Outline of Functions
		17	Modification of description of table in 2.1 Absolute Maximum Ratings (T _A = 25°C)
		18	Modification of table, Note, and Caution in 2.2.1 X1 oscillator characteristics
		18	Modification of table in 2.2.2 On-chip oscillator characteristics
		19	Modification of Note 3 in 2.3.1 Pin characteristics (1/4)
		20	Modification of Note 3 in 2.3.1 Pin characteristics (2/4)
		23	Modification of Notes 1 and 2 in (1) 20-, 24-pin products (1/2)
		24	Modification of Notes 1 and 3 in (1) 20-, 24-pin products (2/2)
		25	Modification of Notes 1 and 2 in (2) 30-pin products (1/2)
		26	Modification of Notes 1 and 3 in (2) 30-pin products (2/2)
		27	Modification of (3) Peripheral functions (Common to all products)
		28	Modification of table in 2.4 AC Characteristics
		29	Addition of Minimum Instruction Execution Time during Main System Clock Operation
		30	Modification of figures of AC Timing Test Point and External Main System Clock Timing
		31	Modification of figure of AC Timing Test Point
		31	Modification of description and Note 2 in (1) During communication at same potential (UART mode)
		32	Modification of description in (2) During communication at same potential (CSI mode)
		33	Modification of description in (3) During communication at same potential (CSI mode)
		34	Modification of description in (4) During communication at same potential (CSI mode)
		36	Modification of table and Note 2 in (5) During communication at same potential (simplified I ² C mode)
		38, 39	Modification of table and Notes 1 to 9 in (6) Communication at different potential
		40	(1.8 V, 2.5 V, 3 V) (UART mode) Modification of Remarks 1 to 3 in (6) Communication at different potential (1.8
		40	V, 2.5 V, 3 V) (UART mode)
		41	Modification of table in (7) Communication at different potential (2.5 V, 3 V) (CSI mode)
		42	Modification of Caution in (7) Communication at different potential (2.5 V, 3 V) (CSI mode)
		43	Modification of table in (8) Communication at different potential (1.8 V, 2.5 V, 3 V) (CSI mode) (1/3)
		44	Modification of table and Notes 1 and 2 in (8) Communication at different potential (1.8 V, 2.5 V, 3 V) (CSI mode) (2/3)
		45	Modification of table, Note 1, and Caution 1 in (8) Communication at different potential (1.8 V, 2.5 V, 3 V) (CSI mode) (3/3)
		47	Modification of table in (9) Communication at different potential (1.8 V, 2.5 V, 3 V) (CSI mode)
		50	Modification of table, Note 1, and Caution 1 in (10) Communication at different potential (1.8 V, 2.5 V, 3 V) (simplified I ² C mode)

		Description	
Rev.	Date	Page	Summary
2.00	Sep 06, 2013	52	Modification of Remark in 2.5.2 Serial interface IICA
	•	53	Addition of table to 2.6.1 A/D converter characteristics
		53	Modification of description in 2.6.1 (1)
		54	Modification of Notes 3 to 5 in 2.6.1 (1)
		54	Modification of description and Notes 2 to 4 in 2.6.1 (2)
2.00	Sep 06, 2013	55	Modification of description and Notes 3 and 4 in 2.6.1 (3)
		56	Modification of description and Notes 3 and 4 in 2.6.1 (4)
		57	Modification of table in 2.6.2 Temperature sensor/internal reference voltage characteristics
		57	Modification of table and Note in 2.6.3 POR circuit characteristics
		58	Modification of table in 2.6.4 LVD circuit characteristics
		59	Modification of table of LVD detection voltage of interrupt & reset mode
		59	Modification of number and title to 2.6.5 Power supply voltage rising slope characteristics
		61	Modification of table, figure, and Remark in 2.10 Timing of Entry to Flash Memory Programming Modes
		62 to 103	Addition of products of industrial applications (G: $T_A = -40$ to $+105^{\circ}C$)
		104 to 106	Addition of products of industrial applications (G: $T_A = -40$ to $+105^{\circ}C$)
2.10	Mar 25, 2016	6	Modification of Figure 1-1 Part Number, Memory Size, and Package of RL78/G12
		7	Modification of Table 1-1 List of Ordering Part Numbers
		8	Addition of product name (RL78/G12) and description (Top View) in 1.4.1 20- pin products
		9	Addition of product name (RL78/G12) and description (Top View) in 1.4.2 24- pin products
		10	Addition of product name (RL78/G12) and description (Top View) in 1.4.3 30- pin products
		15	Modification of description in 1.7 Outline of Functions
		16	Modification of description, and addition of target products
		52	Modification of note 2 in 2.5.2 Serial interface IICA
		60	Modification of title and note, and addition of caution in 2.7 RAM Data Retention Characteristics
		60	Modification of conditions in 2.8 Flash Memory Programming Characteristics
		62	Modification of description, and addition of target products and remark
		94	Modification of note 2 in 3.5.2 Serial interface IICA
		102	Modification of title and note in 3.7 RAM Data Retention Characteristics
		102	Modification of conditions in 3.8 Flash Memory Programming Characteristics
		104 to 106	Addition of package name
2.20	Oct 31, 2018	4	Modification of Table 1-1 List of Ordering Part Numbers
		7	Modification of pin configuration diagram in 1.4.1 20-pin products

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NOTES FOR CMOS DEVICES

- (1) VOLTAGE APPLICATION WAVEFORM AT INPUT PIN: Waveform distortion due to input noise or a reflected wave may cause malfunction. If the input of the CMOS device stays in the area between VIL (MAX) and VIH (MIN) due to noise, etc., the device may malfunction. Take care to prevent chattering noise from entering the device when the input level is fixed, and also in the transition period when the input level passes through the area between VIL (MAX) and VIH (MIN).
- (2) HANDLING OF UNUSED INPUT PINS: Unconnected CMOS device inputs can be cause of malfunction. If an input pin is unconnected, it is possible that an internal input level may be generated due to noise, etc., causing malfunction. CMOS devices behave differently than Bipolar or NMOS devices. Input levels of CMOS devices must be fixed high or low by using pull-up or pull-down circuitry. Each unused pin should be connected to VDD or GND via a resistor if there is a possibility that it will be an output pin. All handling related to unused pins must be judged separately for each device and according to related specifications governing the device.
- (3) PRECAUTION AGAINST ESD: A strong electric field, when exposed to a MOS device, can cause destruction of the gate oxide and ultimately degrade the device operation. Steps must be taken to stop generation of static electricity as much as possible, and quickly dissipate it when it has occurred. Environmental control must be adequate. When it is dry, a humidifier should be used. It is recommended to avoid using insulators that easily build up static electricity. Semiconductor devices must be stored and transported in an anti-static container, static shielding bag or conductive material. All test and measurement tools including work benches and floors should be grounded. The operator should be grounded using a wrist strap. Semiconductor devices must not be touched with bare hands. Similar precautions need to be taken for PW boards with mounted semiconductor devices.
- (4) STATUS BEFORE INITIALIZATION: Power-on does not necessarily define the initial status of a MOS device. Immediately after the power source is turned ON, devices with reset functions have not yet been initialized. Hence, power-on does not guarantee output pin levels, I/O settings or contents of registers. A device is not initialized until the reset signal is received. A reset operation must be executed immediately after power-on for devices with reset functions.
- (5) POWER ON/OFF SEQUENCE: In the case of a device that uses different power supplies for the internal operation and external interface, as a rule, switch on the external power supply after switching on the internal power supply. When switching the power supply off, as a rule, switch off the external power supply and then the internal power supply. Use of the reverse power on/off sequences may result in the application of an overvoltage to the internal elements of the device, causing malfunction and degradation of internal elements due to the passage of an abnormal current. The correct power on/off sequence must be judged separately for each device and according to related specifications governing the device.
- (6) INPUT OF SIGNAL DURING POWER OFF STATE : Do not input signals or an I/O pull-up power supply while the device is not powered. The current injection that results from input of such a signal or I/O pull-up power supply may cause malfunction and the abnormal current that passes in the device at this time may cause degradation of internal elements. Input of signals during the power off state must be judged separately for each device and according to related specifications governing the device.

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